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STM32F303xB STM32F303xC

ARM®-based Cortex®-M4 32b MCU+FPU, up to 256KB Flash+48KB SRAM, 4 ADCs, 2 DAC ch., 7 comp, 4 PGA, timers, 2.0-3.6 V

Datasheet - production data

Features

- Core: ARM[®] Cortex[®]-M4 32-bit CPU with FPU (72 MHz max), single-cycle multiplication and HW division, 90 DMIPS (from CCM) /1.25 DMIPS/MHz (Dhrystone 2.1) performance at 0 wait state memory access, DSP instruction and MPU (memory protection unit)
- Operating conditions:
 - V_{DD}, V_{DDA} voltage range: 2.0 V to 3.6 V
- Memories
 - 128 to 256 Kbytes of Flash memory
 - Up to 40 Kbytes of SRAM, with HW parity check implemented on the first 16 Kbytes.
 - Routine booster: 8 Kbytes of SRAM on instruction and data bus, with HW parity check (CCM)
- CRC calculation unit
- Reset and supply management
 - Power-on/Power-down reset (POR/PDR)
 - Programmable voltage detector (PVD)
 - Low power modes: Sleep, Stop and Standby
 - V_{BAT} supply for RTC and backup registers
- Clock management
 - 4 to 32 MHz crystal oscillator
 - 32 kHz oscillator for RTC with calibration
 - Internal 8 MHz RC with x 16 PLL option
 - Internal 40 kHz oscillator
- Up to 87 fast I/Os
 - All mappable on external interrupt vectors
 - Several 5 V-tolerant
- 12-channel DMA controller
- Four ADCs 0.20 µS (up to 39 channels) with selectable resolution of 12/10/8/6 bits, 0 to 3.6 V conversion range, single ended/differential input, separate analog supply from 2 to 3.6 V
- Two 12-bit DAC channels with analog supply from 2.4 to 3.6 V
- Seven fast rail-to-rail analog comparators with analog supply from 2 to 3.6 V
- Four operational amplifiers that can be used in PGA mode, all terminals accessible with analog supply from 2.4 to 3.6 V

LQFP48 (7 × 7 mm) LQFP64 (10 × 10 mm) LQFP100 (14 × 14 mm)



- Up to 24 capacitive sensing channels supporting touchkey, linear and rotary touch sensors
- Up to 13 timers
 - One 32-bit timer and two 16-bit timers with up to 4 IC/OC/PWM or pulse counter and quadrature (incremental) encoder input
 - Two 16-bit 6-channel advanced-control timers, with up to 6 PWM channels, deadtime generation and emergency stop
 - One 16-bit timer with 2 IC/OCs, 1 OCN/PWM, deadtime generation and emergency stop
 - Two 16-bit timers with IC/OC/OCN/PWM, deadtime generation and emergency stop
 - Two watchdog timers (independent, window)
 - SysTick timer: 24-bit downcounter
 - Two 16-bit basic timers to drive the DAC
- Calendar RTC with Alarm, periodic wakeup from Stop/Standby
- Communication interfaces
 - CAN interface (2.0B Active)
 - Two I²C Fast mode plus (1 Mbit/s) with 20 mA current sink, SMBus/PMBus, wakeup from STOP
 - Up to five USART/UARTs (ISO 7816 interface, LIN, IrDA, modem control)
 - Up to three SPIs, two with multiplexed half/full duplex I2S interface, 4 to 16 programmable bit frames
 - USB 2.0 full speed interface
 - Infrared transmitter
- Serial wire debug, Cortex[®]-M4 with FPU ETM, JTAG
- 96-bit unique ID

Table 1. Device summary

Reference	Part number			
STM32F303xB STM32F303xC	STM32F303CB, STM32F303CC, STM32F303RB, STM32F303RC, STM32F303VB, STM32F303VC			

Contents

1	Intro	duction	8
2	Desc	ription	9
3	Func	tional overview	12
	3.1	ARM® Cortex®-M4 core with FPU with embedded Flash and SRAM	12
	3.2	Memory protection unit (MPU)	12
	3.3	Embedded Flash memory	12
	3.4	Embedded SRAM	13
	3.5	Boot modes	13
	3.6	Cyclic redundancy check (CRC)	13
	3.7	Power management	14
		3.7.1 Power supply schemes	14
		3.7.2 Power supply supervision	14
		3.7.3 Voltage regulator	14
		3.7.4 Low-power modes	15
	3.8	Clocks and startup	16
	3.9	General-purpose input/outputs (GPIOs)	18
	3.10	Direct memory access (DMA)	18
	3.11	Interrupts and events	18
		3.11.1 Nested vectored interrupt controller (NVIC)	18
	3.12	Fast analog-to-digital converter (ADC)	19
		3.12.1 Temperature sensor	19
		3.12.2 Internal voltage reference (V _{REFINT})	
		3.12.3 V _{BAT} battery voltage monitoring	
		3.12.4 OPAMP reference voltage (VREFOPAMP)	
	3.13	Digital-to-analog converter (DAC)	20
	3.14	Operational amplifier (OPAMP)	20
	3.15	Fast comparators (COMP)	21
	3.16	Timers and watchdogs	21
		3.16.1 Advanced timers (TIM1, TIM8)	22
		3.16.2 General-purpose timers (TIM2, TIM3, TIM4, TIM15, TIM16, TIM17)	
		3.16.3 Basic timers (TIM6, TIM7)	22

		3.16.4	Independent watchdog (IWDG)	23
		3.16.5	Window watchdog (WWDG)	23
		3.16.6	SysTick timer	23
	3.17	Real-tir	me clock (RTC) and backup registers	. 23
	3.18	Inter-in	tegrated circuit interface (I ² C)	. 24
	3.19	Univers	sal synchronous/asynchronous receiver transmitter (USART)	. 25
	3.20	Univers	sal asynchronous receiver transmitter (UART)	. 25
	3.21	Serial p	peripheral interface (SPI)/Inter-integrated sound interfaces (I2S)	. 26
	3.22	Control	ller area network (CAN)	. 26
	3.23	Univers	sal serial bus (USB)	. 26
	3.24	Infrared	d Transmitter	. 27
	3.25	Touch	sensing controller (TSC)	. 27
	3.26		pment support	
		3.26.1	Serial wire JTAG debug port (SWJ-DP)	
		3.26.2	Embedded trace macrocell™	29
	D '	4	and the second second	00
	DINA	uts and	pin description	. 30
4	FIIIO			
5			oping	. 49
	Mem	ory mar	oping	
5	Mem Elect	ory mar	pping	. 52
5	Mem	ory mar	oping	. 52
5	Mem Elect	ory mar rical ch	pping paracteristics	. 52 . 52
5	Mem Elect	ory map rical ch Parame 6.1.1	pping	. 52 . 52 52
5	Mem Elect	ory map rical ch Parame 6.1.1 6.1.2 6.1.3	pping naracteristics eter conditions Minimum and maximum values Typical values	. 52 . 52 . 52 52 52
5	Mem Elect	ory map rical ch Parame 6.1.1 6.1.2 6.1.3	pping	. 52 . 52 . 52 . 52 . 52 . 52 . 52
5	Mem Elect	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4	pping	. 52 . 52 . 52 . 52 . 52 . 52 . 52
5	Mem Elect	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5	pping naracteristics eter conditions Minimum and maximum values Typical values Typical curves Loading capacitor Pin input voltage	. 52 . 52 . 52 . 52 . 52 . 52 . 52 . 52
5	Mem Elect	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5 6.1.6 6.1.7	pping	. 52 . 52 . 52 . 52 . 52 . 52 . 52 . 52 . 54
5	Mem Elect 6.1	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5 6.1.6 6.1.7 Absolut	pping caracteristics eter conditions Minimum and maximum values Typical values Typical curves Loading capacitor Pin input voltage Power supply scheme Current consumption measurement	. 52 52 52 52 52 52 52 53 54 55
5	Mem Elect 6.1	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5 6.1.6 6.1.7 Absolut	eter conditions Minimum and maximum values Typical values Typical curves Loading capacitor Pin input voltage Power supply scheme Current consumption measurement te maximum ratings	. 52 52 52 52 52 54 55 57
5	Mem Elect 6.1	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5 6.1.6 6.1.7 Absolut Operati	pping paracteristics eter conditions Minimum and maximum values Typical values Typical curves Loading capacitor Pin input voltage Power supply scheme Current consumption measurement te maximum ratings ing conditions	. 52 . 52 . 52 . 52 . 52 . 52 . 52 . 52 . 52
5	Mem Elect 6.1	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5 6.1.6 6.1.7 Absolut Operati 6.3.1	poping paracteristics eter conditions Minimum and maximum values Typical values Typical curves Loading capacitor Pin input voltage Power supply scheme Current consumption measurement te maximum ratings ing conditions General operating conditions	. 52 52 52 52 52 52 53 54 55 57 58
5	Mem Elect 6.1	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5 6.1.6 6.1.7 Absolut Operati 6.3.1 6.3.2	poping	. 52 52 52 52 52 54 55 57 58 58
5	Mem Elect 6.1	ory map rical ch Parame 6.1.1 6.1.2 6.1.3 6.1.4 6.1.5 6.1.6 6.1.7 Absolut Operati 6.3.1 6.3.2 6.3.3	poping paracteristics eter conditions Minimum and maximum values Typical values Typical curves Loading capacitor Pin input voltage Power supply scheme Current consumption measurement te maximum ratings ing conditions General operating conditions Operating conditions at power-up / power-down Embedded reset and power control block characteristics	. 52 52 52 52 52 52 53 54 55 57 58 60



		6.3.6	Wakeup time from low-power mode71
		6.3.7	External clock source characteristics
		6.3.8	Internal clock source characteristics
		6.3.9	PLL characteristics
		6.3.10	Memory characteristics
		6.3.11	EMC characteristics
		6.3.12	Electrical sensitivity characteristics
		6.3.13	I/O current injection characteristics
		6.3.14	I/O port characteristics
		6.3.15	NRST pin characteristics
		6.3.16	Timer characteristics91
		6.3.17	Communications interfaces
		6.3.18	ADC characteristics
		6.3.19	DAC electrical specifications
		6.3.20	Comparator characteristics
		6.3.21	Operational amplifier characteristics
		6.3.22	Temperature sensor characteristics
		6.3.23	V _{BAT} monitoring characteristics
7	Pacl	kage cha	aracteristics
	7.1	Packag	ge mechanical data
	7.2	Therma	al characteristics
		7.2.1	Reference document
		7.2.2	Selecting the product temperature range
8	Part	number	ing133
9	Revi	ision his	tory



List of tables

Table 1.	Device summary	. 1
Table 2.	STM32F303xB/STM32F303xC family device features and peripheral counts	
Table 3.	Timer feature comparison	
Table 4.	Comparison of I2C analog and digital filters	
Table 5.	STM32F303xB/STM32F303xC I ² C implementation	
Table 6.	USART features	
Table 7.	STM32F303xB/STM32F303xC SPI/I2S implementation	
Table 8.	Capacitive sensing GPIOs available on STM32F303xB/STM32F303xC devices	
Table 9.	No. of capacitive sensing channels available on STM32F303xB/STM32F303xC devices . 2	
Table 10.	Legend/abbreviations used in the pinout table	
Table 11.	STM32F303xB/STM32F303xC pin definitions	
Table 12.	Alternate functions for port A	
Table 13.	Alternate functions for port B	
Table 14.	Alternate functions for port C	
Table 15.	Alternate functions for port D	
Table 16.	Alternate functions for port E	
Table 17.	Alternate functions for port F	
Table 18.	STM32F303xB/STM32F303xC memory map, peripheral register boundary addresses §	
Table 19.	Voltage characteristics	
Table 20.	Current characteristics	
Table 21.	Thermal characteristics	
Table 22.	General operating conditions	
Table 23.	Operating conditions at power-up / power-down	
Table 24.	Embedded reset and power control block characteristics	
Table 25.	Programmable voltage detector characteristics	
Table 26.	Embedded internal reference voltage	
Table 27.	Internal reference voltage calibration values	
Table 28.	Typical and maximum current consumption from V_{DD} supply at $V_{DD} = 3.6V \dots \dots$	
Table 29.	Typical and maximum current consumption from the V _{DDA} supply	
Table 30.	Typical and maximum V _{DD} consumption in Stop and Standby modes	
Table 31.	Typical and maximum V _{DDA} consumption in Stop and Standby modes	
Table 32.	Typical and maximum current consumption from V _{BAT} supply	
Table 33.	Typical current consumption in Run mode, code with data processing running from Flash6	
Table 34.	Typical current consumption in Sleep mode, code running from Flash or RAM	
Table 35.	Switching output I/O current consumption	
Table 36.	Peripheral current consumption	
Table 37.	Low-power mode wakeup timings	
Table 38.	High-speed external user clock characteristics	
Table 39.	Low-speed external user clock characteristics	73
Table 40.	HSE oscillator characteristics	
Table 41.	LSE oscillator characteristics (f _{LSE} = 32.768 kHz)	76
Table 42.	HSI oscillator characteristics	
Table 43.	LSI oscillator characteristics	
Table 44.	PLL characteristics	
Table 45.	Flash memory characteristics	
Table 46.	Flash memory endurance and data retention	
Table 47.	EMS characteristics	
Table 48.	EMI characteristics	



Table 49.	ESD absolute maximum ratings	. 82
Table 50.	Electrical sensitivities	. 83
Table 51.	I/O current injection susceptibility	. 84
Table 52.	I/O static characteristics	. 85
Table 53.	Output voltage characteristics	. 88
Table 54.	I/O AC characteristics	. 89
Table 55.	NRST pin characteristics	. 90
Table 56.	TIMx characteristics	. 91
Table 57.	IWDG min/max timeout period at 40 kHz (LSI)	. 92
Table 58.	WWDG min-max timeout value @72 MHz (PCLK)	. 92
Table 59.	I2C timings specification (see I2C specification, rev.03, June 2007)	. 93
Table 60.	I2C analog filter characteristics	. 95
Table 61.	SPI characteristics	. 96
Table 62.	I ² S characteristics	. 99
Table 63.	USB startup time	101
Table 64.	USB DC electrical characteristics	102
Table 65.	USB: Full-speed electrical characteristics	103
Table 66.	ADC characteristics	104
Table 67.	Maximum ADC RAIN	105
Table 68.	ADC accuracy - limited test conditions, 100-pin packages	107
Table 69.	ADC accuracy, 100-pin packages	109
Table 70.	ADC accuracy - limited test conditions, 64-pin packages	111
Table 71.	ADC accuracy, 64-pin packages	113
Table 72.	ADC accuracy at 1MSPS	114
Table 73.	DAC characteristics	116
Table 74.	Comparator characteristics	117
Table 75.	Operational amplifier characteristics	119
Table 76.	TS characteristics	122
Table 77.	Temperature sensor calibration values	122
Table 78.	V _{BAT} monitoring characteristics	122
Table 79.	LQPF100 – 14 x 14 mm, low-profile quad flat package mechanical data	124
Table 80.	LQFP64 – 10 x 10 mm low-profile quad flat package mechanical data	126
Table 81.	LQFP48 – 7 x 7 mm, 48-pin low-profile quad flat package mechanical data	128
Table 82.	Package thermal characteristics	130
Table 83.	Ordering information scheme	133
Table 84.	Document revision history	134



List of figures

Figure 1.	STM32F303xB/STM32F303xC block diagram	
Figure 2.	Clock tree	
Figure 3.	Infrared transmitter	
Figure 4.	STM32F303xB/STM32F303xC LQFP48 pinout	30
Figure 5.	STM32F303xB/STM32F303xC LQFP64 pinout	31
Figure 6.	STM32F303xB/STM32F303xC LQFP100 pinout	32
Figure 7.	STM32F303xB/STM32F303xC memory map	49
Figure 8.	Pin loading conditions	52
Figure 9.	Pin input voltage	52
Figure 10.	Power supply scheme	53
Figure 11.	Current consumption measurement scheme	
Figure 12.	Typical V _{BAT} current consumption (LSE and RTC ON/LSEDRV[1:0] = '00')	
Figure 13.	High-speed external clock source AC timing diagram	72
Figure 14.	Low-speed external clock source AC timing diagram	
Figure 15.	Typical application with an 8 MHz crystal	
Figure 16.	Typical application with a 32.768 kHz crystal	
Figure 17.	HSI oscillator accuracy characterization results	
Figure 18.	TC and TTa I/O input characteristics - CMOS port	
Figure 19.	TC and TTa I/O input characteristics - TTL port	
Figure 20.	Five volt tolerant (FT and FTf) I/O input characteristics - CMOS port	
Figure 21.	Five volt tolerant (FT and FTf) I/O input characteristics - TTL port	
Figure 22.	I/O AC characteristics definition	
Figure 23.	Recommended NRST pin protection	
Figure 24.	I ² C bus AC waveforms and measurement circuit	
Figure 25.	SPI timing diagram - slave mode and CPHA = 0	97
Figure 26.	SPI timing diagram - slave mode and CPHA = 1 ⁽¹⁾	97
Figure 27.	SPI timing diagram - master mode ⁽¹⁾	98
Figure 28.	I ² S slave timing diagram (Philips protocol) ⁽¹⁾	. 100
Figure 29.	I ² S master timing diagram (Philips protocol) ⁽¹⁾	
Figure 30.	USB timings: definition of data signal rise and fall time	
Figure 31.	ADC accuracy characteristics	
Figure 32.	Typical connection diagram using the ADC	
Figure 33.	12-bit buffered /non-buffered DAC	
Figure 34.	OPAMP voltage noise versus frequency	
Figure 35.	LQFP100 – 14 x 14 mm, 100-pin low-profile quad flat package outline	
Figure 36.	LQFP100 recommended footprint	
Figure 37.	LQFP64 – 10 x 10 mm, 64 pin low-profile quad flat package outline	
Figure 38.	LQFP64 recommended footprint	
Figure 39.	LQFP48 – 7 x 7 mm, 48-pin low-profile quad flat package outline	
Figure 40.	LQFP48 recommended footprint	129



1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F303xB/STM32F303xC microcontrollers.

This STM32F303xB/STM32F303xC datasheet should be read in conjunction with the RM0316 STM32F303x, STM32F358xC and STM32F328x4/6/8 reference manual. The reference manual is available from the STMicroelectronics website www.st.com.

For information on the Cortex®-M4 core with FPU, please refer to:

- Cortex®-M4 with FPU Technical Reference Manual, available from ARM website www.arm.com.
- STM32F3xxx and STM32F4xxx Cortex[®]-M4 programming manual (PM0214) available from our website www.st.com.



2 Description

The STM32F303xB/STM32F303xC family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core with FPU operating at a frequency of up to 72 MHz, and embedding a floating point unit (FPU), a memory protection unit (MPU) and an embedded trace macrocell (ETM). The family incorporates high-speed embedded memories (up to 256 Kbytes of Flash memory, up to 40 Kbytes of SRAM) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The devices offer up to four fast 12-bit ADCs (5 Msps), seven comparators, four operational amplifiers, up to two DAC channels, a low-power RTC, up to five general-purpose 16-bit timers, one general-purpose 32-bit timer, and two timers dedicated to motor control. They also feature standard and advanced communication interfaces: up to two I²Cs, up to three SPIs (two SPIs are with multiplexed full-duplex I2Ss), three USARTs, up to two UARTs, CAN and USB. To achieve audio class accuracy, the I2S peripherals can be clocked via an external PLL.

The STM32F303xB/STM32F303xC family operates in the -40 to +85 $^{\circ}$ C and -40 to +105 $^{\circ}$ C temperature ranges from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F303xB/STM32F303xC family offers devices in three packages ranging from 48 pins to 100 pins.

The set of included peripherals changes with the device chosen.



Table 2.STM32F303xB/STM32F303xC family device features and peripheral counts

Timers Gel Bas	I Memory) Ivanced Introl eneral purpose	128 32	256 40	128 32 8 2 (16		128 32	256 40
CCM (Core Coupled RAM (Kbytes) Adv con Timers Gel Bas	I Memory) Ivanced Introl Ivanced Introl Ivanced Ivance	32	40	8	3	32	40
Timers RAM (Kbytes) Adv con Get Bas	Ivanced ntrol eneral purpose sic						
Timers Gel Bas	ntrol eneral purpose ssic			2 (16	S-hit)		
Bas	sic				2 (16-bit)		
				5 (16-bit) 1 (32-bit)			
	or (12C)(1)			2 (16	6-bit)		
SPI	1 (123)			3(2)		
I ² C				2	2		
Communication US.	SART			3	3		
interfaces	\RT	0		2			
CA	AN	1					
US	SB	1					
	ormal I/Os C, TTa)	20		2	27 45		5
5-ve	olt tolerant s (FT, FTf)	17 25		42			
DMA channels		12					
Capacitive sensing c	channels	1	17 18		4		
12-bit ADCs		4					
12-bit DAC channels	3	2					
Analog comparator		7					
Operational amplifier	rs	4					
CPU frequency		72 MHz					
Operating voltage		2.0 to 3.6 V					
Operating temperature		Ambient operating temperature: - 40 to 85 °C / - 40 to 105 °C Junction temperature: - 40 to 125 °C				o 105 °C	
Packages		LQF	P48	LQF	P64	LQF	P100

^{1.} The SPI interfaces can work in an exclusive way in either the SPI mode or the I²S audio mode.

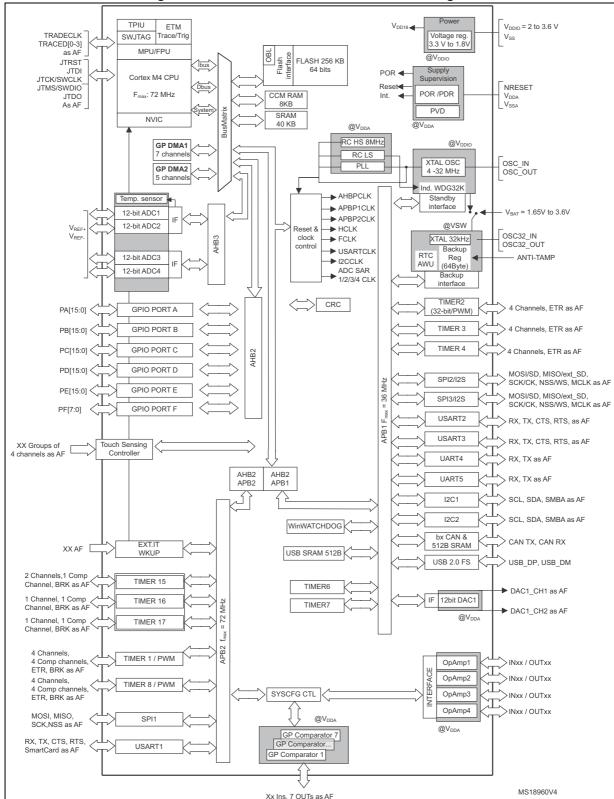


Figure 1.STM32F303xB/STM32F303xC block diagram

1. AF: alternate function on I/O pins.



3 Functional overview

3.1 ARM[®] Cortex[®]-M4 core with FPU with embedded Flash and SRAM

The ARM Cortex-M4 processor with FPU is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM Cortex-M4 32-bit RISC processor with FPU features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU speeds up software development by using metalanguage development tools, while avoiding saturation.

With its embedded ARM core, the STM32F303xB/STM32F303xC family is compatible with all ARM tools and software.

Figure 1 shows the general block diagram of the STM32F303xB/STM32F303xC family devices.

3.2 Memory protection unit (MPU)

The memory protection unit (MPU) is used to separate the processing of tasks from the data protection. The MPU can manage up to 8 protection areas that can all be further divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The memory protection unit is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.3 Embedded Flash memory

All STM32F303xB/STM32F303xC devices feature up to 256 Kbytes of embedded Flash memory available for storing programs and data. The Flash memory access time is adjusted to the CPU clock frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above).



3.4 Embedded SRAM

STM32F303xB/STM32F303xC devices feature up to 48 Kbytes of embedded SRAM with hardware parity check. The memory can be accessed in read/write at CPU clock speed with 0 wait states, allowing the CPU to achieve 90 Dhrystone Mips at 72 MHz (when running code from the CCM (Core Coupled Memory) RAM).

- 8 Kbytes of CCM RAM mapped on both instruction and data bus, used to execute critical routines or to access data (parity check on all of CCM RAM).
- 40 Kbytes of SRAM mapped on the data bus (parity check on first 16 Kbytes of SRAM).

3.5 Boot modes

At startup, Boot0 pin and Boot1 option bit are used to select one of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in the system memory. It is used to reprogram the Flash memory by using USART1 (PA9/PA10), USART2 (PD5/PD6) or USB (PA11/PA12) through DFU (device firmware upgrade).

3.6 Cyclic redundancy check (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.7 Power management

3.7.1 Power supply schemes

- V_{SS} , V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. It is provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supply for ADC, DACs, comparators operational amplifiers, reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the DACs and operational amplifiers are used). The V_{DDA} voltage level must be always greater or equal to the V_{DD} voltage level and must be provided first.
- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

3.7.2 Power supply supervision

The device has an integrated power-on reset (POR) and power-down reset (PDR) circuits. They are always active, and ensure proper operation above a threshold of 2 V. The device remains in reset mode when the monitored supply voltage is below a specified threshold, VPOR/PDR, without the need for an external reset circuit.

- The POR monitors only the V_{DD} supply voltage. During the startup phase it is required that V_{DDA} should arrive first and be greater than or equal to V_{DD}.
- The PDR monitors both the V_{DD} and V_{DDA} supply voltages, however the V_{DDA} power supply supervisor can be disabled (by programming a dedicated Option bit) to reduce the power consumption if the application design ensures that V_{DDA} is higher than or equal to V_{DD}.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the VPVD threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.7.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR), and power-down.

- The MR mode is used in the nominal regulation mode (Run)
- The LPR mode is used in Stop mode.
- The power-down mode is used in Standby mode: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The voltage regulator is always enabled after reset. It is disabled in Standby mode.

577

3.7.4 Low-power modes

The STM32F303xB/STM32F303xC supports three low power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

Stop mode

Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the USB wakeup, the RTC alarm, COMPx, I2Cx or U(S)ARTx.

Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the Backup domain and Standby circuitry.

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin or an RTC alarm occurs.

Note:

The RTC, the IWDG and the corresponding clock sources are not stopped by entering Stop or Standby mode.

3.8 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-32 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example with failure of an indirectly used external oscillator).

Several prescalers allow to configure the AHB frequency, the high speed APB (APB2) and the low speed APB (APB1) domains. The maximum frequency of the AHB and the high speed APB domains is 72 MHz, while the maximum allowed frequency of the low speed APB domain is 36 MHz.

Figure 2.Clock tree FLITFCLK to Flash programming interface HSI → to I2Cx (x = 1,2) SYSCLK **I2SSRC** SYSCLK ▶to I2Sx (x = 2,3) I2S_CKIN USB USBCLK prescaler to USB interface 8 MHz HSI /1,1.5 HSI RC /2 to AHB bus, core, memory and DMA HCLK PLLSRC | PLLMUL to cortex System timer /8 SW → FHCLK Cortex free HSI PLL running clock
to APB1 peripherals AHB APB1 PLLCLK PCLK1 x2,x3, prescaler prescaler /1,2,..512 /1,2,4,8,16 x16 HSE. **SYSCLK** If (APB1 prescaler css → to TIM 2,3,4,6,7 /2,/3,.. =1) x1 else x2 /16 PCLK1 SYSCLK HSI to U(S)ARTx (x = 2..5) OSC_OUT 4-32 MHz HSE OSC LSE OSC IN APB2 PCLK2 prescaler → to APB2 peripherals /1,2,4,8,16 /32 RTCCLK → to RTC OSC32_IN LSE OSC If (APB2 prescaler → to TIM 15,16,17 32.768kHz LSE OSC32_OUT =1) x1 else x2 RTCSEL[1:0] PCLK2 → IWDGCLK to IWDG LSI RC SYSCLK HSI ▶ to USART1 40kHz LSE /2 -PLLCLK Main clock HSI output MCO LSI x2 ►TIM1/8 **HSE** SYSCLK -LSE ADC Prescaler /1,2,4 мсо to ADCxy (xy = 12, 34)ADC Prescaler 1,2,4,6,8,10,12,16 32,64,128,256 MS34001V2



3.9 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current capable except for analog inputs.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

Fast I/O handling allows I/O toggling up to 36 MHz.

3.10 Direct memory access (DMA)

The flexible general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each of the 12 DMA channels is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I^2C , USART, general-purpose timers, DAC and ADC.

3.11 Interrupts and events

3.11.1 Nested vectored interrupt controller (NVIC)

The STM32F303xB/STM32F303xC devices embed a nested vectored interrupt controller (NVIC) able to handle up to 66 maskable interrupt channels and 16 priority levels.

The NVIC benefits are the following:

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving higher priority interrupts
- Support for tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

The NVIC hardware block provides flexible interrupt management features with minimal interrupt latency.

477

3.12 Fast analog-to-digital converter (ADC)

four fast analog-to-digital converters 5 MSPS, with selectable resolution between 12 and 6 bit, are embedded in the STM32F303xB/STM32F303xC family devices. The ADCs have up to 39 external channels. Some of the external channels are shared between ADC1&2 and between ADC3&4. Channels can be configured to be either single-ended input or differential input. The ADCs can perform conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADCs have also internal channels: Temperature sensor connected to ADC1 channel 16, $V_{BAT/2}$ connected to ADC1 channel 17, Voltage reference V_{REFINT} connected to the 4 ADCs channel 18, VOPAMP1 connected to ADC1 channel 15, VOPAMP2 connected to ADC2 channel 17, VREFOPAMP3 connected to ADC3 channel 17 and VREFOPAMP4 connected to ADC4 channel 17.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold
- Single-shunt phase current reading techniques.

The ADC can be served by the DMA controller. 3 analog watchdogs per ADC are available.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers and the advanced-control timers (TIM1 and TIM8) can be internally connected to the ADC start trigger and injection trigger, respectively, to allow the application to synchronize A/D conversion and timers.

3.12.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

3.12.2 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADCx_IN18, x=1...4 input channel. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

3.12.3 V_{BAT} battery voltage monitoring

This embedded hardware feature allows the application to measure the V_{BAT} battery voltage using the internal ADC channel ADC1_IN17. As the V_{BAT} voltage may be higher than V_{DDA} , and thus outside the ADC input range, the V_{BAT} pin is internally connected to a bridge divider by 2. As a consequence, the converted digital value is half the V_{BAT} voltage.

3.12.4 OPAMP reference voltage (VREFOPAMP)

Every OPAMP reference voltage can be measured using a corresponding ADC internal channel: VREFOPAMP1 connected to ADC1 channel 15, VREFOPAMP2 connected to ADC2 channel 17, VREFOPAMP3 connected to ADC3 channel 17, VREFOPAMP4 connected to ADC4 channel 17.

3.13 Digital-to-analog converter (DAC)

Two 12-bit buffered DAC channels can be used to convert digital signals into analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This digital interface supports the following features:

- Two DAC output channels
- 8-bit or 10-bit monotonic output
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- Dual DAC channel independent or simultaneous conversions
- DMA capability (for each channel)
- External triggers for conversion

3.14 Operational amplifier (OPAMP)

The STM32F303xB/STM32F303xC embeds four operational amplifiers with external or internal follower routing and PGA capability (or even amplifier and filter capability with external components). When an operational amplifier is selected, an external ADC channel is used to enable output measurement.

The operational amplifier features:

- 8.2 MHz bandwidth
- 0.5 mA output capability
- Rail-to-rail input/output
- In PGA mode, the gain can be programmed to be 2, 4, 8 or 16.

57/

3.15 Fast comparators (COMP)

The STM32F303xB/STM32F303xC devices embed seven fast rail-to-rail comparators with programmable reference voltage (internal or external), hysteresis and speed (low speed for low power) and with selectable output polarity.

The reference voltage can be one of the following:

- External I/O
- DAC output pin
- Internal reference voltage or submultiple (1/4, 1/2, 3/4). Refer to *Table 26: Embedded internal reference voltage on page 60* for the value and precision of the internal reference voltage.

All comparators can wake up from STOP mode, generate interrupts and breaks for the timers and can be also combined per pair into a window comparator

3.16 Timers and watchdogs

The STM32F303xB/STM32F303xC includes two advanced control timers, up to six general-purpose timers, two basic timers, two watchdog timers and a SysTick timer. The table below compares the features of the advanced control, general purpose and basic timers.

Table 3.Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare Channels	Complementary outputs
Advanced	TIM1, TIM8	16-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	Yes
General- purpose	TIM2	32-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	No
General- purpose	TIM3, TIM4	16-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	No
General- purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General- purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.16.1 Advanced timers (TIM1, TIM8)

The advanced-control timers (TIM1 and TIM8) can each be seen as a three-phase PWM multiplexed on six channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers. The four independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIM timers (described in *Section 3.16.2* using the same architecture, so the advanced-control timers can work together with the TIM timers via the Timer Link feature for synchronization or event chaining.

3.16.2 General-purpose timers (TIM2, TIM3, TIM4, TIM15, TIM16, TIM17)

There are up to six synchronizable general-purpose timers embedded in the STM32F303xB/STM32F303xC (see *Table 3* for differences). Each general-purpose timer can be used to generate PWM outputs, or act as a simple time base.

TIM2, 3, and TIM4

These are full-featured general-purpose timers:

- TIM2 has a 32-bit auto-reload up/downcounter and 32-bit prescaler
- TIM3 and 4 have 16-bit auto-reload up/downcounters and 16-bit prescalers.

These timers all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together, or with the other general-purpose timers via the Timer Link feature for synchronization or event chaining.

The counters can be frozen in debug mode.

All have independent DMA request generation and support quadrature encoders.

TIM15, 16 and 17

These three timers general-purpose timers with mid-range features:

They have 16-bit auto-reload upcounters and 16-bit prescalers.

- TIM15 has 2 channels and 1 complementary channel
- TIM16 and TIM17 have 1 channel and 1 complementary channel

All channels can be used for input capture/output compare, PWM or one-pulse mode output.

The timers can work together via the Timer Link feature for synchronization or event chaining. The timers have independent DMA request generation.

The counters can be frozen in debug mode.

3.16.3 Basic timers (TIM6, TIM7)

These timers are mainly used for DAC trigger generation. They can also be used as a generic 16-bit time base.



3.16.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

3.16.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.16.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

3.17 Real-time clock (RTC) and backup registers

The RTC and the 16 backup registers are supplied through a switch that takes power from either the V_{DD} supply when present or the V_{BAT} pin. The backup registers are sixteen 32-bit registers used to store 64 bytes of user application data when V_{DD} power is not present.

They are not reset by a system or power reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Automatic correction for 28, 29 (leap year), 30 and 31 days of the month.
- Two programmable alarms with wake up from Stop and Standby mode capability.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy.
- Three anti-tamper detection pins with programmable filter. The MCU can be woken up from Stopand Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can
 be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be
 woken up from Stop and Standby modes on timestamp event detection.



 17-bit Auto-reload counter for periodic interrupt with wakeup from STOP/STANDBY capability.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 40 kHz)
- The high-speed external clock divided by 32.

3.18 Inter-integrated circuit interface (I²C)

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard (up to 100 KHz), fast (up to 400 KHz) and fast mode + (up to 1 MHz) modes.

Both support 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (2 addresses, 1 with configurable mask). They also include programmable analog and digital noise filters.

Table 4. Comparison of I2C analog and digital filters

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks
Benefits	Available in Stop mode	Extra filtering capability vs. standard requirements. Stable length
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.

In addition, they provide hardware support for SMBUS 2.0 and PMBUS 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. They also have a clock domain independent from the CPU clock, allowing the I2Cx (x=1,2) to wake up the MCU from Stop mode on address match.

The I2C interfaces can be served by the DMA controller.

Refer to *Table 5* for the features available in I2C1 and I2C2.

Table 5.STM32F303xB/STM32F303xC I²C implementation

I2C features ⁽¹⁾	I2C1	I2C2
7-bit addressing mode	Х	Х
10-bit addressing mode	Х	Х
Standard mode (up to 100 kbit/s)	Х	Х
Fast mode (up to 400 kbit/s)	Х	Х
Fast Mode Plus with 20mA output drive I/Os (up to 1 Mbit/s)	Х	Х
Independent clock	Х	Х



Table 5.STM32F303xB/STM32F303xC I²C implementation (continued)

I2C features ⁽¹⁾	I2C1	I2C2
SMBus	Х	Х
Wakeup from STOP	Х	Х

^{1.} X = supported.

3.19 Universal synchronous/asynchronous receiver transmitter (USART)

The STM32F303xB/STM32F303xC devices have three embedded universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3).

The USART interfaces are able to communicate at speeds of up to 9 Mbits/s.

They provide hardware management of the CTS and RTS signals, they support IrDA SIR ENDEC, the multiprocessor communication mode, the single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART interfaces can be served by the DMA controller.

3.20 Universal asynchronous receiver transmitter (UART)

The STM32F303xB/STM32F303xC devices have 2 embedded universal asynchronous receiver transmitters (UART4, and UART5). The UART interfaces support IrDA SIR ENDEC, multiprocessor communication mode and single-wire half-duplex communication mode. The UART4 interface can be served by the DMA controller.

Refer to *Table 6* for the features available in all U(S)ART interfaces.

Table 6.USART features

USART modes/features ⁽¹⁾	USART1	USART2	USART3	UART4	UART5
Hardware flow control for modem	Х	Х	Х	-	-
Continuous communication using DMA	Х	Х	Х	Х	-
Multiprocessor communication	Х	Х	Х	Х	Х
Synchronous mode	Х	Х	Х	-	-
Smartcard mode	Х	Х	Х	-	-
Single-wire half-duplex communication	Х	Х	Х	Х	Х
IrDA SIR ENDEC block	Х	Х	Х	Х	Х
LIN mode	Х	Х	Х	Х	Х
Dual clock domain and wakeup from Stop mode	Х	Х	Х	Х	Х
Receiver timeout interrupt	Х	Х	Х	Х	Х
Modbus communication	Х	Х	Х	Х	Х
Auto baud rate detection	Х	Х	Х	-	-
Driver Enable	Х	Х	Х	-	-

^{1.} X = supported.



3.21 Serial peripheral interface (SPI)/Inter-integrated sound interfaces (I2S)

Up to three SPIs are able to communicate up to 18 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits.

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) supporting four different audio standards can operate as master or slave at half-duplex and full duplex communication modes. They can be configured to transfer 16 and 24 or 32 bits with 16-bit or 32-bit data resolution and synchronized by a specific signal. Audio sampling frequency from 8 kHz up to 192 kHz can be set by 8-bit programmable linear prescaler. When operating in master mode it can output a clock for an external audio component at 256 times the sampling frequency.

Refer to *Table 7* for the features available in SPI1, SPI2 and SPI3.

SPI features ⁽¹⁾	SPI1	SPI2	SPI3
Hardware CRC calculation	Х	X	Х
Rx/Tx FIFO	Х	Х	Х
NSS pulse mode	Х	Х	Х
I2S mode	-	Х	Х
TI mode	Х	Х	Х

Table 7.STM32F303xB/STM32F303xC SPI/I2S implementation

3.22 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.23 Universal serial bus (USB)

The STM32F303xB/STM32F303xC devices embed an USB device peripheral compatible with the USB full-speed 12 Mbs. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and suspend/resume support. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator). The USB has a dedicated 512-bytes SRAM memory for data transmission and reception.



^{1.} X = supported.

3.24 Infrared Transmitter

The STM32F303xB/STM32F303xC devices provide an infrared transmitter solution. The solution is based on internal connections between TIM16 and TIM17 as shown in the figure below.

TIM17 is used to provide the carrier frequency and TIM16 provides the main signal to be sent. The infrared output signal is available on PB9 or PA13.

To generate the infrared remote control signals, TIM16 channel 1 and TIM17 channel 1 must be properly configured to generate correct waveforms. All standard IR pulse modulation modes can be obtained by programming the two timers output compare channels.

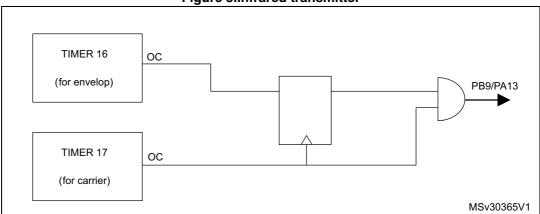


Figure 3.Infrared transmitter

3.25 Touch sensing controller (TSC)

The STM32F303xB/STM32F303xC devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 24 capacitive sensing channels distributed over 8 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

Table 8.Capacitive sensing GPIOs available on STM32F303xB/STM32F303xC devices

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
	TSC_G1_IO1	PA0		TSC_G5_IO1	PB3
1	TSC_G1_IO2	PA1	5	TSC_G5_IO2	PB4
'	TSC_G1_IO3	PA2	5	TSC_G5_IO3	PB6
	TSC_G1_IO4	PA3		TSC_G5_IO4	PB7
	TSC_G2_IO1	PA4		TSC_G6_IO1	PB11
2	TSC_G2_IO2	PA5	6	TSC_G6_IO2	PB12
	TSC_G2_IO3	PA6	0	TSC_G6_IO3	PB13
	TSC_G2_IO4	PA7		TSC_G6_IO4	PB14
	TSC_G3_IO1	PC5		TSC_G7_IO1	PE2
3	TSC_G3_IO2	PB0	7	TSC_G7_IO2	PE3
3	TSC_G3_IO3	PB1	,	TSC_G7_IO3	PE4
	TSC_G3_IO4	PB2		TSC_G7_IO4	PE5
	TSC_G4_IO1	PA9		TSC_G8_IO1	PD12
4	TSC_G4_IO2	PA10	8	TSC_G8_IO2	PD13
7	TSC_G4_IO3	PA13	0	TSC_G8_IO3	PD14
	TSC_G4_IO4	PA14		TSC_G8_IO4	PD15

Table 9.No. of capacitive sensing channels available on STM32F303xB/STM32F303xC devices

Analog I/O group	Number of capacitive sensing channels							
Alialog I/O group	STM32F303Vx	STM32F303Rx	STM32F303Cx					
G1	3	3	3					
G2	3	3	3					
G3	3	3	2					
G4	3	3	3					
G5	3	3	3					
G6	3	3	3					
G7	3	0	0					
G8	3	0	0					
Number of capacitive sensing channels	24	18	17					

DocID023353 Rev 8 28/138



3.26 Development support

3.26.1 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

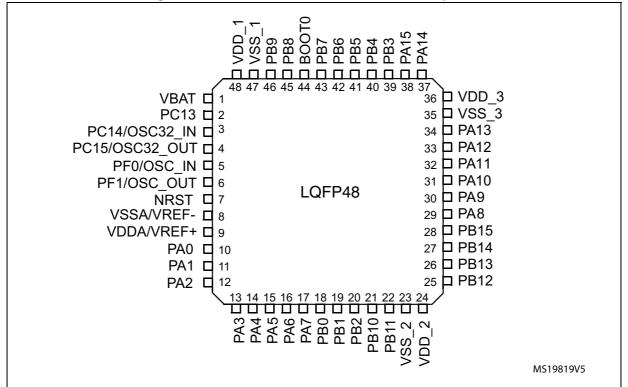
3.26.2 Embedded trace macrocell™

The ARM embedded trace macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F303xB/STM32F303xC through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using a high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.



4 Pinouts and pin description

Figure 4.STM32F303xB/STM32F303xC LQFP48 pinout



PB9 PB8 BOOT0 PB7 PB6 PB5 PB4 PB3 64 63 62 61 60 59 58 57 56 55 54 53 52 51 50 49 48 □ VDD_3 <u>_______</u> VBAT ☐ 1 47 USS 3 PC13 ☐ 2 46 🗖 PA13 PC14/OSC32_IN 🗖 3 45 PA12 PC15/OSC32 OUT ☐ 4 44 🗖 PA11 PF0/OSC IN ☐ 5 PF1/OSC_OUT ☐ 6 43 PA10 NRST ☐ 7 42 🏻 PA9 41 🗖 PA8 PC0 **□**8 LQFP64 PC1 **□** 9 40 PC9 PC2 ☐ 10 39 🗖 PC8 38 🗖 PC7 PC3 ☐ 11 VSSA/VREF- ☐ 12 37 🗖 PC6 36 PB15 VDDA ☐ 13 PA0 🗖 14 35 PB14 PA1 | 15 34 🗖 PB13 PA2 1 16 33 PB12 18 19 20 21 22 23 24 25 26 27 28 29 30 31 32 VDD 4 G ai18484V4

Figure 5.STM32F303xB/STM32F303xC LQFP64 pinout

Figure 6.STM32F303xB/STM32F303xC LQFP100 pinout

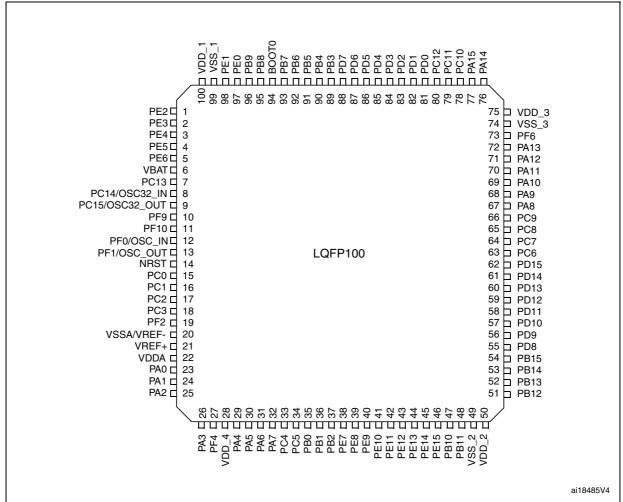


Table 10.Legend/abbreviations used in the pinout table

Na	me	Abbreviation	Definition			
Pin r	name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name				
		S	Supply pin			
Pin	type	I	Input only pin			
		I/O	Input / output pin			
		FT	5 V tolerant I/O			
		FTf	5 V tolerant I/O, FM+ capable			
I/O otr	ucture	TTa	3.3 V tolerant I/O directly connected to ADC			
1/0 Str	ucture	TC Standard 3.3V I/O				
		В	Dedicated BOOT0 pin			
		RST	Bidirectional reset pin with embedded weak pull-up resistor			
No	tes	Unless otherwis	e specified by a note, all I/Os are set as floating inputs during and after reset			
B:	Alternate functions	Fu	nctions selected through GPIOx_AFR registers			
Pin functions	Additional functions	Functions directly selected/enabled through peripheral registers				



Table 11.STM32F303xB/STM32F303xC pin definitions

Pir	n numb	er	Pin name		<u>₽</u>		Pin functions	
LQFP100	LQFP64	LQFP48	(function after reset)	Pin type	I/O structure	I/O structu	Alternate functions	Additional functions
1	1	-	PE2	I/O	FT	(1)	TRACECK, TIM3_CH1, TSC_G7_IO1, EVENTOUT	-
2	-	-	PE3	I/O	FT	(1)	TRACED0, TIM3_CH2, TSC_G7_IO2, EVENTOUT	-
3	-	-	PE4	I/O	FT	(1)	TRACED1, TIM3_CH3, TSC_G7_IO3, EVENTOUT	-
4	-	-	PE5	I/O	FT	(1)	TRACED2, TIM3_CH4, TSC_G7_IO4, EVENTOUT	-
5	-	-	PE6	I/O	FT	(1)	TRACED3, EVENTOUT	WKUP3, RTC_TAMP3
6	1	1	V _{BAT}	S	-	-	Backup p	power supply
7	2	2	PC13 ⁽²⁾	I/O	TC	-	TIM1_CH1N	WKUP2, RTC_TAMP1, RTC_TS, RTC_OUT
8	3	3	PC14 ⁽²⁾ OSC32_IN (PC14)	I/O	TC	-	-	OSC32_IN
9	4	4	PC15 ⁽²⁾ OSC32_ OUT (PC15)	I/O	TC	-	-	OSC32_OUT
10	-	-	PF9	I/O	FT	(1)	TIM15_CH1, SPI2_SCK, EVENTOUT	-
11	-	-	PF10	I/O	FT	(1)	TIM15_CH2, SPI2_SCK, EVENTOUT	-
12	5	5	PF0- OSC_IN (PF0)	1/0	FTf	-	TIM1_CH3N, I2C2_SDA,	OSC_IN
13	6	6	PF1- OSC_OUT (PF1)	I/O	FTf	-	I2C2_SCL	OSC_OUT
14	7	7	NRST	I/O	RST		Device reset input / inter	rnal reset output (active low)
15	8	-	PC0	I/O	TTa	(1)	EVENTOUT	ADC12_IN6, COMP7_INM
16	9	-	PC1	I/O	TTa	(1)	EVENTOUT	ADC12_IN7, COMP7_INP
17	10	-	PC2	I/O	TTa	(1)	COMP7_OUT, EVENTOUT	ADC12_IN8
18	11	1	PC3	I/O	TTa	(1)	TIM1_BKIN2, EVENTOUT	ADC12_IN9
19	-	-	PF2	I/O	TTa	(1)	EVENTOUT	ADC12_IN10
20	12	8	VSSA/ VREF-	S	-	-	Analog ground/Negative reference voltage	
21	-	-	VREF+ ⁽³⁾	S	-	-	Positive reference voltage	
22	-	-	VDDA	S	-	-	Analog p	power supply
-	13	9	VDDA/ VREF+	S	-	-	Analog power supply/Positive reference voltage	

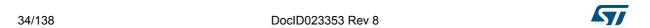


Table 11.STM32F303xB/STM32F303xC pin definitions (continued)

Pir	n numb		Pin name				Pin fu	unctions
LQFP100	LQFP64	LQFP48	(function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
23	14	10	PA0	I/O	ТТа	-	USART2_CTS, TIM2_CH1_ETRTIM8_BKIN, TIM8_ETR,TSC_G1_IO1, COMP1_OUT, EVENTOUT	ADC1_IN1, COMP1_INM, RTC_ TAMP2, WKUP1, COMP7_INP
24	15	11	PA1	I/O	TTa	1	USART2_RTS, TIM2_CH2, TSC_G1_IO2, TIM15_CH1N, RTC_REFIN, EVENTOUT	ADC1_IN2, COMP1_INP, OPAMP1_VINP, OPAMP3_VINP
25	16	12	PA2	I/O	TTa	-	USART2_TX, TIM2_CH3, TIM15_CH1, TSC_G1_IO3, COMP2_OUT, EVENTOUT	ADC1_IN3, COMP2_INM, OPAMP1_VOUT
26	17	13	PA3	I/O	TTa	-	USART2_RX, TIM2_CH4, TIM15_CH2, TSC_G1_IO4, EVENTOUT	ADC1_IN4, OPAMP1_VINP, COMP2_INP, OPAMP1_VINM
27	18	-	PF4	I/O	TTa	(1)	COMP1_OUT, EVENTOUT	ADC1_IN5
28	19	-	VDD_4	S	-	-	-	-
29	20	14	PA4	I/O	TTa	-	SPI1_NSS, SPI3_NSS, I2S3_WS, USART2_CK, TSC_G2_IO1, TIM3_CH2, EVENTOUT	ADC2_IN1, DAC1_OUT1, OPAMP4_VINP, COMP1_INM, COMP2_INM, COMP3_INMCOMP4_INM, COMP5_INMCOMP6_INM,CO MP7_INM
30	21	15	PA5	I/O	ТТа	-	SPI1_SCK, TIM2_CH1_ETR, TSC_G2_IO2, EVENTOUT	ADC2_IN2, DAC1_OUT2 OPAMP1_VINP, OPAMP2_VINM, OPAMP3_VINP COMP1_INM, COMP2_INM, COMP3_INMCOMP4_INM,CO MP5_INMCOMP6_INM, COMP7_INM
31	22	16	PA6	I/O	TTa	-	SPI1_MISO, TIM3_CH1, TIM8_BKIN, TIM1_BKIN, TIM16_CH1, COMP1_OUT, TSC_G2_IO3, EVENTOUT	ADC2_IN3, OPAMP2_VOUT
32	23	17	PA7	I/O	TTa	-	SPI1_MOSI, TIM3_CH2, TIM17_CH1, TIM1_CH1N, TIM8_CH1NTSC_G2_IO4, COMP2_OUT, EVENTOUT	ADC2_IN4, COMP2_INP, OPAMP2_VINP, OPAMP1_VINP
33	24	-	PC4	I/O	TTa	(1)	USART1_TX, EVENTOUT	ADC2_IN5
34	25	-	PC5	I/O	TTa	(1)	USART1_RX, TSC_G3_IO1, EVENTOUT	ADC2_IN11, OPAMP2_VINM, OPAMP1_VINM
35	26	18	PB0	I/O	TTa	-	TIM3_CH3, TIM1_CH2N, TIM8_CH2N,TSC_G3_IO2, EVENTOUT	ADC3_IN12, COMP4_INP, OPAMP3_VINPOPAMP2_VINP



Table 11.STM32F303xB/STM32F303xC pin definitions (continued)

Pir	n numb	er	Pin name				Pin fu	unctions
LQFP100	LQFP64	LQFP48	(function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
36	27	19	PB1	I/O	TTa	-	TIM3_CH4, TIM1_CH3N , TIM8_CH3NCOMP4_OUT, TSC_G3_IO3, EVENTOUT	ADC3_IN1, OPAMP3_VOUT-
37	28	20	PB2	I/O	TTa	-	TSC_G3_IO4, EVENTOUT	ADC2_IN12, COMP4_INM, OPAMP3_VINM
38	-	-	PE7	I/O	TTa	(1)	TIM1_ETR, EVENTOUT	ADC3_IN13, COMP4_INP
39	-	-	PE8	I/O	TTa	(1)	TIM1_CH1N, EVENTOUT	COMP4_INM, ADC34_IN6
40	-	-	PE9	I/O	TTa	(1)	TIM1_CH1, EVENTOUT	ADC3_IN2
41	-	•	PE10	I/O	TTa	(1)	TIM1_CH2N, EVENTOUT	ADC3_IN14
42	-	•	PE11	I/O	TTa	(1)	TIM1_CH2, EVENTOUT	ADC3_IN15
43	-	-	PE12	I/O	TTa	(1)	TIM1_CH3N, EVENTOUT	ADC3_IN16
44	-	-	PE13	I/O	TTa	(1)	TIM1_CH3, EVENTOUT	ADC3_IN3
45	-	-	PE14	I/O	TTa	(1)	TIM1_CH4, TIM1_BKIN2, EVENTOUT	ADC4_IN1
46	-	-	PE15	I/O	TTa	(1)	USART3_RX, TIM1_BKIN, EVENTOUT	ADC4_IN2
47	29	21	PB10	I/O	TTa	-	USART3_TX, TIM2_CH3, TSC_SYNC, EVENTOUT	COMP5_INM,OPAMP4_VINM, OPAMP3_VINM
48	30	22	PB11	I/O	TTa	-	USART3_RX, TIM2_CH4, TSC_G6_IO1, EVENTOUT	COMP6_INP, OPAMP4_VINP
49	31	23	VSS_2	S	-	-	Digita	al ground
50	32	24	VDD_2	S	-	-	Digital p	ower supply
51	33	25	PB12	I/O	ТТа	-	SPI2_NSS,I2S2_WS, I2C2_SMBA, USART3_CK, TIM1_BKIN, TSC_G6_IO2, EVENTOUT	ADC4_IN3, COMP3_INM,OPAMP4_VOUT
52	34	26	PB13	I/O	TTa	-	SPI2_SCK,I2S2_CK, USART3_CTS, TIM1_CH1N, TSC_G6_IO3, EVENTOUT	ADC3_IN5, COMP5_INP,OPAMP4_VINP, OPAMP3_VINP
53	35	27	PB14	I/O	ТТа	-	SPI2_MISO, I2S2ext_SD, USART3_RTS, TIM1_CH2N, TIM15_CH1, TSC_G6_IO4, EVENTOUT	COMP3_INP,ADC4_IN4, OPAMP2_VINP
54	36	28	PB15	I/O	TTa	-	SPI2_MOSI, I2S2_SD, TIM1_CH3N, RTC_REFIN, TIM15_CH1N, TIM15_CH2, EVENTOUT	ADC4_IN5, COMP6_INM
55	-	-	PD8	I/O	TTa	(1)	USART3_TX, EVENTOUT	ADC4_IN12, OPAMP4_VINM
56	-	-	PD9	I/O	TTa	(1)	USART3_RX, EVENTOUT	ADC4_IN13
57	-	-	PD10	I/O	TTa	(1)	USART3_CK, EVENTOUT	ADC34_IN7, COMP6_INM
58	-	-	PD11	I/O	TTa	(1)	USART3_CTS, EVENTOUT	ADC34_IN8, COMP6_INP, OPAMP4_VINP

Table 11.STM32F303xB/STM32F303xC pin definitions (continued)

Pir	n numb	oer	Pin name	o o	ure		Pin fu	unctions
LQFP100	LQFP64	LQFP48	(function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
59	-	-	PD12	I/O	TTa	(1)	USART3_RTS, TIM4_CH1, TSC_G8_IO1, EVENTOUT	ADC34_IN9, COMP5_INP
60	-	-	PD13	I/O	TTa	(1)	TIM4_CH2, TSC_G8_IO2, EVENTOUT	ADC34_IN10,COMP5_INM
61	-	-	PD14	I/O	TTa	(1)	TIM4_CH3, TSC_G8_IO3, EVENTOUT	COMP3_INP,ADC34_IN11,OPA MP2_VINP
62	-	-	PD15	I/O	TTa	(1)	SPI2_NSS, TIM4_CH4, TSC_G8_IO4, EVENTOUT	COMP3_INM
63	37	-	PC6	I/O	FT	(1)	I2S2_MCK, COMP6_OUT, TIM8_CH1, TIM3_CH1, EVENTOUT	-
64	38	-	PC7	I/O	FT	(1)	I2S3_MCK, TIM8_CH2, TIM3_CH2, COMP5_OUT, EVENTOUT	-
65	39	-	PC8	I/O	FT	(1)	TIM8_CH3, TIM3_CH3, COMP3_OUT, EVENTOUT	-
66	40	-	PC9	I/O	FT	(1)	TIM8_CH4, TIM8_BKIN2,TIM3_CH4, I2S_CKIN, EVENTOUT	-
67	41	29	PA8	I/O	FT	-	I2C2_SMBA,I2S2_MCK, USART1_CK, TIM1_CH1, TIM4_ETR, MCO, COMP3_OUT, EVENTOUT	-
68	42	30	PA9	I/O	FTf	-	I2C2_SCL,I2S3_MCK, USART1_TX, TIM1_CH2, TIM2_CH3, TIM15_BKIN, TSC_G4_IO1, COMP5_OUT, EVENTOUT	-
69	43	31	PA10	I/O	FTf	ı	I2C2_SDA, USART1_RX, TIM1_CH3, TIM2_CH4, TIM8_BKIN, TIM17_BKIN, TSC_G4_IO2, COMP6_OUT, EVENTOUT	-
70	44	32	PA11	I/O	FT	-	USART1_CTS, USB_DM, CAN_RX, TIM1_CH1N, TIM1_CH4, TIM1_BKIN2, TIM4_CH1, COMP1_OUT, EVENTOUT	-
71	45	33	PA12	I/O	FT	USART1_RTS, USB_DP, CAN_TX, TIM1_CH2N, - TIM1_ETR, TIM4_CH2, TIM16_CH1, COMP2_OUT, EVENTOUT		-



Table 11.STM32F303xB/STM32F303xC pin definitions (continued)

Pir	n numb		Pin name				Pin fu	inctions
LQFP100	LQFP64	LQFP48	(function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
72	46	34	PA13	I/O	FT	-	USART3_CTS, TIM4_CH3, TIM16_CH1N, TSC_G4_IO3, IR_OUT, SWDIO-JTMS, EVENTOUT	-
73	-	-	PF6	I/O	FTf	(1)	I2C2_SCL, USART3_RTS, TIM4_CH4, EVENTOUT	-
74	47	35	VSS_3	S	-	-	Gr	ound
75	48	36	VDD_3	S	_	-	Digital po	ower supply
76	49	37	PA14	I/O	FTf	-	I2C1_SDA, USART2_TX, TIM8_CH2,TIM1_BKIN, TSC_G4_IO4,SWCLK-JTCK, EVENTOUT	-
77	50	38	PA15	I/O	FTf	-	I2C1_SCL, SPI1_NSS, SPI3_NSS, I2S3_WS, JTDI, USART2_RX, TIM1_BKIN, TIM2_CH1_ETR, TIM8_CH1, EVENTOUT	-
78	51	-	PC10	I/O	FT	(1)	SPI3_SCK, I2S3_CK, USART3_TX, UART4_TX, TIM8_CH1N, EVENTOUT	-
79	52	-	PC11	I/O	FT	(1)	SPI3_MISO, I2S3ext_SD, USART3_RX, UART4_RX, TIM8_CH2N, EVENTOUT	-
80	53	-	PC12	I/O	FT	(1)	SPI3_MOSI, I2S3_SD, USART3_CK, UART5_TX, TIM8_CH3N, EVENTOUT	-
81	-	-	PD0	I/O	FT	(1)	CAN_RX, EVENTOUT	-
82	-	-	PD1	I/O	FT	(1)	CAN_TX, TIM8_CH4, TIM8_BKIN2,EVENTOUT	-
83	54	-	PD2	I/O	FT	(1)	UART5_RX, TIM3_ETR, TIM8_BKIN, EVENTOUT	-
84	-	-	PD3	I/O	FT	(1)	USART2_CTS, TIM2_CH1_ETR, EVENTOUT	-
85	-	-	PD4	I/O	FT	(1)	USART2_RTS, TIM2_CH2, EVENTOUT	
86	-	-	PD5	I/O	FT	(1)	USART2_TX, EVENTOUT	-
87	-	-	PD6	I/O	FT	(1)	USART2_RX, TIM2_CH4, EVENTOUT	-
88	-	-	PD7	I/O	FT	(1)	USART2_CK, TIM2_CH3, EVENTOUT	



Table 11.STM32F303xB/STM32F303xC pin definitions (continued)

Pir	n numb	er	Pin name	o o	a. n		Pin fu	unctions	
LQFP100	LQFP64	LQFP48	(function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions	
89	55	39	PB3	I/O	FT	-	SPI3_SCK, I2S3_CK, SPI1_SCK, USART2_TX, TIM2_CH2, TIM3_ETR, TIM4_ETR, TIM8_CH1N, TSC_G5_IO1, JTDO- TRACESWO, EVENTOUT	-	
90	56	40	PB4	I/O	FT	-	SPI3_MISO, I2S3ext_SD, SPI1_MISO, USART2_RX, TIM3_CH1, TIM16_CH1, TIM17_BKIN, TIM8_CH2N, TSC_G5_IO2, NJTRST, EVENTOUT	-	
91	57	41	PB5	I/O	FT	-	SPI3_MOSI, SPI1_MOSI, I2S3_SD, I2C1_SMBA, USART2_CK, TIM16_BKIN, TIM3_CH2, TIM8_CH3N, TIM17_CH1, EVENTOUT	-	
92	58	42	PB6	I/O	FTf	-	I2C1_SCL, USART1_TX, TIM16_CH1N, TIM4_CH1, TIM8_CH1,TSC_G5_IO3, TIM8_ETR, TIM8_BKIN2, EVENTOUT	-	
93	59	43	PB7	1/0	FTf	1	I2C1_SDA, USART1_RX, TIM3_CH4, TIM4_CH2, TIM17_CH1N, TIM8_BKIN, TSC_G5_IO4, EVENTOUT	-	
94	60	44	воото	ı	В	-	Boot mem	ory selection	
95	61	45	PB8	1/0	FTf	1	I2C1_SCL, CAN_RX, TIM16_CH1, TIM4_CH3, TIM8_CH2, TIM1_BKIN, TSC_SYNC, COMP1_OUT, EVENTOUT	-	
96	62	46	PB9	I/O	FTf	-	I2C1_SDA, CAN_TX, TIM17_CH1, TIM4_CH4, TIM8_CH3, IR_OUT, COMP2_OUT, EVENTOUT	-	
97	-	-	PE0	I/O	FT	(1)	USART1_TX, TIM4_ETR, TIM16_CH1, EVENTOUT	-	
98	-	-	PE1	I/O	FT	(1)	USART1_RX, TIM17_CH1, EVENTOUT	-	
99	63	47	VSS_1	S	-	-	Gr	round	
100	64	48	VDD_1	S	-	-	Digital power supply		

Function availability depends on the chosen device.
 When using the small packages (48 and 64 pin packages), the GPIO pins which are not present on these packages, must not be configured in analog mode.



- PC13, PC14 and PC15 are supplied through the power switch. Since the switch sinks only a limited amount of current (3 mA), the use of GPIO PC13 to PC15 in output mode is limited:

 The speed should not exceed 2 MHz with a maximum load of 30 pF
 These GPIOs must not be used as current sources (e.g. to drive an LED).

After the first backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the Backup registers which is not reset by the main reset. For details on how to manage these GPIOs, refer to the Battery backup domain and BKP register description sections in the RM0316 reference manual.

3. The VREF+ functionality is available only on the 100 pin package. On the 64-pin and 48-pin packages, the VREF+ is internally connected to VDDA.





Table 12.Alternate functions for port A

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF14	AF15
PA0	-	TIM2_ CH1_ ETR	-	TSC_ G1_IO1	-	-	-	USART2 _CTS	COMP1 _OUT	TIM8_ BKIN	TIM8_ ETR	-	-	-	EVENT OUT
PA1	RTC_ REFIN	TIM2_ CH2	-	TSC_ G1_IO2	-	-	-	USART2 _RTS		TIM15_ CH1N	-	-	-	-	EVENT OUT
PA2	-	TIM2_ CH3	-	TSC_ G1_IO3	-	-	-	USART2 _TX	COMP2 _OUT	TIM15_ CH1	-	-	-	-	EVENT OUT
PA3	-	TIM2_ CH4	-	TSC_ G1_IO4	-	-	-	USART2 _RX	-	TIM15_ CH2	-	-	-	-	EVENT OUT
PA4	-	-	TIM3_ CH2	TSC_ G2_IO1	-	SPI1_ NSS	SPI3_NSS, I2S3_WS	USART2 _CK	-	-	-	-	-	-	EVENT OUT
PA5	-	TIM2_ CH1_ ETR	-	TSC_ G2_IO2	-	SPI1_ SCK	-	-	-	-	-	-	-	-	EVENT OUT
PA6	-	TIM16_ CH1	TIM3_ CH1	TSC_ G2_IO3	TIM8_ BKIN	SPI1_ MISO	TIM1_BKIN	-	COMP1 _OUT	-	-	-	-	-	EVENT OUT
PA7	-	TIM17_ CH1	TIM3_ CH2	TSC_ G2_IO4	TIM8_ CH1N	SPI1_ MOSI	TIM1_CH1N	-	COMP2 _OUT	-	-	-	-	-	EVENT OUT
PA8	мсо	-	-	-	I2C2_ SMBA	I2S2_ MCK	TIM1_CH1	USART1 _CK	COMP3 _OUT	-	TIM4_ ETR	-	-	-	EVENT OUT
PA9	-	-	-	TSC_ G4_IO1	I2C2_ SCL	I2S3_ MCK	TIM1_CH2	USART1 _TX	COMP5 _OUT	TIM15_ BKIN	TIM2_ CH3	-	-	-	EVENT OUT
PA10	-	TIM17_ BKIN	-	TSC_ G4_IO2	I2C2_ SDA	-	TIM1_CH3	USART1 _RX	COMP6 _OUT	-	TIM2_ CH4	TIM8_BKI N	-	-	EVENT OUT
PA11		-	-	-	-	-	TIM1_CH1N	USART1 _CTS	COMP1 _OUT	CAN_RX	TIM4_ CH1	TIM1_CH4	TIM1_ BKIN2	USB_ DM	EVENT OUT

Pinouts and pin description

Table 12.Alternate functions for port A (continued)

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF14	AF15
PA12	-	TIM16_ CH1	-	-	-	-	TIM1_CH2N	USART1 _RTS	COMP2 _OUT	CAN_TX	TIM4_ CH2	TIM1_ETR	-	USB_ DP	EVENT OUT
PA13	SWDIO -JTMS	TIM16_ CH1N	-	TSC_ G4_IO3	-	IR_ OUT	-	USART3 _CTS	-	-	TIM4_ CH3	-	-	-	EVENT OUT
PA14	SWCLK -JTCK	-	-	TSC_ G4_IO4	I2C1_ SDA	TIM8_ CH2	TIM1_BKIN	USART2 _TX	-	-	-	-	-	-	EVENT OUT
PA15	JTDI	TIM2_ CH1_ ETR	TIM8_ CH1	-	I2C1_ SCL	SPI1_ NSS	SPI3_NSS, I2S3_WS	USART2 _RX	-	TIM1_ BKIN	-	-	-	-	EVENT OUT



Table 13.Alternate functions for port B

					1								
Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF12	AF15
PB0	-	-	TIM3_ CH3	TSC_ G3_IO2	TIM8_ CH2N	-	TIM1_CH2N	-	-	-	-	-	EVENT OUT
PB1	-	-	TIM3_ CH4	TSC_ G3_IO3	TIM8_ CH3N	-	TIM1_CH3N	-	COMP4_ OUT	-	-	-	EVENT OUT
PB2	-	-	-	TSC_ G3_IO4	-	-	-	-	-	-	-	-	EVENT OUT
PB3	JTDO- TRACES WO	TIM2_ CH2	TIM4_ ETR	TSC_ G5_IO1	TIM8_ CH1N	SPI1_ SCK	SPI3_SCK, I2S3_CK	USART2_ TX	-	-	TIM3_ ETR	-	EVENT OUT
PB4	NJTRST	TIM16_ CH1	TIM3_ CH1	TSC_ G5_IO2	TIM8_ CH2N	SPI1_ MISO	SPI3_MISO, I2S3ext_SD	USART2_ RX	-	-	TIM17_ BKIN	-	EVENT OUT
PB5	-	TIM16_ BKIN	TIM3_ CH2	TIM8_ CH3N	I2C1_ SMBA	SPI1_ MOSI	SPI3_MOSI, I2S3_SD	USART2_ CK	-	-	TIM17_ CH1	-	EVENT OUT
PB6	-	TIM16_ CH1N	TIM4_ CH1	TSC_ G5_IO3	I2C1_SCL	TIM8_CH1	TIM8_ ETR	USART1_ TX	-	-	TIM8_ BKIN2	-	EVENT OUT
PB7	-	TIM17_ CH1N	TIM4_ CH2	TSC_ G5_IO4	I2C1_ SDA	TIM8_ BKIN	-	USART1_ RX	-	-	TIM3_ CH4	-	EVENT OUT
PB8	-	TIM16_ CH1	TIM4_ CH3	TSC_ SYNC	I2C1_SCL	-	-	-	COMP1_ OUT	CAN_RX	TIM8_ CH2	TIM1_ BKIN	EVENT OUT
PB9	-	TIM17_ CH1	TIM4_ CH4		I2C1_ SDA	-	IR_OUT	-	COMP2_ OUT	CAN_TX	TIM8_ CH3	-	EVENT OUT
PB10	-	TIM2_ CH3	-	TSC_ SYNC	-	-	-	USART3_ TX	-	-	-	-	EVENT OUT
PB11	-	TIM2_ CH4	-	TSC_ G6_IO1	-	-	-	USART3_ RX	-	-	-	-	EVENT OUT
PB12	-	-	-	TSC_ G6_IO2	I2C2_ SMBA	SPI2_NSS, I2S2_WS	TIM1_ BKIN	USART3_ CK	-	-	-	-	EVENT OUT

Pinouts and pin description

Table 13.Alternate functions for port B (continued)

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF12	AF15
PB13	-	-	-	TSC_ G6_IO3	-	SPI2_SCK, I2S2_CK	TIM1_ CH1N	USART3_ CTS	-	-	-	-	EVENT OUT
PB14	-	TIM15_ CH1	-	TSC_ G6_IO4	-	SPI2_MISO, I2S2ext_SD	TIM1_ CH2N	USART3_ RTS	-	-	-	-	EVENT OUT
PB15	RTC_ REFIN	TIM15_ CH2	TIM15_ CH1N	-	TIM1_ CH3N	SPI2_MOSI, I2S2_SD	-	-	-	-	-	-	EVENT OUT



Table 14.Alternate functions for port C

Port & Pin Name	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PC0	EVENTOUT	-	-	-	-	-	-
PC1	EVENTOUT	-	-	-	-	-	-
PC2	EVENTOUT	-	COMP7_OUT	-	-	-	-
PC3	EVENTOUT	-	-	-	-	TIM1_BKIN2	-
PC4	EVENTOUT	-	-	-	-	-	USART1_TX
PC5	EVENTOUT	-	TSC_G3_IO1	-	-	-	USART1_RX
PC6	EVENTOUT	TIM3_CH1	-	TIM8_CH1	-	I2S2_MCK	COMP6_OUT
PC7	EVENTOUT	TIM3_CH2	-	TIM8_CH2	-	I2S3_MCK	COMP5_OUT
PC8	EVENTOUT	TIM3_CH3	-	TIM8_CH3	-	-	COMP3_OUT
PC9	EVENTOUT	TIM3_CH4	-	TIM8_CH4	I2S_CKIN	TIM8_BKIN2	-
PC10	EVENTOUT	-	-	TIM8_CH1N	UART4_TX	SPI3_SCK, I2S3_CK	USART3_TX
PC11	EVENTOUT	-	-	TIM8_CH2N	UART4_RX	SPI3_MISO, I2S3ext_SD	USART3_RX
PC12	EVENTOUT	-	-	TIM8_CH3N	UART5_TX	SPI3_MOSI, I2S3_SD	USART3_CK
PC13	-	-	-	TIM1_CH1N	-	-	-
PC14	-	-	-	-	-	-	-
PC15	-	-	-	-	-	-	-

Table 15.Alternate functions for port D

Port & Pin Name	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PD0	EVENTOUT	-	-	-	-	-	CAN_RX
PD1	EVENTOUT	-	-	TIM8_CH4	-	TIM8_BKIN2	CAN_TX
PD2	EVENTOUT	TIM3_ETR	-	TIM8_BKIN	UART5_RX	-	-
PD3	EVENTOUT	TIM2_CH1_ETR	-	-	-	-	USART2_CTS
PD4	EVENTOUT	TIM2_CH2	-	-	-	-	USART2_RTS
PD5	EVENTOUT	-	-	-	-	-	USART2_TX
PD6	EVENTOUT	TIM2_CH4	-	-	-	-	USART2_RX
PD7	EVENTOUT	TIM2_CH3	-	-	-	-	USART2_CK
PD8	EVENTOUT	-	-	-	-	-	USART3_TX
PD9	EVENTOUT	-	-	-	-	-	USART3_RX
PD10	EVENTOUT	-	-	-	-	-	USART3_CK
PD11	EVENTOUT	-	-	-	-	-	USART3_CTS
PD12	EVENTOUT	TIM4_CH1	TSC_G8_IO1	-	-	-	USART3_RTS
PD13	EVENTOUT	TIM4_CH2	TSC_G8_IO2	-	-	-	-
PD14	EVENTOUT	TIM4_CH3	TSC_G8_IO3	-	-	-	-
PD15	EVENTOUT	TIM4_CH4	TSC_G8_IO4	-	-	SPI2_NSS	-





Table 16.Alternate functions for port E

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF6	AF7
PE0	-	EVENTOUT	TIM4_ETR	-	TIM16_CH1	-	USART1_TX
PE1	-	EVENTOUT	-	-	TIM17_CH1	-	USART1_RX
PE2	TRACECK	EVENTOUT	TIM3_CH1	TSC_G7_IO1	-	-	-
PE3	TRACED0	EVENTOUT	TIM3_CH2	TSC_G7_IO2	-	-	-
PE4	TRACED1	EVENTOUT	TIM3_CH3	TSC_G7_IO3	-	-	-
PE5	TRACED2	EVENTOUT	TIM3_CH4	TSC_G7_IO4	-	-	-
PE6	TRACED3	EVENTOUT		-	-	-	-
PE7	-	EVENTOUT	TIM1_ETR	-	-	-	-
PE8	-	EVENTOUT	TIM1_CH1N	-	-	-	-
PE9	-	EVENTOUT	TIM1_CH1	-	-	-	-
PE10	-	EVENTOUT	TIM1_CH2N	-	-	-	-
PE11	-	EVENTOUT	TIM1_CH2	-	-	-	-
PE12	-	EVENTOUT	TIM1_CH3N	-	-	-	-
PE13	-	EVENTOUT	TIM1_CH3	-	-	-	-
PE14	-	EVENTOUT	TIM1_CH4	-	-	TIM1_BKIN2	-
PE15	-	EVENTOUT	TIM1_BKIN	-	-	-	USART3_RX

Table 17.Alternate	functions	for	port	F
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Port & Pin Name	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PF0	-	-	-	I2C2_SDA	-	TIM1_CH3N	-
PF1	-	-	-	I2C2_SCL	-	-	-
PF2	EVENTOUT	-	-	-	-	-	-
PF4	EVENTOUT	COMP1_OUT	-	-	-	-	-
PF6	EVENTOUT	TIM4_CH4	-	I2C2_SCL	-	-	USART3_RTS
PF9	EVENTOUT	-	TIM15_CH1	-	SPI2_SCK	-	-
PF10	EVENTOUT	-	TIM15_CH2	-	SPI2_SCK	-	-

5 Memory mapping

0x5000 07FF AHB3 0xFFFF FFFF 0x5000 0000 Cortex-M4 Reserved with FPU 7 0x4800 1800 Internal Peripherals AHB2 0xE000 0000 0x4800 0000 Reserved 6 0x4002 43FF AHB1 0xC000 0000 0x4002 0000 Reserved 5 0x4001 6C00 APB2 0xA000 0000 0x4001 0000 Reserved 4 0x4000 A000 APB1 0x8000 0000 0x4000 0000 3 ,0x1FFF FFFF Option bytes 0x6000 0000 0x1FFF F800 System memory 2 0x1FFF D800 Reserved 0x1000 2000 0x4000 0000 Peripherals **CCM RAM** 0x1000 0000 Reserved 1 0x0804 0000 0x2000 0000 **SRAM** Flash memory 0x0800 0000 0 CODE Reserved 0x0004 0000 Flash, system 0x0000 0000 memory or SRAM, depending on BOOT configuration Reserved 0x0000 0000 MSv30355V2

Figure 7.STM32F303xB/STM32F303xC memory map

Table 18.STM32F303xB/STM32F303xC memory map, peripheral register boundary addresses

Bus	Boundary address	Size (bytes)	Peripheral
AHB3	0x5000 0400 - 0x5000 07FF	1 K	ADC3 - ADC4
ANDS	0x5000 0000 - 0x5000 03FF	1 K	ADC1 - ADC2
	0x4800 1800 - 0x4FFF FFFF	~132 M	Reserved
	0x4800 1400 - 0x4800 17FF	1 K	GPIOF
	0x4800 1000 - 0x4800 13FF	1 K	GPIOE
AHB2	0x4800 0C00 - 0x4800 0FFF	1 K	GPIOD
	0x4800 0800 - 0x4800 0BFF	1 K	GPIOC
	0x4800 0400 - 0x4800 07FF	1 K	GPIOB
	0x4800 0000 - 0x4800 03FF	1 K	GPIOA
	0x4002 4400 - 0x47FF FFFF	~128 M	Reserved
	0x4002 4000 - 0x4002 43FF	1 K	TSC
	0x4002 3400 - 0x4002 3FFF	3 K	Reserved
	0x4002 3000 - 0x4002 33FF	1 K	CRC
AHB1	0x4002 2400 - 0x4002 2FFF	3 K	Reserved
	0x4002 2000 - 0x4002 23FF	1 K	Flash interface
	0x4002 1400 - 0x4002 1FFF	3 K	Reserved
	0x4002 1000 - 0x4002 13FF	1 K	RCC
	0x4002 0800 - 0x4002 0FFF	2 K	Reserved
	0x4002 0400 - 0x4002 07FF	1 K	DMA2
	0x4002 0000 - 0x4002 03FF	1 K	DMA1
	0x4001 8000 - 0x4001 FFFF	32 K	Reserved
	0x4001 4C00 - 0x4001 7FFF	13 K	Reserved
	0x4001 4800 - 0x4001 4BFF	1 K	TIM17
AHB1	0x4001 4400 - 0x4001 47FF	1 K	TIM16
	0x4001 4000 - 0x4001 43FF	1 K	TIM15
	0x4001 3C00 - 0x4001 3FFF	1 K	Reserved
	0x4001 3800 - 0x4001 3BFF	1 K	USART1
APB2	0x4001 3400 - 0x4001 37FF	1 K	TIM8
	0x4001 3000 - 0x4001 33FF	1 K	SPI1
	0x4001 2C00 - 0x4001 2FFF	1 K	TIM1
	0x4001 0800 - 0x4001 2BFF	9 K	Reserved
	0x4001 0400 - 0x4001 07FF	1 K	EXTI
	0x4001 0000 - 0x4001 03FF	1 K	SYSCFG + COMP + OPAMP

Table 18.STM32F303xB/STM32F303xC memory map, peripheral register boundary addresses (continued)

Bus	Boundary address	Size (bytes)	Peripheral
	0x4000 8000 - 0x4000 FFFF	32 K	Reserved
	0x4000 7800 - 0x4000 7FFF	2 K	Reserved
	0x4000 7400 - 0x4000 77FF	1 K	DAC (dual)
	0x4000 7000 - 0x4000 73FF	1 K	PWR
	0x4000 6800 - 0x4000 6FFF	2 K	Reserved
	0x4000 6400 - 0x4000 67FF	1 K	bxCAN
	0x4000 6000 - 0x4000 63FF	1 K	USB SRAM 512 bytes
	0x4000 5C00 - 0x4000 5FFF	1 K	USB device FS
	0x4000 5800 - 0x4000 5BFF	1 K	I2C2
	0x4000 5400 - 0x4000 57FF	1 K	I2C1
	0x4000 5000 - 0x4000 53FF	1 K	UART5
	0x4000 4C00 - 0x4000 4FFF	1 K	UART4
	0x4000 4800 - 0x4000 4BFF	1 K	USART3
	0x4000 4400 - 0x4000 47FF	1 K	USART2
APB1	0x4000 4000 - 0x4000 43FF	1 K	I2S3ext
AFDI	0x4000 3C00 - 0x4000 3FFF	1 K	SPI3/I2S3
	0x4000 3800 - 0x4000 3BFF	1 K	SPI2/I2S2
	0x4000 3400 - 0x4000 37FF	1 K	I2S2ext
	0x4000 3000 - 0x4000 33FF	1 K	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 K	WWDG
	0x4000 2800 - 0x4000 2BFF	1 K	RTC
	0x4000 1800 - 0x4000 27FF	4 K	Reserved
	0x4000 1400 - 0x4000 17FF	1 K	TIM7
	0x4000 1000 - 0x4000 13FF	1 K	TIM6
	0x4000 0C00 - 0x4000 0FFF	1 K	Reserved
	0x4000 0800 - 0x4000 0BFF	1 K	TIM4
	0x4000 0400 - 0x4000 07FF	1 K	TIM3
	0x4000 0000 - 0x4000 03FF	1 K	TIM2

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3o).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25$ °C, $V_{DD} = V_{DDA} = 3.3$ V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2 σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

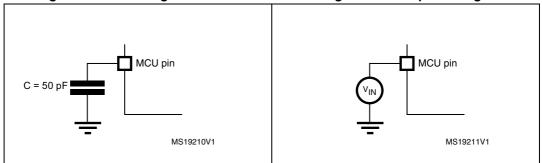
6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 8.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 9*.

Figure 8. Pin loading conditions Figure 9. Pin input voltage



6.1.6 Power supply scheme

1.65 - 3.6V

Backup circuitry
(LSE,RTC,
(LSE,R

Figure 10. Power supply scheme

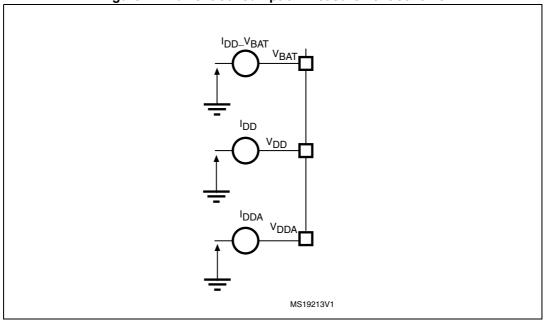
 Dotted lines represent the internal connections on low pin count packages, joining the dedicated supply pins.

Caution:

Each power supply pair (V_{DD}/V_{SS} , V_{DDA}/V_{SSA} etc..) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

6.1.7 Current consumption measurement

Figure 11. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 19: Voltage characteristics*, *Table 20: Current characteristics*, and *Table 21: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 19. Voltage characteristics⁽¹⁾

Symbol	Ratings	Min	Max	Unit
V_{DD} – V_{SS}	External main supply voltage (including V_{DDA} , V_{BAT} and V_{DD})	-0.3	4.0	
V _{DD} –V _{DDA}	Allowed voltage difference for V _{DD} > V _{DDA}	-	0.4	
V _{REF+} -V _{DDA} ⁽²⁾	$_{REF+}$ - $V_{DDA}^{(2)}$ Allowed voltage difference for V_{REF+} > V_{DDA}		0.4]
V _{IN} ⁽³⁾	Input voltage on FT and FTf pins	V _{SS} -0.3	V _{DD} + 4.0	V
	Input voltage on TTa pins	V _{SS} -0.3	4.0	
VIN'	Input voltage on any other pin	V _{SS} -0.3	4.0	
	Input voltage on Boot0 pin	0	9	
ΔV _{DDx}	Variations between different V _{DD} power pins	-	50	mV
V _{SSX} -V _{SS}	Variations between all the different ground pins	-	50	IIIV
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3.12: Electrical sensitivity characteristics		-

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range. The following relationship must be respected between V_{DDA} and V_{DD}: V_{DDA} must power on before or at the same time as V_{DD} in the power up sequence. V_{DDA} must be greater than or equal to V_{DD}.



^{2.} V_{REF+} must be always lower or equal than V_{DDA} ($V_{REF+} \le V_{DDA}$). If unused then it must be connected to V_{DDA} .

V_{IN} maximum must always be respected. Refer to Table 20: Current characteristics for the maximum allowed injected current values.

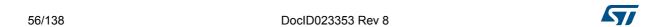
Table 20. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all VDD_x power lines (source)	160	
Σl _{VSS}	Total current out of sum of all VSS_x ground lines (sink)	-160	
I _{VDD}	Maximum current into each V _{DD_x} power line (source) ⁽¹⁾	100	
I _{VSS}	Maximum current out of each V _{SS_x} ground line (sink) ⁽¹⁾	-100	
1	Output current sunk by any I/O and control pin	25	
I _{IO(PIN)}	Output current source by any I/O and control pin	-25	
ΣI	Total output current sunk by sum of all IOs and control pins ⁽²⁾	80	- mA
$\Sigma I_{IO(PIN)}$	Total output current sourced by sum of all IOs and control pins ⁽²⁾	-80	
	Injected current on FT, FTf and B pins ⁽³⁾	-5/+0	
I _{INJ(PIN)}	Injected current on TC and RST pin ⁽⁴⁾	± 5	
	Injected current on TTa pins ⁽⁵⁾	± 5	
$\Sigma I_{\text{INJ(PIN)}}$	Total injected current (sum of all I/O and control pins) ⁽⁶⁾	± 25	

- All main power (V_{DD}, V_{DDA}) and ground (V_{SS} and V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
- This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
- 3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value
- A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 19: Voltage characteristics* for the maximum allowed input voltage values.
- 5. A positive injection is induced by V_{IN} > V_{DDA} while a negative injection is induced by V_{IN} < V_{SS}. I_{INJ}(PIN) must never be exceeded. Refer also to *Table 19: Voltage characteristics* for the maximum allowed input voltage values. Negative injection disturbs the analog performance of the device. See note ⁽²⁾ below *Table 68*.
- When several inputs are submitted to a current injection, the maximum ΣI_{INJ(PIN)} is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 21. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-65 to +150	°C
T _J	Maximum junction temperature	150	°C



6.3 Operating conditions

6.3.1 General operating conditions

Table 22. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit	
f _{HCLK}	Internal AHB clock frequency	-	0	72		
f _{PCLK1} Internal APB1 clock frequency		-	0	36	MHz	
f _{PCLK2}	Internal APB2 clock frequency	-	0	72		
V _{DD}	Standard operating voltage	-	2	3.6	V	
\/	Analog operating voltage (OPAMP and DAC not used)	Must have a potential equal to or higher than	2	3.6	V	
V_{DDA}	Analog operating voltage (OPAMP and DAC used)	V _{DD}	2.4	3.6	V	
V _{BAT}	Backup operating voltage	-	1.65	3.6	V	
		TC I/O	-0.3	V _{DD} +0.3		
V	I/O input voltage	TTa I/O	-0.3	V _{DDA} +0.3	V	
V _{IN}		FT and FTf I/O ⁽¹⁾	-0.3	5.5		
		воото	0	5.5		
	Power dissipation at T _A =	LQFP100	-	488		
P_{D}	85 °C for suffix 6 or T _A = 105 °C for suffix 7 ⁽²⁾	LQFP64	-	444	mW	
	105 °C for suffix 7 ⁽²⁾	LQFP48	-	364		
	Ambient temperature for 6 suffix version	Maximum power dissipation	-40	85	°C	
TA	Sullix version	Low power dissipation ⁽³⁾	-40	105		
1A	Ambient temperature for 7 suffix version	Maximum power dissipation	-40	105	°C	
	Sullix VEISION	Low power dissipation ⁽³⁾	-40	125		
TJ	lunction temperature rease	6 suffix version	-40	105	°C	
IJ	Junction temperature range	7 suffix version	-40 125			

^{1.} To sustain a voltage higher than V_{DD} +0.3 V, the internal pull-up/pull-down resistors must be disabled.

^{2.} If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see Section 7.2: Thermal characteristics).

^{3.} In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see Section 7.2: Thermal characteristics).

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 23* are derived from tests performed under the ambient temperature condition summarized in *Table 22*.

Table 23. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t _{VDD}	V _{DD} rise time rate		0	∞	
	V _{DD} fall time rate	-	20	∞	μs/V
	V _{DDA} rise time rate		0	∞	μ5/ ν
	V _{DDA} fall time rate	_	20	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 24* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 24. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{POR/PDR} ⁽¹⁾	Power on/power down	Falling edge	1.8 ⁽²⁾	1.88	1.96	V
* POR/PDR	reset threshold	Rising edge	1.84	1.92	2.0	V
V _{PDRhyst} ⁽¹⁾	PDR hysteresis	-	-	40	-	mV
t _{RSTTEMPO} (3)	POR reset temporization	-	1.5	2.5	4.5	ms

The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD}.

577

^{2.} The product behavior is guaranteed by design down to the minimum $V_{\mbox{\scriptsize POR/PDR}}$ value.

^{3.} Guaranteed by design, not tested in production.

Table 25. Programmable voltage detector characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
V _{PVD0} PVD threshold 0		Rising edge	2.1	2.18	2.26	
VPVD0	PVD tillesiloid 0	Falling edge	2	2.08	2.16	
\/	PVD threshold 1	Rising edge	2.19	2.28	2.37	
V _{PVD1}	PVD tillesiloid i	Falling edge	2.09	2.18	2.27	
V	PVD threshold 2	Rising edge	2.28	2.38	2.48	
V _{PVD2}	PVD tillesiloid 2	Falling edge	2.18	2.28	2.38	
V _{PVD3}	PVD threshold 3	Rising edge	2.38	2.48	2.58	
	F VD tillesiloid 3	Falling edge	2.28	2.38	2.48	V
1/	PVD threshold 4	Rising edge	2.47	2.58	2.69	V
V_{PVD4}		Falling edge	2.37	2.48	2.59	
\/	PVD threshold 5	Rising edge	2.57	2.68	2.79	
V _{PVD5}		Falling edge	2.47	2.58	2.69	
	DVD throubold 6	Rising edge	2.66	2.78	2.9	
V _{PVD6}	PVD threshold 6	Falling edge	2.56	2.68	2.8	
\/	PVD threshold 7	Rising edge	2.76	2.88	3	
V _{PVD7}	F VD tillesiloid /	Falling edge	2.66	2.78	2.9	
V _{PVDhyst} ⁽²⁾	PVD hysteresis	-	-	100	-	mV
IDD(PVD)	PVD current consumption	-	-	0.15	0.26	μΑ

^{1.} Data based on characterization results only, not tested in production.

^{2.} Guaranteed by design, not tested in production.

6.3.4 Embedded reference voltage

The parameters given in *Table 26* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
M	Internal reference voltage	-40 °C < T _A < +105 °C	1.16	1.2	1.25	V
V_{REFINT}	internal reference voltage	-40 °C < T _A < +85 °C	1.16	1.2	1.24 ⁽¹⁾	V
T _{S_vrefint}	ADC sampling time when reading the internal reference voltage	-	2.2	-	-	μs
V _{RERINT}	Internal reference voltage spread over the temperature range	V _{DD} = 3 V ±10 mV	-	-	10 ⁽²⁾	mV
T _{Coeff}	Temperature coefficient	-	-	-	100 ⁽²⁾	ppm/°C

Table 26. Embedded internal reference voltage

^{2.} Guaranteed by design, not tested in production.

Table 211 Internal reference vertage came and reference									
Calibration value name	Description	Memory address							
V _{REFINT_CAL}	Raw data acquired at temperature of 30 °C V _{DDA} = 3.3 V	0x1FFF F7BA - 0x1FFF F7BB							

Table 27. Internal reference voltage calibration values

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 11: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz,1 wait state from 24 to 48 MHz and 2 wait states from 48 to 72 MHz)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled f_{PCLK2} = f_{HCLK} and f_{PCLK1} = f_{HCLK/2}
- When f_{HCLK} > 8 MHz, the PLL is ON and the PLL input is equal to HSI/2 (4 MHz) or HSE (8 MHz) in bypass mode.



^{1.} Data based on characterization results, not tested in production.

The parameters given in *Table 28* to *Table 32* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22*.

Table 28. Typical and maximum current consumption from V_{DD} supply at V_{DD} = 3.6V

					periphe		abled		periphe			
Symbol	Parameter	Conditions	f _{HCLK}	CLK _	Max @ T _A ⁽¹⁾		T		ax @ T	Unit		
				Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C	
			72 MHz	61.2	65.8	67.6	68.5	27.8	30.3	30.7	31.5	
			64 MHz	54.7	59.1	60.2	61.1	24.6	27.2	27.6	28.3	
		External	48 MHz	41.7	45.1	46.2	47.2	19.2	21.1	21.4	21.8	
		clock (HSE	32 MHz	28.1	31.5	32.5	32.7	12.9	14.6	14.8	15.3	
	Supply	bypass)	24 MHz	21.4	23.7	24.4	25.2	10.0	11.4	11.4	12.1	
	current in Run mode,		8 MHz	7.4	8.4	8.6	9.4	3.6	4.1	4.4	5.0	
	executing		1 MHz	1.3	1.6	1.8	2.6	0.8	1.0	1.2	2.1	
	from Flash	Internal clock (HSI)	64 MHz	49.7	54.4	55.4	56.3	24.5	27.2	27.4	28.1	
			48 MHz	37.9	42.2	43.0	43.5	18.9	21.4	21.5	21.6	-
			32 MHz	25.8	29.2	29.2	30.0	12.7	14.2	14.6	15.2	
			24 MHz	19.7	22.3	22.6	23.2	6.7	7.7	7.9	8.5	
			8 MHz	6.9	7.8	8.3	8.8	3.5	4.0	4.4	5.0	mA
I _{DD}			72 MHz	60.8	66.2 ⁽²⁾	69.7	70.4 ⁽²⁾	27.4	31.7 ⁽²⁾	32.2	32.5 ⁽²⁾	IIIA
			64 MHz	54.3	59.1	62.2	63.3	24.3	28.3	28.7	28.8	
		External	48 MHz	41.0	45.6	47.3	47.9	18.3	21.6	21.9	22.1	
		clock (HSE	32 MHz	27.6	32.4	32.4	32.9	12.3	15.0	15.2	15.4	
	Supply	bypass)	24 MHz	20.8	23.9	24.3	25.0	9.3	11.3	11.4	12.0	
	current in Run mode,		8 MHz	6.9	7.8	8.7	9.0	3.1	3.7	4.2	4.9	
	executing		1 MHz	0.9	1.2	1.5	2.3	0.4	0.6	1.0	1.8	
	from RAM		64 MHz	49.2	53.9	55.2	57.4	23.9	27.8	28.2	28.4]
			48 MHz	37.3	40.8	41.4	44.1	18.2	21.0	21.6	21.9]
		Internal clock (HSI)	32 MHz	25.1	27.6	29.1	30.1	12.0	14.0	14.5	15.1	1
			24 MHz	19.0	21.6	22.1	22.9	6.3	7.2	7.7	8.1	
			8 MHz	6.4	7.3	7.9	8.4	3.0	3.5	4.0	4.7	

Table 28. Typical and maximum current consumption from V_{DD} supply at V_{DD} = 3.6V (continued)

				All	periphe	erals en	abled	All	periphe	erals dis	abled	
Symbol	Parameter	Conditions	f _{HCLK}	Tyrn	М	ax @ T	A ⁽¹⁾	Tyrn	M	lax @ T	105 °C 8.7 7.9 6.3 4.8 3.9 2.2 1.5 7.5 5.9 4.5 2.9	Unit
				Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C		
			72 MHz	44.0	48.4	49.4	50.5	6.6	7.5	7.9	8.7	
			64 MHz	39.2	43.3	44.0	45.2	6.0	6.8	7.2	7.9	
		External	48 MHz	29.6	32.7	33.3	34.3	4.5	5.2	5.6	6.3	
	Committee	clock (HSE	32 MHz	19.7	23.3	23.3	23.5	3.1	3.5	4.0	4.8	
	Supply current in	bypass)	24 MHz	14.9	17.6	17.8	18.3	2.4	2.8	3.3	3.9	
	Sleep mode,		8 MHz	4.9	5.7	6.1	6.9	0.8	1.0	1.4	2.2	mA
I _{DD}	executing		1 MHz	0.6	0.9	1.2	2.1	0.1	0.3	0.6	1.5]
	from Flash or RAM		64 MHz	34.2	38.1	39.2	40.3	5.7	6.3	6.8	7.5	
	OI TO GVI		48 MHz	25.8	28.7	29.6	30.3	4.3	4.8	5.2	A(1) 105 °C 8.7 7.9 6.3 4.8 3.9 2.2 1.5 7.5 5.9 4.5	
		Internal clock (HSI)	32 MHz	17.4	19.4	19.9	20.7	2.9	3.2	3.7	4.5	
		3.33 (1.131)	24 MHz	13.2	15.1	15.6	15.9	1.5	1.8	2.2	2.9	
		8 MHz	4.5	5.0	5.6	6.2	0.7	0.9	1.2	2.1		

^{1.} Data based on characterization results, not tested in production unless otherwise specified.

Table 29. Typical and maximum current consumption from the V_{DDA} supply

					V_{DDA}	= 2.4 V	,		V_{DDA}	= 3.6 \	/	
Symbol	Parameter	Conditions (1)	f _{HCLK}	Tvn	M	ax @ T _A	(2)	Typ	М	Max @ T _A ⁽²⁾		Unit
				Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C 329 293 230 169 135 9 9 381 318	
			72 MHz	225	276	289	297	245	302	319	329	
			64 MHz	198	249	261	268	216	270	284	293	
		48 MHz	149	195	204	211	159	209	222	230		
	Supply	HSE bypass	32 MHz	102	145	152	157	110	154	162	169	
	current in	,,,,,,,,	24 MHz	80	119	124	128	86	126	131	135	
	Run mode, code		8 MHz	2	3	4	6	3	4	5	9	μA
I _{DDA}	executing		1 MHz	2	3	5	7	3	4	6	9	
	from Flash or RAM		64 MHz	270	323	337	344	299	354	371	381	
	OI KAIVI		48 MHz	220	269	280	286	244	293	309	318	
		HSI clock	32 MHz	173	218	228	233	193	239	251	257	
			24 MHz	151	194	200	204	169	211	219	225	
			8 MHz	73	97	99	103	88	105	110	116	

^{1.} Current consumption from the V_{DDA} supply is independent of whether the peripherals are on or off. Furthermore when the PLL is off, I_{DDA} is independent from the frequency.



^{2.} Data based on characterization results and tested in production with code executing from RAM.

^{2.} Data based on characterization results, not tested in production.

Table 30. Typical and maximum $V_{\mbox{\scriptsize DD}}$ consumption in Stop and Standby modes

				Тур (@V _{DD} ((V _{DD} =V	/ _{DDA})			Max ⁽¹⁾		
Symbol	Parameter	Conditions	2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit
	O	Regulator in run mode, all oscillators OFF	20.05	20.33	20.42	20.50	20.67	20.80	44.2 ⁽²⁾	350	735 ⁽²⁾	
I _{DD}	Stop mode	Regulator in low-power mode, all oscillators OFF	7.63	7.77	7.90	8.07	8.17	8.33	30.6 ⁽²⁾	335	720 ⁽²⁾	μA
Supply current in Standby mode	LSI ON and IWDG ON	0.80	0.96	1.09	1.23	1.37	1.51	-	-	-	1	
	Standby	LSI OFF and IWDG OFF	0.60	0.74	0.83	0.93	1.02	1.11	5.0 ⁽²⁾	7.8	13.3 ⁽²⁾	

^{1.} Data based on characterization results, not tested in production unless otherwise specified.

Table 31. Typical and maximum V_{DDA} consumption in Stop and Standby modes

					Тур @	V _{DD} (V _{DD} =	V _{DDA})			Max ⁽¹⁾		
Symbol	Parameter		Conditions	2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit
	Supply	NO	Regulator in run mode, all oscillators OFF	1.81	1.95	2.07	2.20	2.35	2.52	3.7	5.5	8.8	
current in Stop mode Supply current in	ו ס	Regulator in low-power mode, all oscillators OFF	1.81	1.95	2.07	2.20	2.35	2.52	3.7	5.5	8.8		
			LSI ON and IWDG ON	2.22	2.42	2.59	2.78	3.0	3.24	ı	ı	-	
	Standby >	V_{DDA}	LSI OFF and IWDG OFF	1.69	1.82	1.94	2.08	2.23	2.40	3.5	5.4	9.2	μA
I _{DDA}	Supply 발		Regulator in run mode, all oscillators OFF	1.05	1.08	1.10	1.15	1.22	1.29	ı	ı	-	μΛ
	current in	nonitoring C	Regulator in low-power mode, all oscillators OFF	1.05	1.08	1.10	1.15	1.22	1.29	-	-	-	
	- Japp.		LSI ON and IWDG ON	1.44	1.52	1.60	1.71	1.84	1.98	ı	1	-	
	current in Standby mode	_{Маа}	LSI OFF and IWDG OFF	0.93	0.95	0.98	1.02	1.08	1.15	1	1	-	

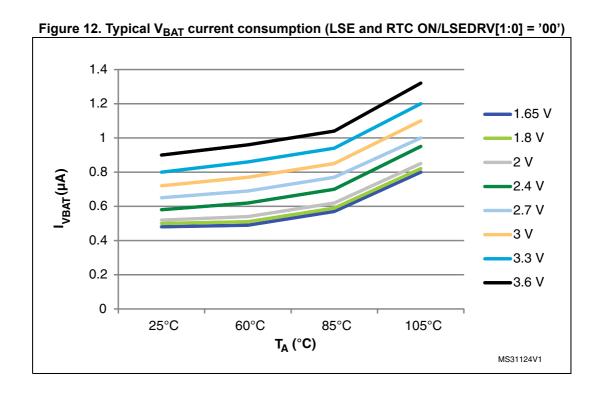
^{1.} Data based on characterization results, not tested in production.

^{2.} Data based on characterization results and tested in production.

Table 32. Typical and maximum current consumption from V_{BAT} supply

Symbol	Para	Conditions				Typ @\	V _{BAT}	-		_	@V _E	.6 V ⁽²⁾	Unit	
Symbol	meter	(1)	1.65V	1.8V	2V	2.4V	2.7V	3V	3.3V	3.6V	T _A = 25°C		T _A = 105°C	Onic
I _{DD_VBAT} domain supply	Backup domain	LSE & RTC ON; "Xtal mode" lower driving capability; LSEDRV[1: 0] = '00'	0.48	0.50	0.52	0.58	0.65	0.72	0.80	0.90	1.1	1.5	2.0	
	supply current	LSE & RTC ON; "Xtal mode" higher driving capability; LSEDRV[1: 0] = '11'	0.83	0.86	0.90	0.98	1.03	1.10	1.20	1.30	1.5	2.2	2.9	- μΑ

- 1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a CL of 6 pF for typical values.
- 2. Data based on characterization results, not tested in production.



57

Typical current consumption

The MCU is placed under the following conditions:

- V_{DD} = V_{DDA} = 3.3 V
- All I/O pins available on each package are in analog input configuration
- The Flash access time is adjusted to f_{HCLK} frequency (0 wait states from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states from 48 MHz to 72 MHz), and Flash prefetch is ON
- When the peripherals are enabled, f_{APB1} = f_{AHB/2}, f_{APB2} = f_{AHB}
- PLL is used for frequencies greater than 8 MHz
- AHB prescaler of 2, 4, 8,16 and 64 is used for the frequencies 4 MHz, 2 MHz, 1 MHz, 500 kHz and 125 kHz respectively.

Table 33. Typical current consumption in Run mode, code with data processing running from Flash

				Т	yp			
Symbol	Parameter	Conditions	f _{HCLK}	Peripherals enabled	Peripherals disabled	Unit		
			72 MHz	61.3	28.0			
			64 MHz	54.8	25.4			
			48 MHz	41.9	19.3			
			32 MHz	28.5	13.3	1		
			24 MHz	21.8	10.4	1		
,	Supply current in		16 MHz	14.9	7.2	mA		
I _{DD}		un mode from 8 MHz 4 MHz 2 MHz	8 MHz	7.7	3.9	IIIA		
	00 11 7		4 MHz	4.5	2.5	1		
			2.8	1.7	-			
			1 MHz	1.9	1.3			
		Running from HSE	500 kHz	1.4	1.1	1		
		crystal clock 8 MHz, code executing from	125 kHz	1.1	0.9	-		
			72 MHz	240.3	239.5			
		Flash	64 MHz	210.9	210.3	1		
			48 MHz	155.8	155.6	1		
			32 MHz	105.7	105.6			
			24 MHz	82.1	82.0	1		
I _{DDA} ^{(1) (2)}	Supply current in Run mode from		16 MHz	58.8	58.8	Ī∧		
DDA` / ` /	V _{DDA} supply		8 MHz	2.4	2.4	μA		
	DDA - FF J		4 MHz	2.4	2.4	1		
			2 MHz	2.4	2.4	1		
			1 MHz	2.4	2.4	1		
			500 kHz	2.4	2.4	1		
			125 kHz	2.4	2.4	1		

V_{DDA} monitoring is ON.

^{2.} When peripherals are enabled, the power consumption of the analog part of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.



Table 34. Typical current consumption in Sleep mode, code running from Flash or RAM

				Т	ур			
Symbol	Parameter	Conditions	f _{HCLK}	Peripherals enabled	Peripherals disabled	Unit		
			72 MHz	44.1	7.0			
			64 MHz 39.7	39.7	6.3			
			48 MHz	30.3	4.9			
			32 MHz	20.5	3.5			
			24 MHz	15.4	2.8			
1	Supply current in		16 MHz	10.6	2.0			
I_{DD}	Sleep mode from V _{DD} supply		8 MHz	5.4	1.1	mA		
			4 MHz	3.2	1.0			
			2.1	0.9	1			
			1 MHz	1.5	0.8			
		Running from HSE	500 kHz	1.2	0.8			
		crystal clock 8 MHz,	125 kHz	1.0	0.8			
		code executing from	72 MHz	239.7	238.5			
		Flash or RAM	64 MHz	210.5	209.6			
			48 MHz	155.0	155.6			
			32 MHz	105.3	105.2			
			24 MHz	81.9	81.8			
I _{DDA} ^{(1) (2)}	Supply current in Sleep mode from		16 MHz	58.7	58.6	Ī		
IDDA` ´ ` ´	V _{DDA} supply		8 MHz	2.4	2.4	μA		
			4 MHz	2.4	2.4			
			2 MHz	2.4	2.4			
			1 MHz	2.4	2.4	1		
			500 kHz	2.4	2.4			
			125 kHz	2.4	2.4			

^{1.} V_{DDA} monitoring is ON.

^{2.} When peripherals are enabled, the power consumption of the analog part of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 52: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution:

Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 36: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

 I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_{S}$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.



Table 35. Switching output I/O current consumption

Symbol	Parameter	Conditions ⁽¹⁾	I/O toggling frequency (f _{SW})	Тур	Unit
			2 MHz	0.90	
			4 MHz	0.90 0.93 1.16 1.60 2.51 2.97 0.93 1.06 1.47 2.26 3.39 5.99 1.03	
		$V_{DD} = 3.3 V$ $C_{ext} = 0 pF$	8 MHz	1.16	
		$C = C_{INT} + C_{EXT} + C_{S}$	18 MHz	1.60	
			36 MHz	2.51	
			48 MHz	2.97	
			2 MHz	0.93	
		4 MHz	1.06		
		V _{DD} = 3.3 V C _{ext} = 10 pF	8 MHz	1.47	
		$C_{\text{ext}} - 10 \text{ pr}$ $C = C_{\text{INT}} + C_{\text{EXT}} + C_{\text{S}}$	18 MHz	2.26	
			36 MHz	3.39	
			48 MHz	5.99	
			2 MHz	1.03	
I _{SW}	I/O current consumption	V _{DD} = 3.3 V	4 MHz	1.30	mA
	·	$C_{ext} = 22 pF$	8 MHz	1.79	
		$C = C_{INT} + C_{EXT} + C_{S}$	18 MHz	3.01	
			36 MHz	5.99	
			2 MHz	1.10	
		V _{DD} = 3.3 V	4 MHz	1.31	
		C _{ext} = 33 pF	8 MHz	2.06	
		$C = C_{INT} + C_{EXT} + C_{S}$	18 MHz	3.47	
			36 MHz	8.35	
			2 MHz	1.20	
		V _{DD} = 3.3 V	4 MHz	1.54	
		$C_{ext} = 47 pF$	8 MHz	2.46]
		$C = C_{INT} + C_{EXT} + C_{S}$	18 MHz	4.51	
			36 MHz	9.98	

^{1.} CS = 5 pF (estimated value).

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- all I/O pins are in analog input configuration
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- ambient operating temperature at 25°C and V_{DD} = V_{DDA} = 3.3 V.

Table 36. Peripheral current consumption

	Typical consumption ⁽¹⁾	llm:4
Peripheral	I _{DD}	Unit
BusMatrix ⁽²⁾	12.6	
DMA1	7.6	
DMA2	6.1	
CRC	2.1	
GPIOA	10.0	
GPIOB	10.3	
GPIOC	2.2	
GPIOD	8.8	
GPIOE	3.3	
GPIOF	3.0	
TSC	5.5	
ADC1&2	17.3	
ADC3&4	18.8	\ /\ \ \ \
APB2-Bridge (3)	3.6	— μA/MHz
SYSCFG	7.3	
TIM1	40.0	
SPI1	8.8	
TIM8	36.4	
USART1	23.3	
TIM15	17.1	
TIM16	10.1	
TIM17	11.0	
APB1-Bridge (3)	6.1	
TIM2	49.1	
TIM3	38.8	
TIM4	38.3	

Table 36. Peripheral current consumption (continued)

Peripheral	Typical consumption ⁽¹⁾	Unit
i cripnerar	I _{DD}	Omi
TIM6	9.7	
TIM7	12.1	
WWDG	6.4	
SPI2	40.4	
SPI3	40.0	
USART2	41.9	
USART3	40.2	
UART4	36.5	μA/MHz
UART5	30.8	
I2C1	10.5	
I2C2	10.4	
USB	26.2	
CAN	33.4	
PWR	5.7	
DAC	15.4	

^{1.} The power consumption of the analog part (I_{DDA}) of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.

^{2.} BusMatrix is automatically active when at least one master is ON (CPU, DMA1 or DMA2).

^{3.} The APBx bridge is automatically active when at least one peripheral is ON on the same bus.

6.3.6 Wakeup time from low-power mode

The wakeup times given in *Table 37* are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep mode: the wakeup event is WFE.
- WKUP1 (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 37. Low-power mode wakeup timings

Symbol	Parameter	Conditions		Туј	@V DD,	V _{DD} = V	DDA		Max	Unit
Symbol	Farameter	Conditions	2.0 V	2.4 V	2.7 V	3 V	3.3 V	3.6 V	IVIAX	J
twustop	Wakeup from	Regulator in run mode	4.1	3.9	3.8	3.7	3.6	3.5	4.5	
	Stop mode	Regulator in low power mode	7.9	6.7	6.1	5.7	5.4	5.2	9	μs
t _{WUSTANDBY} (1)	Wakeup from Standby mode	LSI and IWDG OFF	69.2	60.3	56.4	53.7	51.7	50	100	
t _{WUSLEEP}	Wakeup from Sleep mode	-	6			-	CPU clock cycles			

^{1.} Data based on characterization results, not tested in production.

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

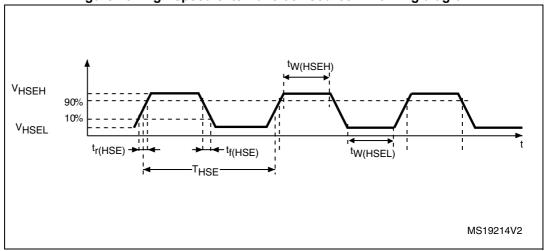
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 13*.

Table 38. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSE_ext}	User external clock source frequency ⁽¹⁾		1	8	32	MHz
V _{HSEH}	OSC_IN input pin high level voltage		0.7V _{DD}	-	V_{DD}	V
V _{HSEL}	OSC_IN input pin low level voltage	-	V_{SS}	-	0.3V _{DD}	
t _{w(HSEH)}	OSC_IN high or low time ⁽¹⁾		15	-	-	ns
t _{r(HSE)}	OSC_IN rise or fall time ⁽¹⁾		-	-	20	110

^{1.} Guaranteed by design, not tested in production.

Figure 13. High-speed external clock source AC timing diagram



Low-speed external user clock generated from an external source

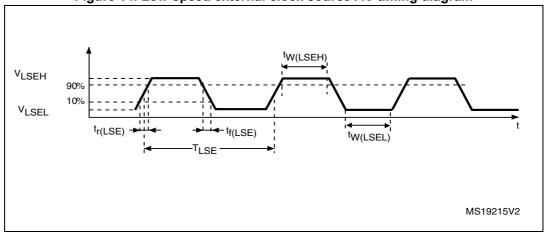
In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 14*

Table 39. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSE_ext}	User External clock source frequency ⁽¹⁾		-	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage		0.7V _{DD}	-	V_{DD}	V
V _{LSEL}	OSC32_IN input pin low level voltage	-	V _{SS}	ı	0.3V _{DD}	V
t _{w(LSEH)}	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
$\begin{array}{c} t_{r(\text{LSE})} \\ t_{f(\text{LSE})} \end{array}$	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	10

^{1.} Guaranteed by design, not tested in production.

Figure 14. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 40*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Conditions⁽¹⁾ Min⁽²⁾ Max⁽²⁾ **Symbol Parameter** Typ Unit Oscillator frequency 8 32 MHz 4 fosc in 200 R_F Feedback resistor $k\Omega$ _ During startup⁽³⁾ 8.5 V_{DD} =3.3 V, Rm= 30 Ω Λ 4 CL=10 pF@8 MHz V_{DD} =3.3 V, Rm= 45 Ω 0.5 CL=10 pF@8 MHz HSE current consumption mΑ I_{DD} V_{DD}=3.3 V, Rm= 30Ω 8.0 CL=10 pF@32 MHz $V_{DD} = 3.3 \text{ V, Rm} = 30\Omega$ 1 CL=10 pF@32 MHz V_{DD} =3.3 V, Rm= 30 Ω 1.5 CL=10 pF@32 MHz 10 mA/V Oscillator transconductance Startup g_{m} $t_{\rm SU(HSE)}^{(4)}$ 2 V_{DD} is stabilized Startup time ms

Table 40. HSE oscillator characteristics

^{1.} Resonator characteristics given by the crystal/ceramic resonator manufacturer.

^{2.} Guaranteed by design, not tested in production.

^{3.} This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time.

^{4.} t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 15*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note:

For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

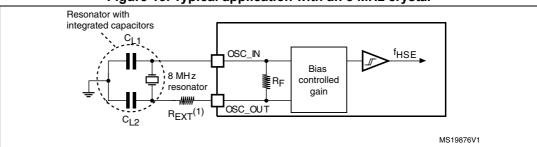


Figure 15. Typical application with an 8 MHz crystal

1. $R_{\mbox{\scriptsize EXT}}$ value depends on the crystal characteristics.

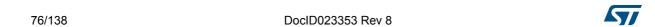
Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 41*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions ⁽¹⁾	Min ⁽²⁾	Тур	Max ⁽²⁾	Unit	
		LSEDRV[1:0]=00 lower driving capability	-	0.5	0.9		
	LSE current consumption	LSEDRV[1:0]=01 medium low driving capability	-	-	1	^	
I _{DD}	LSE current consumption	LSEDRV[1:0]=10 medium high driving capability	-	-	1.3	μΑ	
		LSEDRV[1:0]=11 higher driving capability	-	-	1.6		
	Oscillator transconductance	LSEDRV[1:0]=00 lower driving capability	5	-	-		
<u> </u>		LSEDRV[1:0]=01 medium low driving capability	8	-	-		
9 _m		LSEDRV[1:0]=10 medium high driving capability	15	-	-	- μ Α /V	
		LSEDRV[1:0]=11 higher driving capability	25	-	-		
t _{SU(LSE)} (3)	Startup time	V _{DD} is stabilized	-	2	-	s	

Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



^{2.} Guaranteed by design, not tested in production.

^{3.} t_{SU(LSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer.

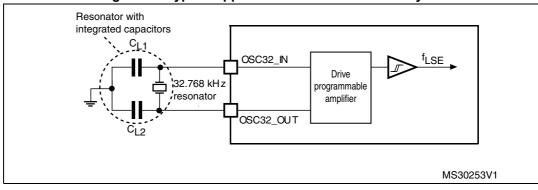


Figure 16. Typical application with a 32.768 kHz crystal

Note:

An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.

6.3.8 Internal clock source characteristics

The parameters given in *Table 42* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22*.

High-speed internal (HSI) RC oscillator

Table 42. HSI oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI}	Frequency	-	-	8	-	MHz
TRIM	HSI user trimming step	-	-	-	1 ⁽²⁾	%
DuCy _(HSI)	Duty cycle	-	45 ⁽²⁾	-	55 ⁽²⁾	%
		T _A = -40 to 105 °C	-3.8 ⁽³⁾	-	4.6 ⁽³⁾	%
400	Accuracy of the HSI oscillator (factory calibrated)	T _A = -10 to 85 °C	-2.9 ⁽³⁾	-	2.9 ⁽³⁾	%
ACC _{HSI}		T _A = 0 to 70 °C	-	-	-	%
		T _A = 25 °C	-1	-	1	%
t _{su(HSI)}	HSI oscillator startup time	-	1 ⁽²⁾	-	2 ⁽²⁾	μs
I _{DD(HSI)}	HSI oscillator power consumption	-	-	80	100 ⁽²⁾	μΑ

- 1. V_{DDA} = 3.3 V, T_{A} = -40 to 105 °C unless otherwise specified.
- 2. Guaranteed by design, not tested in production.
- 3. Data based on characterization results, not tested in production.

Figure 17. HSI oscillator accuracy characterization results **ACC**_{HSI} 3% MAX MIN -20 0 20 40 60 80 100 120 -2% -3% -4% TA [°C] -5% MS30985V2

1. The above curves are based on characterisation results, not tested in production.

Low-speed internal (LSI) RC oscillator

Table 43. LSI oscillator characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Unit
f _{LSI}	Frequency	30	40	50	kHz
t _{su(LSI)} ⁽²⁾	t _{su(LSI)} (2) LSI oscillator startup time		-	85	μs
I _{DD(LSI)} ⁽²⁾	LSI oscillator power consumption	-	0.75	1.2	μΑ

^{1.} V_{DDA} = 3.3 V, T_A = -40 to 105 °C unless otherwise specified.

6.3.9 PLL characteristics

The parameters given in *Table 44* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22*.

Table 44. PLL characteristics

Symbol	Parameter		Unit		
Symbol	Farameter	Min	Тур	Max	Offic
f	PLL input clock ⁽¹⁾	1 ⁽²⁾	-	24 ⁽²⁾	MHz
f _{PLL_IN}	PLL input clock duty cycle	40 ⁽²⁾	-	60 ⁽²⁾	%
f _{PLL_OUT}	PLL multiplier output clock	16 ⁽²⁾	-	72	MHz
t _{LOCK}	PLL lock time	-	-	200 ⁽²⁾	μs
Jitter	Cycle-to-cycle jitter	-	-	300 ⁽²⁾	ps

Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

^{2.} Guaranteed by design, not tested in production.

^{2.} Guaranteed by design, not tested in production.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = -40 to 105 $^{\circ}C$ unless otherwise specified.

Table 45. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
t _{prog}	16-bit programming time	$T_A = -40 \text{ to } +105 ^{\circ}\text{C}$	40	53.5	60	μs
t _{ERASE}	Page (2 KB) erase time	$T_A = -40 \text{ to } +105 ^{\circ}\text{C}$	20	-	40	ms
t _{ME}	Mass erase time	$T_A = -40 \text{ to } +105 ^{\circ}\text{C}$	20	-	40	ms
	Supply current	Write mode	-	-	10	mA
IDD		Erase mode	-	-	12	mA

^{1.} Guaranteed by design, not tested in production.

Table 46. Flash memory endurance and data retention

Symbol	Parameter Conditions	Conditions	Value	Unit
Symbol	Parameter	Conditions	Min ⁽¹⁾	
N _{END}	Endurance	$T_A = -40$ to +85 °C (6 suffix versions) $T_A = -40$ to +105 °C (7 suffix versions)	10	kcycles
		1 kcycle ⁽²⁾ at T _A = 85 °C	30	
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 105 °C	10	Years
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	

^{1.} Data based on characterization results, not tested in production.

^{2.} Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 47*. They are based on the EMS levels and classes defined in application note AN1709.

Level/ **Symbol Parameter Conditions** Class $V_{DD} = 3.3 \text{ V, LQFP100, T}_{A} = +25^{\circ}\text{C,}$ Voltage limits to be applied on any I/O pin to V_{FESD} f_{HCLK} = 72 MHz 3B induce a functional disturbance conforms to IEC 61000-4-2 $V_{DD} = 3.3 \text{ V, LQFP100, T}_{A} = +25^{\circ}\text{C,}$ Fast transient voltage burst limits to be f_{HCLK} = 72 MHz $\mathsf{V}_{\mathsf{EFTB}}$ applied through 100 pF on V_{DD} and V_{SS} 4A pins to induce a functional disturbance conforms to IEC 61000-4-4

Table 47. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)



Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Symbol	Parameter	Conditions	Monitored	Max vs. [f _{HSE} /f _{HCLK}]	Unit
Syllibol	i arameter		frequency band	8/72 MHz	
	Peak level	eak level $V_{DD} = 3.6 \text{ V}, T_A = 25 ^{\circ}\text{C}, -100 \text{ LQFP}$ $\begin{array}{c} \text{LQFP100 package} \\ \text{compliant with IEC} \\ \text{61967-2} \end{array}$	0.1 to 30 MHz	7	
			30 to 130 MHz	20	dΒμV
S _{EMI}			130 MHz to 1GHz	27	
			SAE EMI Level	4	-

Table 48. EMI characteristics

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts \times (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to JESD22-A114	2	2000	
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to ANSI/ESD STM5.3.1	II	500	V

Table 49. ESD absolute maximum ratings



^{1.} Data based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 50. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +105 °C conforming to JESD78A	II level A

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5 \,\mu\text{A}/+0 \,\mu\text{A}$ range), or other functional failure (for example reset occurrence or oscillator frequency deviation).

The test results are given in Table 51.

Table 51. I/O current injection susceptibility

		Functional s	usceptibility		
Symbol	Description	Negative injection	Positive injection	Unit	
	Injected current on BOOT0	-0	NA		
	Injected current on PC0, PC1, PC2, PC3, PF2, PA0, PA1, PA2, PA3, PF4, PA4, PA5, PA6, PA7, PC4, PC5, PB2 with induced leakage current on other pins from this group less than -50 μ A	- 5	-		
I _{INJ}	Injected current on PB0, PB1, PE7, PE8, PE9, PE10, PE11, PE12, PE13, PE14, PE15, PB12, PB13, PB14, PB15, PD8, PD9, PD10, PD11, PD12, PD13, PD14 with induced leakage current on other pins from this group less than -50 µA	- 5	-	mA	
5	Injected current on PC0, PC1, PC2, PC3, PF2, PA0, PA1, PA2, PA3, PF4, PA4, PA5, PA6, PA7, PC4, PC5, PB2, PB0, PB1, PE7, PE8, PE9, PE10, PE11, PE12, PE13, PE14, PE15, PB12, PB13, PB14, PB15, PD8, PD9, PD10, PD11, PD12, PD13, PD14 with induced leakage current on other pins from this group less than $400~\mu\text{A}$	-	+5		
	Injected current on any other FT and FTf pins	- 5	NA		
	Injected current on any other pins	- 5	+5		

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.



6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 52* are derived from tests performed under the conditions summarized in *Table 22*. All I/Os are CMOS and TTL compliant.

Table 52. I/O static characteristics

Symbol	Parameter Conditions		Min	Тур	Max	Unit
		TC and TTa I/O	-	-	0.3 V _{DD} +0.07 ⁽¹⁾	
	Low level input	FT and FTf I/O	-	-	0.475 V _{DD} -0.2 ⁽¹⁾	
V _{IL}	voltage	BOOT0	-	-	0.3 V _{DD} -0.3 ⁽¹⁾	
		All I/Os except BOOT0	-	-	0.3 V _{DD} ⁽²⁾	V
		TC and TTa I/O	0.445 V _{DD} +0.398 ⁽¹⁾	-	-	V
.,	High level input	FT and FTf I/O	0.5 V _{DD} +0.2 ⁽¹⁾	-	-	
V _{IH}	voltage	воото	0.2 V _{DD} +0.95 ⁽¹⁾	-	-	
		All I/Os except BOOT0	0.7 V _{DD} ⁽²⁾	-	-	
V_{hys}	Schmitt trigger hysteresis	TC and TTa I/O	-	200 (1)	-	
		FT and FTf I/O	-	100 ⁽¹⁾	-	mV
		воото	-	300 ⁽¹⁾	-	
		TC, FT and FTf I/O TTa I/O in digital mode $V_{SS} \le V_{IN} \le V_{DD}$	-	-	±0.1	
I _{lkg}	Input leakage current ⁽³⁾	TTa I/O in digital mode V _{DD} ≤V _{IN} ≤V _{DDA}	-	-	1	μA
3	Current	TTa I/O in analog mode V _{SS} ≤V _{IN} ≤V _{DDA}	-	-	±0.2	
		FT and FTf I/O ⁽⁴⁾ V _{DD} ≤V _{IN} ≤5 V	-	-	10	
R _{PU}	Weak pull-up equivalent resistor ⁽⁵⁾	$V_{IN} = V_{SS}$	25	40	55	kΩ
R _{PD}	Weak pull-down equivalent resistor ⁽⁵⁾	$V_{IN} = V_{DD}$	25	40	55	kΩ
C _{IO}	I/O pin capacitance	-	-	5	-	pF

^{1.} Data based on design simulation.

Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimum (~10% order).



^{2.} Tested in production.

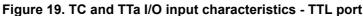
^{3.} Leakage could be higher than the maximum value. if negative current is injected on adjacent pins. Refer to *Table 51: I/O current injection susceptibility*.

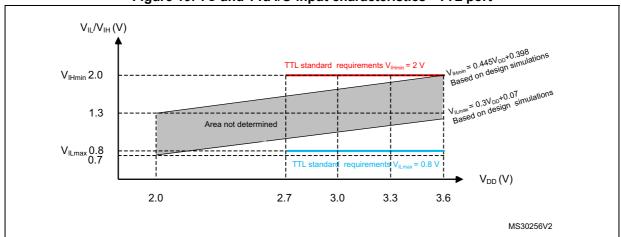
^{4.} To sustain a voltage higher than V_{DD} +0.3 V, the internal pull-up/pull-down resistors must be disabled.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 18* and *Figure 19* for standard I/Os.

 $V_{IL}/V_{IH}(V)$ V_{IHmin} = 0.445V_{DD}+0.398 Based on design simulations $V_{IHmin}\,2.0$ $_{\text{new}} = 0.3 \text{V}_{\text{DD}} + 0.07$ sed on design simulations 1.3 Area not determined = 0.3V_{DD} $V_{\text{ILmax}} \underset{0.6}{0.7}$ $V_{DD}(V)$ 2.0 2.7 3.0 3.3 3.6 MS30255V2

Figure 18. TC and TTa I/O input characteristics - CMOS port





V_{IL}/V_{IH} (V)

2.0

CMOS standard requirements V_{IHmin} = 0.7 V_{DD}

Tested in production

Area not determined

CMOS standard requirements V_{ILmax} = 0.475V_{DD}·0.2

V_{ILmax} = 0.475V_{DD}·0.2

V_{ILmax} = 0.475V_{DD}·0.2

Sased on design simulations

Based on design simulations

V_{ILmax} = 0.3V_{DD}

V_{DD} (V)

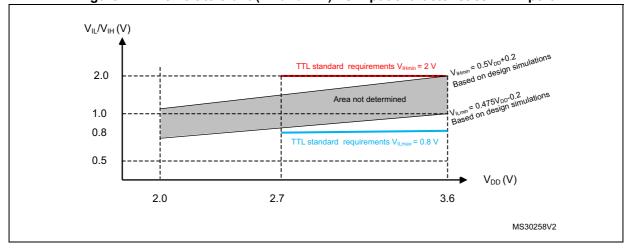
2.0

3.6

MS30257V2

Figure 20. Five volt tolerant (FT and FTf) I/O input characteristics - CMOS port





Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in Section 6.2:

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 20*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 20*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 53* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*. All I/Os (FT, TTa and TC unless otherwise specified) are CMOS and TTL compliant.

Unit **Symbol Conditions Parameter** Min Max $V_{OL}^{(1)}$ Output low level voltage for an I/O pin CMOS port⁽²⁾ 0.4 I_{IO} = +8 mA $V_{OH}^{(3)}$ Output high level voltage for an I/O pin $V_{DD}-0.4$ $2.7 \text{ V} < \text{V}_{DD} < 3.6 \text{ V}$ V_{OI} (1) TTL port⁽²⁾ Output low level voltage for an I/O pin 0.4 I_{1O} = +8 mA V_{OH} (3) Output high level voltage for an I/O pin 2.4 2.7 V < V_{DD} < 3.6 V $V_{OL}^{\overline{(1)(4)}}$ Output low level voltage for an I/O pin 1.3 ٧ I_{IO} = +20 mA $2.7 \text{ V} < \text{V}_{DD} < 3.6 \text{ V}$ $V_{OH}^{(3)(4)}$ Output high level voltage for an I/O pin V_{DD} –1.3 $V_{OL}^{(1)(4)}$ Output low level voltage for an I/O pin 0.4 I_{IO} = +6 mA $V_{OH}^{(3)(4)}$ 2 V < V_{DD} < 2.7 V Output high level voltage for an I/O pin $V_{DD}-0.4$ Output low level voltage for an FTf I/O pin in $I_{10} = +20 \text{ mA}$ $V_{OLFM+}^{(1)(4)}$ 0.4 $2.7 \stackrel{.}{V} < V_{DD} < 3.6 V$ FM+ mode

Table 53. Output voltage characteristics

4. Data based on design simulation.

88/138



The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 20* and the sum of I_{IO} (I/O ports and control pins) must not exceed ΣI_{IO(PIN)}.

^{2.} TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.

The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 20* and the sum of I_{IO} (I/O ports and control pins) must not exceed ΣI_{IO(PIN)}.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 22* and *Table 54*, respectively.

Unless otherwise specified, the parameters given are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Table 54. I/O AC characteristics⁽¹⁾

OSPEEDRy [1:0] value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max	Unit
	f _{max(IO)out}	Maximum frequency ⁽²⁾	$C_L = 50 \text{ pF}, V_{DD} = 2 \text{ V to } 3.6 \text{ V}$	-	2 ⁽³⁾	MHz
x0	t _{f(IO)out}	Output high to low level fall time			125 ⁽³⁾	ns
	t _{r(IO)out}	Output low to high level rise time	$-C_L = 50 \text{ pF}, V_{DD} = 2 \text{ V to } 3.6 \text{ V}$	-	125 ⁽³⁾	113
	f _{max(IO)out}	Maximum frequency ⁽²⁾	C _L = 50 pF, V _{DD} = 2 V to 3.6 V	-	10 ⁽³⁾	MHz
01	t _{f(IO)out}	Output high to low level fall time	C _I = 50 pF, V _{DD} = 2 V to 3.6 V	-	25 ⁽³⁾	20
	t _{r(IO)out}	Output low to high level rise time	-C _L = 50 pr, v _{DD} = 2 v to 3.6 v	-	25 ⁽³⁾	ns
			$C_L = 30 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	50 ⁽³⁾	MHz
	f _{max(IO)out}	Maximum frequency ⁽²⁾	C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V	-	30 ⁽³⁾	MHz
			C _L = 50 pF, V _{DD} = 2 V to 2.7 V	-	20 ⁽³⁾	MHz
			$C_L = 30 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	5 ⁽³⁾	
11	$t_{f(IO)out}$	Output high to low level fall time	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	8 ⁽³⁾	
			$C_L = 50 \text{ pF}, V_{DD} = 2 \text{ V to } 2.7 \text{ V}$	-	12 ⁽³⁾	ns
			$C_L = 30 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	5 ⁽³⁾	115
	$t_{r(IO)out}$	Output low to high level rise time	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	8 ⁽³⁾	
			$C_L = 50 \text{ pF}, V_{DD} = 2 \text{ V to } 2.7 \text{ V}$	-	12 ⁽³⁾	
	f _{max(IO)out}	Maximum frequency ⁽²⁾		-	2 ⁽⁴⁾	MHz
FM+ configuration ⁽⁴⁾	t _{f(IO)out}	Output high to low level fall time	C _L = 50 pF, V _{DD} = 2 V to 3.6 V	-	12 ⁽⁴⁾	9
comgaration	t _{r(IO)out}	Output low to high level rise time		-	34 ⁽⁴⁾	ns
-	t _{EXTIPW}	Pulse width of external signals detected by the EXTI controller	-	10 ⁽³⁾	ı	ns

The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the RM0316 reference manual for a description of GPIO Port configuration register.

^{4.} The I/O speed configuration is bypassed in FM+ I/O mode. Refer to the STM32F303x STM32F313x reference manual RM0316 for a description of FM+ I/O mode configuration.



^{2.} The maximum frequency is defined in *Figure 22*.

^{3.} Guaranteed by design, not tested in production.

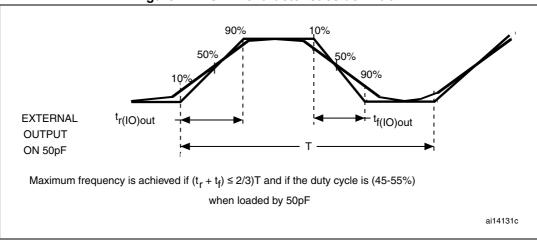


Figure 22. I/O AC characteristics definition

6.3.15 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 52*).

Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 22*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage	-	-	-	0.3V _{DD} + 0.07 ⁽¹⁾	V
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage	-	0.445V _{DD} + 0.398 ⁽¹⁾	-	-	V
V _{hys(NRST)}	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R _{PU}	Weak pull-up equivalent resistor ⁽²⁾	$V_{IN} = V_{SS}$	25	40	55	kΩ
V _{F(NRST)} ⁽¹⁾	NRST Input filtered pulse	-	-	-	100 ⁽¹⁾	ns
V _{NF(NRST)} ⁽¹⁾	NRST Input not filtered pulse	-	500 ⁽¹⁾	-	-	ns

Table 55. NRST pin characteristics

47/

^{1.} Guaranteed by design, not tested in production.

^{2.} The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

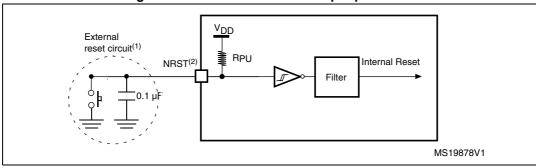


Figure 23. Recommended NRST pin protection

- 1. The reset network protects the device against parasitic resets.
- 2. The user must ensure that the level on the NRST pin can go below the V_{IL(NRST)} max level specified in *Table 55*. Otherwise the reset will not be taken into account by the device.

6.3.16 Timer characteristics

The parameters given in *Table 56* are guaranteed by design.

Refer to Section 6.3.14: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions	Min	Max	Unit
		-	1	-	t _{TIMxCLK}
t _{res(TIM)}	Timer resolution time	f _{TIMxCLK} = 72 MHz (except TIM1/8)	13.9	-	ns
		f _{TIMxCLK} = 144 MHz, x= 1.8	6.95	-	ns
f	Timer external clock	-	0	f _{TIMxCLK} /2	MHz
f _{EXT}	frequency on CH1 to CH4	f _{TIMxCLK} = 72 MHz	0	36	MHz
Dee	Timer resolution	TIMx (except TIM2)	-	16	bit
Res _{TIM}	Timer resolution	TIM2	-	32	Dit
	16-bit counter clock period	-	1	65536	t _{TIMxCLK}
t _{COUNTER}		f _{TIMxCLK} = 72 MHz (except TIM1/8)	0.0139	910	μs
		f _{TIMxCLK} = 144 MHz, x= 1.8	0.0069	455	μs
		-	1	65536 × 65536	t _{TIMxCLK}
t _{MAX_COUNT}	Maximum possible count	f _{TIMxCLK} = 72 MHz	-	59.65	S
W 0. 000141	with 32-bit counter	f _{TIMxCLK} = 144 MHz, x= 1.8	-	29.825	s

Table 56. TIMx⁽¹⁾⁽²⁾ characteristics



TIMx is used as a general term to refer to the TIM1, TIM2, TIM3, TIM4, TIM8, TIM15, TIM16 and TIM17 timers.

^{2.} Guaranteed by design, not tested in production.

Table 57. IWDG min/max timeout period at 40 kHz (LSI) (1)

Prescaler divider	PR[2:0] bits	Min timeout (ms) RL[11:0]= 0x000	Max timeout (ms) RL[11:0]= 0xFFF		
/4	0	0.1	409.6		
/8	1	0.2	819.2		
/16	2	0.4	1638.4		
/32	3	0.8	3276.8		
/64	4	1.6	6553.6		
/128	5	3.2	13107.2		
/256	7	6.4	26214.4		

These timings are given for a 40 kHz clock but the microcontroller's internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 58. WWDG min-max timeout value @72 MHz (PCLK)⁽¹⁾

Prescaler WDGTB		Min timeout value	Max timeout value
1	0	0.05687	3.6409
2	1	0.1137	7.2817
4	2	0.2275	14.564
8	3	0.4551	29.127

^{1.} Guaranteed by design, not tested in production.

477

6.3.17 Communications interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev.03 for:

- Standard-mode (Sm): with a bit rate up to 100 Kbits/s
- Fast-mode (Fm): with a bit rate up to 400 Kbits/s
- Fast-mode Plus (Fm+): with a bit rate up to 1Mbits/s

The I²C timings requirements are guaranteed by design when the I²C peripheral is properly configured (refer to Reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement. Refer to Section 6.3.14: I/O port characteristics.

All I²C I/Os embed an analog filter. refer to the *Table 60: I2C analog filter characteristics*.

Table 59. I2C timings specification (see I2C specification, rev.03, June 2007)⁽¹⁾

Oh al	Danier de la constante de la c	Standa	rd mode	Fast m	node	Fast Mo	de Plus	1114
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Unit
f _{SCL}	SCL clock frequency	0	100	0	400	0	1000	KHz
t _{LOW}	Low period of the SCL clock	4.7	-	1.3	-	0.5	-	μs
t _{HIGH}	High Period of the SCL clock	4		0.6		0.26	-	μs
t _r	Rise time of both SDA and SCL signals	-	1000	-	300	-	120	ns
t _f	Fall time of both SDA and SCL signals	-	300	-	300	-	120	ns
t _{HD;DAT}	Data hold time	0	-	0	-	0	-	μs
t _{VD;DAT}	Data valid time	-	3.45 ⁽²⁾	-	0.9 ⁽²⁾	-	0.45 ⁽²⁾	μs
t _{VD;ACK}	Data valid acknowledge time	-	3.45 ⁽²⁾	-	0.9 ⁽²⁾	-	0.45 ⁽²⁾	μs
t _{SU;DAT}	Data setup time	250	-	100	i	50	-	ns
t _{HD:STA}	Hold time (repeated) START condition	4.0	-	0.6	-	0.26	-	μs
t _{SU:STA}	Set-up time for a repeated START condition	4.7	-	0.6	-	0.26		μs
t _{SU:STO}	Set-up time for STOP condition	4.0	-	0.6	-	0.26	-	μs
t _{BUF}	Bus free time between a STOP and START condition	4.7	-	1.3	-	0.5	-	μs
C _b	Capacitive load for each bus line	-	400	-	400	-	550	pF
t _{SP}	Pulse width of spikes that are suppressed by the analog filter for Standard and Fast mode	0	50 ⁽³⁾	0	50 ⁽³⁾	-	-	ns

- The I2C characteristics are the requirements from I2C bus specification rev03. They are guaranteed by design when I2Cx_TIMING register is correctly programmed (Refer to the RM0316 reference manual). These characteristics are not tested in production.
- 2. The maximum tHD;DAT could be 3.45 µs, 0.9 µs and 0.45 µs for standard mode, fast mode and fast mode plus, but must be less than the maximum of tVD;DAT or tVD;ACK by a transition time.
- 3. The minimum width of the spikes filtered by the analog filter is above $t_{SP}(max)$.

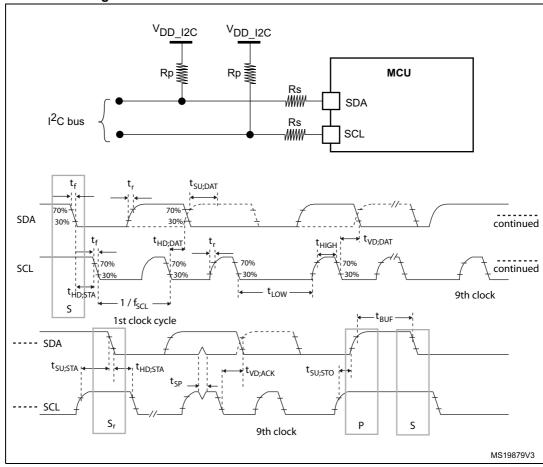


Table 60. I2C analog filter characteristics⁽¹⁾

Symbol	Parameter	Min	Max	Unit
t _{AF}	Pulse width of spikes that are suppressed by the analog filter	50	260	ns

1. Guaranteed by design, not tested in production.

Figure 24. I²C bus AC waveforms and measurement circuit



1. Rs: Series protection resistors, Rp: Pull-up resistors, VDD_I2C: I2C bus supply.

SPI/I²S characteristics

Unless otherwise specified, the parameters given in *Table 61* for SPI or in *Table 62* for I^2S are derived from tests performed under ambient temperature, f_{PCLKX} frequency and V_{DD} supply voltage conditions summarized in *Table 22*.

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Table 61. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode, SPI1 2.7 <v<sub>DD<3.6</v<sub>			24	
f _{SCK}		Slave mode, SPI1 2.7 <v<sub>DD<3.6</v<sub>			24	.
1/t _{c(SCK)}	SPI clock frequency	Master mode, SPI1/2/3 2 <v<sub>DD<3.6</v<sub>	-	-	18	MHz
		Slave mode, SPI1/2/3 2 <v<sub>DD<3.6</v<sub>			18	
DuCy(sck)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-]
t _{w(SCKH)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t _{su(MI)}	Data innut actum time	Master mode	5.5	-	-	
t _{su(SI)}	Data input setup time	Slave mode	6.5	-	-	
t _{h(MI)}	Data input hald time	Master mode	5	-	-	
t _{h(SI)}	Data input hold time	Slave mode	5	-	-	ns
t _{a(SO)}	Data output access time	Slave mode	0	-	4*Tpclk	115
t _{dis(SO)}	Data output disable time	Slave mode	0	-	24	
		Slave mode	-	12	27	
	Data output valid time	Slave mode, SPI1 2.7 <v<sub>DD<3.6V</v<sub>	-	12	18	
		Master mode	-	1.5	3	1
t _{h(SO)}	Data autout hold time	Slave mode	11	-	-	
t _{h(MO)}	Data output hold time	Master mode	0	-	-	

^{1.} Data based on characterization results, not tested in production.



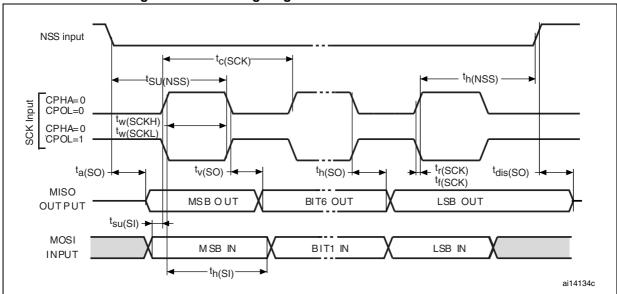
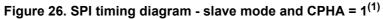
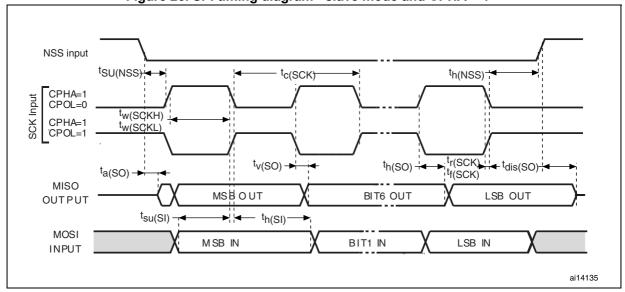


Figure 25. SPI timing diagram - slave mode and CPHA = 0





1. Measurement points are done at $0.5V_{DD}$ and with external C_L = 30 pF.

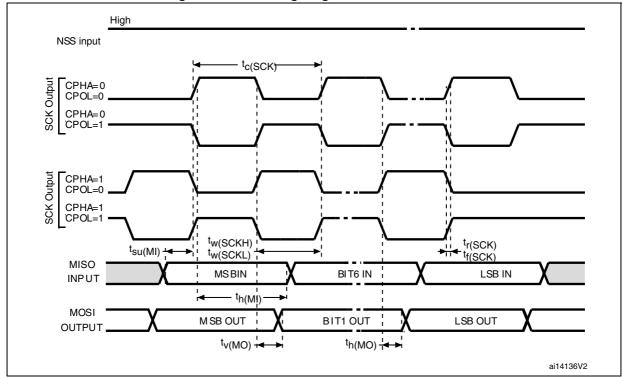


Figure 27. SPI timing diagram - master mode⁽¹⁾

1. Measurement points are done at 0.5V $_{\rm DD}$ and with external C $_{\rm L}$ = 30 pF.

577

Table 62. I²S characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f _{CK}	I ² S clock frequency	Master data: 16 bits, audio freq=48 kHz	1.496	1.503	MHz
1/t _{c(CK)}		Slave	0	12.288	
t _{r(CK)}	I ² S clock rise and fall time	Capacitive load C _L = 30 pF	-	8	
t _{w(CKH)}	I ² S clock high time	Master f _{PCLK} = 36 MHz,	331	-	
t _{w(CKL)}	I ² S clock low time	audio frequency = 48 kHz	332	-	
t _{v(WS)}	WS valid time	Master mode	4	-	ns
t _{h(WS)}	WS hold time	Master mode	4	-	
t _{su(WS)}	WS setup time	Slave mode	4	-	
t _{h(WS)}	WS hold time	Slave mode	0	-	
Duty Cycle	I ² S slave input clock duty cycle	Slave mode	30	70	%
t _{su(SD_MR)}	Data input setup time	Master receiver	9	-	
t _{su(SD_SR)}	Data input setup time	Slave receiver	2	-	
t _{h(SD_MR)}	Data input hold time	Master receiver	0	-	
t _{h(SD_SR)}		Slave receiver	0	-	
t _{v(SD_ST)}	Data output valid time	Slave transmitter (after enable edge)	-	29	ns
t _{h(SD_ST)}	Data output hold time	Slave transmitter (after enable edge)	12	-	
t _{v(SD_MT)}	Data output valid time	Master transmitter (after enable edge)	-	3	
t _{h(SD_MT)}	Data output hold time	Master transmitter (after enable edge)	2	-	

^{1.} Data based on characterization results, not tested in production.

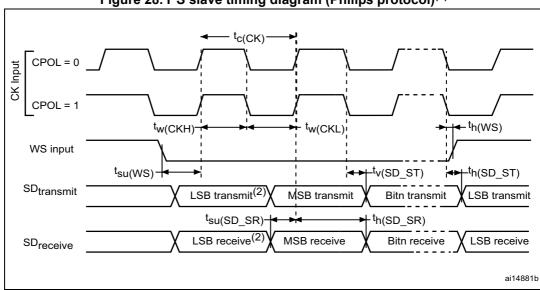


Figure 28. I²S slave timing diagram (Philips protocol)⁽¹⁾

- 1. Measurement points are done at $0.5V_{DD}$ and with external C_L =30 pF.
- LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first

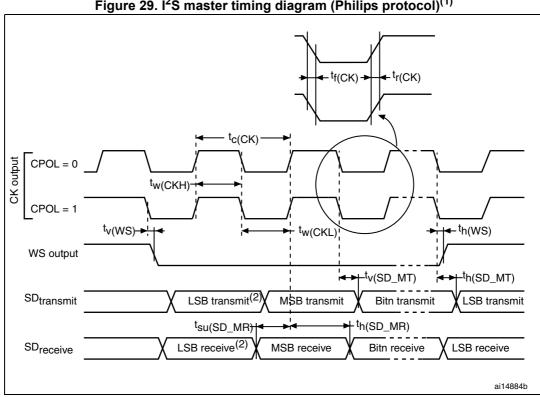


Figure 29. I²S master timing diagram (Philips protocol)⁽¹⁾

- Measurement points are done at $0.5V_{DD}$ and with external C_L =30 pF.
- LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first

USB characteristics

Table 63. USB startup time

Symbol	Parameter	Max	Unit
t _{STARTUP} ⁽¹⁾	USB transceiver startup time	1	μs

^{1.} Guaranteed by design, not tested in production.

Table 64. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit					
Input leve	Input levels									
V _{DD}	USB operating voltage ⁽²⁾	-	3.0 ⁽³⁾	3.6	V					
V _{DI} ⁽⁴⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-						
V _{CM} ⁽⁴⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	٧					
V _{SE} ⁽⁴⁾	Single ended receiver threshold	-	1.3	2.0						
Output le	vels									
V _{OL}	Static output level low	R_L of 1.5 k Ω to 3.6 $V^{(5)}$	-	0.3	V					
V _{OH}	Static output level high	R_L of 15 k Ω to $V_{SS}^{(5)}$	2.8	3.6	'					

- 1. All the voltages are measured from the local ground potential.
- 2. To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 k Ω resistor to a 3.0-to-3.6 V voltage range.
- 3. The STM32F303xB/STM32F303xC USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
- 4. Guaranteed by design, not tested in production.
- 5. R_L is the load connected on the USB drivers.

Figure 30. USB timings: definition of data signal rise and fall time

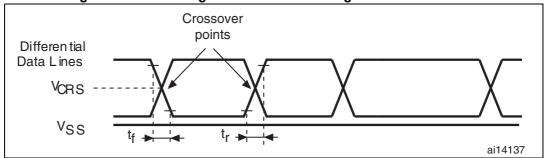


Table 65. USB: Full-speed electrical characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Driver characteristics								
t _r	Rise time ⁽²⁾	C _L = 50 pF	4	-	20	ns		
t _f	Fall time ⁽²⁾	C _L = 50 pF	4	-	20	ns		
t _{rfm}	Rise/ fall time matching	t _r /t _f	90	-	110	%		
V _{CRS}	Output signal crossover voltage	-	1.3	-	2.0	V		
Output driver Impedance ⁽³⁾	Z _{DRV}	driving high and low	28	40	44	Ω		

^{1.} Guaranteed by design, not tested in production.

CAN (controller area network) interface

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

^{3.} No external termination series resistors are required on USB_DP (D+) and USB_DM (D-), the matching impedance is already included in the embedded driver.

6.3.18 ADC characteristics

Unless otherwise specified, the parameters given in *Table 66* to *Table 68* are guaranteed by design, with conditions summarized in *Table 22*.

Table 66. ADC characteristics

Symbol	Parameter Conditions		Min	Тур	Max	Unit
V _{DDA}	Analog supply voltage for ADC	-	2	-	3.6	V
V _{REF+}	Positive reference voltage	-	2	-	V_{DDA}	V
f _{ADC}	ADC clock frequency	-	0.14	-	72	MHz
		Resolution = 12 bits, Fast Channel	0.01	-	5.14	
f _S ⁽¹⁾	Compling rate	Resolution = 10 bits, Fast Channel	0.012	-	- 6	MSPS
'S`´	Sampling rate	Resolution = 8 bits, Fast Channel	0.014	-	7.2	IVIOPO
		Resolution = 6 bits, Fast Channel	0.0175	-	9	
f _{TRIG} ⁽¹⁾	External trigger frequency	f _{ADC} = 72 MHz Resolution = 12 bits	-	-	5.14	MHz
		Resolution = 12 bits	-	-	14	1/f _{ADC}
V _{AIN}	Conversion voltage range ⁽²⁾	-	0	-	V _{REF+}	V
R _{AIN} ⁽¹⁾	External input impedance	-	-	-	100	kΩ
C _{ADC} ⁽¹⁾	Internal sample and hold capacitor	-	-	5	-	pF
t _{STAB} ⁽¹⁾	Power-up time	-	0	0	1	μs
	Calibration times	f _{ADC} = 72 MHz 1.56		6		μs
t _{CAL} ⁽¹⁾	Calibration time	-	112			1/f _{ADC}
	Trigger conversion latency	CKMODE = 00	1.5	2	2.5	1/f _{ADC}
4 (1)	Trigger conversion latency Regular and injected channels without conversion	CKMODE = 01	-	-	2	1/f _{ADC}
t _{latr} (1)		CKMODE = 10	-	-	2.25	1/f _{ADC}
	abort	CKMODE = 11	-	-	2.125	1/f _{ADC}
		CKMODE = 00	2.5	3	3.5	1/f _{ADC}
<u>, (1)</u>	Trigger conversion latency Injected channels aborting a	CKMODE = 01	-	-	3	1/f _{ADC}
t _{latrinj} (1)	regular conversion	CKMODE = 10	-	-	3.25	1/f _{ADC}
		CKMODE = 11	-	-	3.125	1/f _{ADC}
t _S ⁽¹⁾	Sampling time	f _{ADC} = 72 MHz	0.021	-	8.35	μs
ıs' ′	Sampling line	-	1.5	-	601.5	1/f _{ADC}
T _{ADCVREG} (1)	ADC Voltage Regulator Start-up time	-	-	-	10	μs

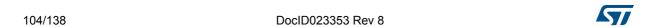


Table 66. ADC characteristics (continued)

Symbol	Parameter Conditions		Min	Тур	Max	Unit
t _{CONV} ⁽¹⁾	Total conversion time	f _{ADC} = 72 MHz Resolution = 12 bits	0.19	-	8.52	μs
	(including sampling time)	Resolution = 12 bits	14 to 614 (t _S for sampling + 12.5 for successive approximation)		1/f _{ADC}	

^{1.} Data guaranteed by design, not tested in Production.

Table 67. Maximum ADC R_{AIN} ⁽¹⁾

	Sampling Sampling cycle @ time [ns] @ 72 MHz 72 MHz		R _{AIN} max (kΩ)				
Resolution			Fast channels ⁽²⁾	Slow channels	Other channels ⁽³⁾		
	1.5	20.83	0.018	NA	NA		
	2.5	34.72	0.150	NA	0.022		
	4.5	62.50	0.470	0.220	0.180		
12 bits	7.5	104.17	0.820	0.560	0.470		
12 Dits	19.5	270.83	2.70	1.80	1.50		
	61.5	854.17	8.20	6.80	4.70		
	181.5	2520.83	22.0	18.0	15.0		
	601.5	8354.17	82.0	68.0	47.0		
	1.5	20.83	0.082	NA	NA		
	2.5	34.72	0.270	0.082	0.100		
	4.5	62.50	0.560	0.390	0.330		
40 6:4-	7.5	104.17	1.20	0.82	0.68		
10 bits	19.5	270.83	3.30	2.70	2.20		
	61.5	854.17	10.0	8.2	6.8		
	181.5	2520.83	33.0	27.0	22.0		
	601.5	8354.17	100.0	82.0	68.0		
	1.5	20.83	0.150	NA	0.039		
	2.5	34.72	0.390	0.180	0.180		
	4.5	62.50	0.820	0.560	0.470		
0.5%	7.5	104.17	1.50	1.20	1.00		
8 bits	19.5	270.83	3.90	3.30	2.70		
	61.5	854.17	12.00	12.00	8.20		
	181.5	2520.83	39.00	33.00	27.00		
	601.5	8354.17	100.00	100.00	82.00		

V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package. Refer to Section 4: Pinouts and pin description for further details.

Table 67. Maximum ADC R_{AIN} ⁽¹⁾ (continued)

	Sampling	Sampling	R _{AIN} max (kΩ)			
Resolution	cycle @ 72 MHz	time [ns] @ 72 MHz	Fast channels ⁽²⁾	Slow channels	Other channels ⁽³⁾	
	1.5	20.83	0.270	0.100	0.150	
	2.5	34.72	0.560	0.390	0.330	
	4.5	62.50	1.200	0.820	0.820	
6 bits	7.5	104.17	2.20	1.80	1.50	
O DIIS	19.5	270.83	5.60	4.70	3.90	
	61.5	854.17	18.0	15.0	12.0	
	181.5	2520.83	56.0	47.0	39.0	
	601.5	8354.17	100.00	100.0	100.0	

^{1.} Data based on characterization results, not tested in production.

^{2.} All fast channels, expect channels on PA2, PA6, PB1, PB12.

^{3.} Channels available on PA2, PA6, PB1, PB12.

Table 68. ADC accuracy - limited test conditions, 100-pin packages (1)(2)

Symbol	Parameter	C	Conditions		Min (3)	Тур	Max (3)	Unit
			Single ended	Fast channel 5.1 Ms	-	±3.5	±4.5	
ET	Total	unadjusted ———	onigic crided	Slow channel 4.8 Ms	-	±4	±4.5	
	error		Differential	Fast channel 5.1 Ms	-	±3	±3	
			Dillerential	Slow channel 4.8 Ms	-	±3	±3	
			Single ended	Fast channel 5.1 Ms	-	±1	±1.5	
EO	Offset error		Sirigle ended	Slow channel 4.8 Ms	-	±1	±2.5	
	Oliset elloi		Differential	Fast channel 5.1 Ms	-	±1	±1.5	
			Dillerential	Slow channel 4.8 Ms	-	±1	±1.5	
			Single ended	Fast channel 5.1 Ms	-	±3	±4	
EG	Gain error	Gain error -	Sirigle efficed	Slow channel 4.8 Ms	-	±3.5	±4	LSB
			Differential	Fast channel 5.1 Ms	-	±1.5	±2.5	LOD
				Slow channel 4.8 Ms	-	<u>+2</u>	±2.5	
	Differential Inearity error Samplin	learity V _{DDA} = V _{REF+} = 3.3 V	Single ended	Fast channel 5.1 Ms	-	±1	±1.5	
ED				Slow channel 4.8 Ms	-	±1	±1.5	
			Differential	Fast channel 5.1 Ms	-	±1	±1	
		100-pin package		Slow channel 4.8 Ms	-	±1	±1	
			Single ended	Fast channel 5.1 Ms	-	±1.5	<u>±2</u>	
EL	Integral linearity error		Differential	Slow channel 4.8 Ms	-	±1.5	±3	
				Fast channel 5.1 Ms	-	±1	±1.5	
			Dillerential	Slow channel 4.8 Ms	-	±1	±1.5	
			Single anded	Fast channel 5.1 Ms	10.7	10.8	-	
ENOB ⁽⁴⁾	Effective		Single ended	Slow channel 4.8 Ms	10.7	10.8	-	bits
EINOB.	bits	umber of its	Differential	Fast channel 5.1 Ms	11.2	11.3	-	טונס
			Dillerential	Slow channel 4.8 Ms	11.1	11.3	-	
	Signal to		Single ended	Fast channel 5.1 Ms	66	67	-	
SINAD ⁽⁴⁾	noise and	gnal-to- iise and		Slow channel 4.8 Ms	66	67	-	dB
SINAD	distortion		Differential	Fast channel 5.1 Ms	69	70	-	ub
	ratio		Differential	Slow channel 4.8 Ms	69	70	-	



Table 68. ADC accuracy - limited test conditions, 100-pin packages (1)(2) (continued)

Symbol	Parameter	C	Min (3)	Тур	Max (3)	Unit		
SNR ⁽⁴⁾	Signal-to- noise ratio	ADC clock freq. \leq 72 MHz Sampling freq \leq 5 Msps $V_{DDA} = V_{REF+} = 3.3 \text{ V}$	Single ended	Fast channel 5.1 Ms	66	67	-	
				Slow channel 4.8 Ms	66	67	-	
			Differential	Fast channel 5.1 Ms	69	70	-	
				Slow channel 4.8 Ms	69	70	-	dB
	Total	25°C 100-pin package iic	Single ended	Fast channel 5.1 Ms	-	-76	-76	uБ
THD ⁽⁴⁾			Siligle ellueu	Slow channel 4.8 Ms	-	-76	-76	
	harmonic distortion		D:ffti-l	Fast channel 5.1 Ms	-	-80	-80	
			Differential	Slow channel 4.8 Ms	-	-80	-80	

^{1.} ADC DC accuracy values are measured after internal calibration.

- 3. Data based on characterization results, not tested in production.
- 4. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

^{2.} ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current. Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in Section 6.3.14 does not affect the ADC accuracy.

Table 69. ADC accuracy, 100-pin packages⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	С	onditions		Min ⁽⁴⁾	Max ⁽⁴⁾	Unit
			Single	Fast channel 5.1 Ms	-	±6.5	
ET	Total		Ended	Slow channel 4.8 Ms	-	±6.5	
= '	unadjusted error		Differential	Fast channel 5.1 Ms	-	<u>±4</u>	
			Dilicicitiai	Slow channel 4.8 Ms	-	<u>±4</u>	
			Single	Fast channel 5.1 Ms	ı	±3	
EO	Offset error		Ended	Slow channel 4.8 Ms	ı	±3	
	Oliset elloi		Differential	Fast channel 5.1 Ms	-	<u>+2</u>	
			Dillerential	Slow channel 4.8 Ms	ı	<u>+2</u>	
			Single	Fast channel 5.1 Ms	ı	±6	
EG	Gain error	ADC clock freq. \leq 72 MHz, Sampling freq. \leq 5 Msps 2 V \leq V _{DDA} , V _{REF+} \leq 3.6 V 100-pin package	Ended	Slow channel 4.8 Ms	ı	#	LSB
	Gaill elloi		Differential	Fast channel 5.1 Ms	ı	#	LOD
			Dilicicitiai	Slow channel 4.8 Ms	-	±3	
			Single	Fast channel 5.1 Ms	ı	±1.5	
ED	Differential linearity		Ended	Slow channel 4.8 Ms	ı	±1.5	
	error		Differential	Fast channel 5.1 Ms	ı	±1.5	
			Dilleterillai	Slow channel 4.8 Ms	ı	±1.5	
			Single	Fast channel 5.1 Ms	-	<u>+2</u>	
EL	Integral linearity		Ended	Slow channel 4.8 Ms	-	±3	
	error		Differential	Fast channel 5.1 Ms	-	<u>+2</u>	
			Dilicicitiai	Slow channel 4.8 Ms	-	<u>+2</u>	
			Single	Fast channel 5.1 Ms	10.4	-	
ENOB	Effective		Ended	Slow channel 4.8 Ms	10.2	ı	bits
(5)	number of bits		Differential	Fast channel 5.1 Ms	10.8	-	DitS
			Dilleteritial	Slow channel 4.8 Ms	10.8		



Table 69. ADC accuracy, 100-pin packages⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	С	Conditions				
	Cianal to		Single	Fast channel 5.1 Ms	64	-	
SINAD	Signal-to- noise and		Ended	Slow channel 4.8 Ms	63	-	
(5)	distortion		Differential	Fast channel 5.1 Ms	67	-	
ratio		Dillerential	Slow channel 4.8 Ms	67	-		
	SNR ⁽⁵⁾ Signal-to- noise ratio Sampling to $2 \text{ V} \leq \text{V}_{DDA}$	ADC clock freq. ≤ 72 MHz,	Single	Fast channel 5.1 Ms	64	-	
CNID(5)		Sampling freq. \leq 5 Msps, 2 V \leq V _{DDA} , V _{REF+} \leq 3.6 V	Ended	Slow channel 4.8 Ms	64	-	dB
SINK			Differential	Fast channel 5.1 Ms	67	-	uБ
		100-pin package		Slow channel 4.8 Ms	67	-	
			Single	Fast channel 5.1 Ms	-	-74	
THD ⁽⁵⁾	Total harmonic		Ended	Slow channel 4.8 Ms	-	-74	
	distortion		Differential	Fast channel 5.1 Ms	-	-78	
			חוובובוונמו	Slow channel 4.8 Ms	-	-76	

- 1. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
 Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in Section 6.3.14 does not affect the ADC accuracy.
- 3. Better performance may be achieved in restricted V_{DDA} , frequency and temperature ranges.
- 4. Data based on characterization results, not tested in production.
- 5. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.



Table 70. ADC accuracy - limited test conditions, 64-pin packages⁽¹⁾⁽²⁾

Symbol	Parameter	C	Conditions		Min (3)	Тур	Max (3)	Unit
			Single ended	Fast channel 5.1 Ms	-	±4	±4.5	
ET	Total		Single ended	Slow channel 4.8 Ms	-	±5.5	±6	
	unadjusted error		Differential	Fast channel 5.1 Ms	-	±3.5	±4	
			Differential	Slow channel 4.8 Ms	-	±3.5	±4	
			Cinale anded	Fast channel 5.1 Ms	-	±2	±2	
F0	Offeeter		Single ended	Slow channel 4.8 Ms	-	±1.5	±2	
EO	Offset error		Differential	Fast channel 5.1 Ms	-	±1.5	±2	
			Differential	Slow channel 4.8 Ms	-	±1.5	±2	
			Cinale anded	Fast channel 5.1 Ms	-	±3	±4	
F0	Cain array		Single ended	Slow channel 4.8 Ms	-	±5	±5.5	LOD
EG	Gain error		Differential	Fast channel 5.1 Ms	-	±3	±3	LSB
			Slow channel 4.8 Ms	-	±3	±3.5		
		arity V _{DDA} = 3.3 V	Single anded	Fast channel 5.1 Ms	-	±1	±1	
ED	Differential		Single ended	Slow channel 4.8 Ms	-	±1	±1	
ED	linearity error		Differential	Fast channel 5.1 Ms	-	±1	±1	
				Slow channel 4.8 Ms	-	±1	±1	
			Oire ede a real e al	Fast channel 5.1 Ms	-	±1.5	±2	
EL	Integral		Single ended -	Slow channel 4.8 Ms	-	±2	±3	
	linearity error		Differential	Fast channel 5.1 Ms	-	±1.5	±1.5	
			Dillerential	Slow channel 4.8 Ms	-	±1.5	±2	
			Single anded	Fast channel 5.1 Ms	10.8	10.8	-	
ENOB	Effective		Single ended	Slow channel 4.8 Ms	10.8	10.8	-	hit
(4)	number of bits		Differential	Fast channel 5.1 Ms	11.2	11.3	-	bit
			Dillerential	Slow channel 4.8 Ms	11.2	11.3	-	
	Ciamal to		Cingle anded	Fast channel 5.1 Ms	66	67	-	
SINAD	Signal-to- noise and		Single ended	Slow channel 4.8 Ms	66	67	-	4D
(4)	distortion ratio		D:#	Fast channel 5.1 Ms	69	70	-	- dB
	Tallo		Differential	Slow channel 4.8 Ms	69	70	-	



Table 70. ADC accuracy - limited test conditions, 64-pin packages⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	C	Min (3)	Тур	Max (3)	Unit		
		ADC clock freq. ≤ 72 MHz Sampling freq ≤ 5 Msps V _{DDA} = 3.3 V	Single ended -	Fast channel 5.1 Ms	66	67	-	
$ >$ $NR \cdots -$	Signal-to- noise ratio		Single ended	Slow channel 4.8 Ms	66	67	-	
			Differential	Fast channel 5.1 Ms	69	70	-	
				Slow channel 4.8 Ms	69	70	-	dB
		25°C 64-pin package	Single ended	Fast channel 5.1 Ms	-	-80	-80	ub l
THD ⁽⁴⁾	Total harmonic		Sirigle efficed	Slow channel 4.8 Ms	-	-78	-77	
	distortion		Differential	Fast channel 5.1 Ms	-	-83	-82	
	diotortion		Dilletetillat	Slow channel 4.8 Ms	-	-81	-80	

^{1.} ADC DC accuracy values are measured after internal calibration.

- 3. Data based on characterization results, not tested in production.
- 4. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

577

ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in Section 6.3.14 does not affect the ADC
accuracy.

Table 71. ADC accuracy, 64-pin packages⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	C	Conditions		Min ⁽⁴⁾	Max (4)	Unit
			Cinalo andod	Fast channel 5.1 Ms	-	±6.5	
	Total		Single ended	Slow channel 4.8 Ms	-	±6.5	
ET	unadjusted error		Differential	Fast channel 5.1 Ms	-	±4	
			Differential	Slow channel 4.8 Ms	-	±4.5	
			Cinale anded	Fast channel 5.1 Ms	-	±3	
EO	Offeet error		Single ended	Slow channel 4.8 Ms	-	±3	
EO	Offset error		Differential	Fast channel 5.1 Ms	-	±2.5	
			Dillerential	Slow channel 4.8 Ms	-	±2.5	
		Single ended Fast channel 5.1 Ms		-	±6		
EG	Coin orror		Single ended	Slow channel 4.8 Ms	-	±6	LCD
EG	Gain error		Differential	Fast channel 5.1 Ms	-	±3.5	- LSB
				Slow channel 4.8 Ms	-	±4	
			0:111	Fast channel 5.1 Ms	-	±1.5	
ED	Differential		Single ended	Slow channel 4.8 Ms	-	±1.5	
ED	linearity error		Differential	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
			Single ended	Fast channel 5.1 Ms	-	±3	
EL	Integral linearity		Sirigle ended	Slow channel 4.8 Ms	-	±3.5	
EL	error		Differential	Fast channel 5.1 Ms	-	±2	
			Dillerential	Slow channel 4.8 Ms	-	±2.5	
			Single ended	Fast channel 5.1 Ms	10.4	-	
ENOB	Effective		Sirigle ended	Slow channel 4.8 Ms	10.4	-	hito
(5)	number of bits		Differential	Fast channel 5.1 Ms	10.8	-	bits
		Dillerential	Slow channel 4.8 Ms	10.8	-		
	Cianal to		Single anded	Fast channel 5.1 Ms	64	-	
SINAD	Signal-to- noise and		Single ended	Slow channel 4.8 Ms	63	-	4P
(5)	distortion ratio		Differential	Fast channel 5.1 Ms	67	-	- dB
	Tallo		Dillerential	Slow channel 4.8 Ms	67	-	



			<u> </u>	<u> </u>			
Symbol	Parameter	C	Min ⁽⁴⁾	Max (4)	Unit		
			Single ended	Fast channel 5.1 Ms	64	-	
SNR 1 -	Signal-to-		Sirigle efficed	Slow channel 4.8 Ms	64	-	
	noise ratio	ADC clock freq. ≤ 72 MHz, Sampling freq ≤ 5 Msps,	Differential	Fast channel 5.1 Ms	67	-	
				Slow channel 4.8 Ms	67	-	dB
		2 V ≤ V _{DDA} ≤ 3.6 V 64-pin package	Cingle anded	Fast channel 5.1 Ms	-	-75	ub
THD ⁽⁵⁾	Total harmonic		Single ended	Slow channel 4.8 Ms	-	-75	
	distortion		Differential	Fast channel 5.1 Ms	-	-79	
			Dilleterillar	Slow channel 4.8 Ms	-	-78	

Table 71. ADC accuracy, 64-pin packages⁽¹⁾⁽²⁾⁽³⁾ (continued)

- 1. ADC DC accuracy values are measured after internal calibration.
- 2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current. Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in Section 6.3.14 does not affect the ADC accuracy.
- 3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
- 4. Data based on characterization results, not tested in production.
- 5. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

Table 72. ADC accuracy at 1MSPS⁽¹⁾⁽²⁾

Symbol	Parameter	Test condition	ıs	Тур	Max ⁽³⁾	Unit
ET	Total unadjusted error		Fast channel	±2.5	±5	
	Total unaujusted enoi		Slow channel	±3.5	±5	
EO	Offset error		Fast channel	±1	±2.5	
	Oliset elloi	- ADC Freq ≤ 72 MHz Sampling Freq ≤ 1MSPS 2.4 V ≤ V _{DDA} = V _{REF+} ≤ 3.6 V	Slow channel	±1.5	±2.5	
EG	Gain error		Fast channel	±2	±3	LSB
EG	Gairrenoi		Slow channel	±3	±4	LOD
ED	Differential linearity error	Single-ended mode	Fast channel	±0.7	±2	
	Differential linearity error		Slow channel	±0.7	±2	
EL	Integral linearity error		Fast channel	±1	±3	
	Integral linearity error		Slow channel	±1.2	±3	

- 1. ADC DC accuracy values are measured after internal calibration.
- 2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current. Any positive injection current within the limits specified for IINJ(PIN) and ∑IINJ(PIN) in Section 6.3.14: I/O port characteristics does not affect the ADC accuracy.
- 3. Data based on characterization results, not tested in production.

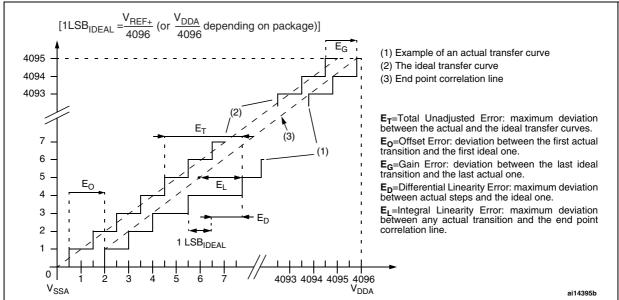
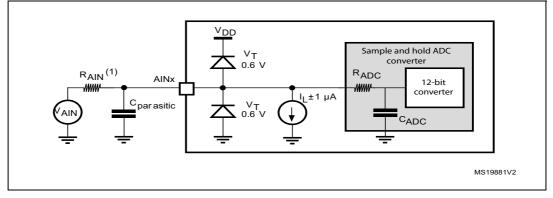


Figure 31. ADC accuracy characteristics

Figure 32. Typical connection diagram using the ADC



- Refer to Table 66 for the values of RAIN
- $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

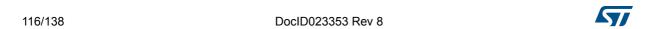
General PCB design guidelines

Power supply decoupling should be performed as shown in Figure 10. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.19 DAC electrical specifications

Table 73. DAC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DDA}	Analog supply voltage	DAC output buffer ON	2.4	-	3.6	V
R _{LOAD} ⁽¹⁾	Resistive load	DAC output buffer ON	5	-	-	kΩ
R _O ⁽¹⁾	Output impedance	DAC output buffer ON	-	-	15	kΩ
C _{LOAD} ⁽¹⁾	Capacitive load	DAC output buffer ON	-	-	50	pF
V _{DAC_OUT} ⁽¹⁾	Voltage on DAC_OUT output	Corresponds to 12-bit input code (0x0E0) to (0xF1C) at $V_{\rm DDA}$ = 3.6 V and (0x155) and (0xEAB) at $V_{\rm DDA}$ = 2.4 V DAC output buffer ON.	0.2	-	V _{DDA} – 0.2	V
		DAC output buffer OFF	-	0.5	V _{DDA} - 1LSB	mV
I _{DDA} ⁽³⁾	DAC DC current consumption in quiescent	With no load, middle code (0x800) on the input.	-	-	380	μΑ
IDDA', '	mode (Standby mode) ⁽²⁾	With no load, worst code (0xF1C) on the input.	-	-	480	μA
(3)	Differential non linearity	Given for a 10-bit input code	-	-	±0.5	LSB
DNL ⁽³⁾	Difference between two consecutive code-1LSB)	Given for a 12-bit input code	-	-	±2	LSB
	Integral non linearity	Given for a 10-bit input code	-	-	±1	LSB
INL ⁽³⁾	(difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095)	Given for a 12-bit input code	-	-	±4	LSB
		-	-	-	±10	mV
Offset ⁽³⁾	Offset error (difference between measured value at Code (0x800) and the ideal	Given for a 10-bit input code at V _{DDA} = 3.6 V	-	-	±3	LSB
	value = V _{DDA} /2)	Given for a 12-bit input code at V _{DDA} = 3.6 V	-	1	±12	LSB
Gain error ⁽³⁾	Gain error	Given for a 12-bit input code	ı	-	±0.5	%
t _{SETTLING} (3)	Settling time (full scale: for a 12-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	C _{LOAD} ⊴50 pF, R _{LOAD} ≥ 5 kΩ	-	3	4	μs
Update rate ⁽³⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	C _{LOAD} ≤50 pF, R _{LOAD} ≥ 5 kΩ	-	-	1	MS/s

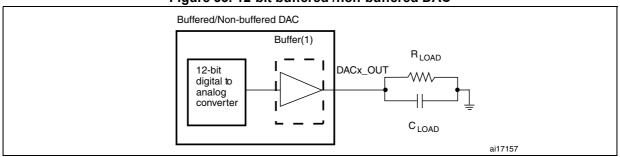


		•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{WAKEUP} ⁽³⁾	DAC Control register)	C _{LOAD} ⊴50 pF, R _{LOAD} ≥ 5 kΩ	-	6.5	10	μs
	Power supply rejection ratio (to V _{DDA}) (static DC measurement	$C_{LOAD} = 50 \text{ pF},$ No $R_{LOAD} \ge 5 \text{ k}\Omega,$	-	– 67	-40	dB

Table 73. DAC characteristics (continued)

- 1. Guaranteed by design, not tested in production.
- 2. Quiescent mode refers to the state of the DAC a keeping steady value on the output, so no dynamic consumption is involved.
- 3. Data based on characterization results, not tested in production.

Figure 33. 12-bit buffered /non-buffered DAC



The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly
without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the
DAC_CR register.

6.3.20 Comparator characteristics

Table 74. Comparator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DDA}	Analog supply voltage	-	2	-	3.6	
V _{IN}	Comparator input voltage range	-	0	-	V_{DDA}	V
V _{BG}	Scaler input voltage	-	ı	1.2	-	
V _{SC}	Scaler offset voltage	-	ı	±5	±10	mV
t _{S_SC}	Scaler startup time from power down	-	-	-	0.1	ms
t _{START}	Comparator startup time	Startup time to reach propagation delay specification	-	-	60	μs

Table 74. Comparator characteristics⁽¹⁾ (continued)

Symbol	Parameter	Condition	ons	Min	Тур	Max	Unit
		Ultra-low power mode		-	2	4.5	
	Propagation delay for	Low power mode		-	0.7	1.5	μs
	200 mV step with 100 mV	Medium power mode	-	0.3	0.6		
	overdrive	High around mode	$V_{DDA} \ge 2.7 \text{ V}$	-	50	100	no
4		High speed mode	V _{DDA} < 2.7 V	-	100	240	ns
t _D		Ultra-low power mode		-	2	7	
	Propagation delay for full	Low power mode		-	0.7	2.1	μs
	range step with 100 mV	Medium power mode		-	0.3	1.2	
	overdrive	I liab aread made	$V_{DDA} \ge 2.7 \text{ V}$	-	90	180	
		High speed mode	V _{DDA} < 2.7 V	-	110	300	ns
V _{offset}	Comparator offset error	-		-	±4	±10	mV
dV _{offset} /dT	Offset error temperature coefficient	-		-	18	-	μV/° C
		Ultra-low power mode		-	1.2	1.5	
	COMP current	Low power mode		-	3	5	
I _{DD(COMP)}	consumption	Medium power mode		-	10	15	μA
		High speed mode			75	100	
		No hysteresis (COMPxHYST[1:0]=00)	-	-	0	-	
		Law by otamacia	High speed mode	3		13	
		Low hysteresis (COMPxHYST[1:0]=01)	All other power modes	5	8	10	
V _{hys}	Comparator hysteresis	Madicus Israelanaia	High speed mode	7		26	mV
		Medium hysteresis (COMPxHYST[1:0]=10)	All other power modes	9	15	19	
		High bustoresis	High speed mode	18		49	
		High hysteresis (COMPxHYST[1:0]=11)	All other power modes	19	31	40	

^{1.} Data guaranteed by design, not tested in production.



6.3.21 Operational amplifier characteristics

Table 75. Operational amplifier characteristics⁽¹⁾

Symbol	Param	neter	Condition	Min	Тур	Max	Unit
V_{DDA}	Analog supply volt	age	-	2.4	-	3.6	V
CMIR	Common mode in	out range	-	0	-	V_{DDA}	V
		Maximum calibration	25°C, No Load on output.	-	-	4	
M	Input offset	range	All voltage/Temp.	-	-	6	mV
VI _{OFFSET}	voltage	After offset	25°C, No Load on output.	-	-	1.6	IIIV
		calibration	All voltage/Temp.	-	-	3	
ΔVI _{OFFSET}	Input offset voltage	e drift	-	-	5	-	μV/°C
I _{LOAD}	Drive current		-	-	-	500	μA
IDDOPAMP	Consumption		No load, quiescent mode	-	690	1450	μΑ
TS_OPAMP_VOUT	ADC sampling time the OPAMP output		-	400	ı	1	ns
CMRR	Common mode rej	ection ratio	-	-	90	-	dB
PSRR	Power supply reject	ction ratio	DC	73	117	-	dB
GBW	Bandwidth		-	-	8.2	-	MHz
SR	Slew rate		-	-	4.7	-	V/µs
R _{LOAD}	Resistive load		-	4	-	-	kΩ
C _{LOAD}	Capacitive load		-	-	-	50	pF
VOH _{SAT}	High saturation vo	Itana	R _{load} = min, Input at V _{DDA} .	-	-	100	
VOLISAT	Tilgir saturation vo	itage	R _{load} = 20K, Input at V _{DDA} .	-	ı	20	mV
VOL	Low acturation val	tago	Rload = min, input at 0V	-	-	100	IIIV
VOL _{SAT}	Low saturation vol	lage	Rload = 20K, input at 0V.	-	-	20	
φm	Phase margin		-	-	62	-	0
t _{OFFTRIM}	Offset trim time: du minimum time nee two steps to have	ded between	-	-	-	2	ms
^t wakeup	Wake up time from	n OFF state.	$\begin{split} &C_{LOAD} \leq \!\! 50 \text{ pf,} \\ &R_{LOAD} \geq 4 \text{ k}\Omega, \\ &\text{Follower} \\ &\text{configuration} \end{split}$	-	2.8	5	μs

Table 75. Operational amplifier characteristics⁽¹⁾ (continued)

Symbol	Parameter	Condition	Min	Тур	Max	Unit
			-	2	-	-
DCA gain	Non inverting gain value		-	4	-	-
PGA gain	Non inverting gain value	-	-	8	-	-
			-	16	-	-
		Gain=2	-	5.4/5.4	-	
	R2/R1 internal resistance values in	Gain=4	-	16.2/5.4	-	kΩ
R _{network}	PGA mode ⁽²⁾	Gain=8	-	37.8/5.4	-	K22
		Gain=16	-	40.5/2.7	-	
PGA gain error	PGA gain error	-	-1%	-	1%	
I _{bias}	OPAMP input bias current	-	-	-	±0.2 ⁽³⁾	μA
	PGA bandwidth for different non inverting gain	PGA Gain = 2, Cload = 50pF, Rload = 4 K Ω	-	4	-	
DCA DW		PGA Gain = 4, Cload = 50pF, Rload = 4 K Ω	-	2	-	NAL 1-
PGA BW		PGA Gain = 8, Cload = 50pF, Rload = 4 K Ω	-	1	-	MHz
		PGA Gain = 16, Cload = 50pF, Rload = 4 K Ω	-	0.5	-	
		@ 1KHz, Output loaded with 4 KΩ	-	109	-	
en	Voltage noise density	@ 10KHz, Output loaded with 4 KΩ	-	43	-	<u>nV</u> √Hz

^{1.} Guaranteed by design, not tested in production.

^{2.} R2 is the internal resistance between OPAMP output and OPAMP inverting input. R1 is the internal resistance between OPAMP inverting input and ground. The PGA gain =1+R2/R1

^{3.} Mostly TTa I/O leakage, when used in analog mode.

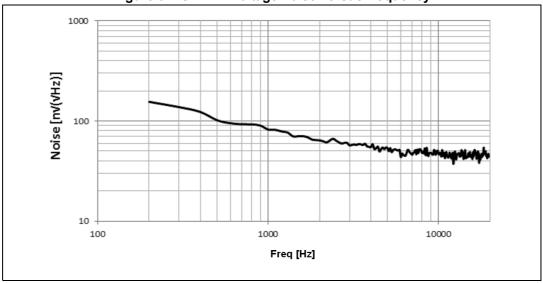


Figure 34. OPAMP voltage noise versus frequency

6.3.22 Temperature sensor characteristics

Table 76. TS characteristics

Symbol	Parameter	Min	Тур	Max	Unit
T _L ⁽¹⁾	V _{SENSE} linearity with temperature	-	±1	<u>+2</u>	°C
Avg_Slope ⁽¹⁾	Average slope	4.0	4.3	4.6	mV/°C
V ₂₅	Voltage at 25 °C	1.34	1.43	1.52	V
t _{START} (1)	Startup time	4	-	10	μs
T _{S_temp} ⁽¹⁾⁽²⁾	ADC sampling time when reading the temperature	2.2	-	-	μs

^{1.} Guaranteed by design, not tested in production.

Table 77. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V _{DDA} = 3.3 V	0x1FFF F7B8 - 0x1FFF F7B9
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C V _{DDA} = 3.3 V	0x1FFF F7C2 - 0x1FFF F7C3

6.3.23 V_{BAT} monitoring characteristics

Table 78. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Тур	Max	Unit
R	Resistor bridge for V _{BAT}	-	50	-	ΚΩ
Q	Ratio on V _{BAT} measurement	-	2	-	
Er ⁽¹⁾	Error on Q	-1	-	+1	%
T _{S_vbat} ⁽¹⁾⁽²⁾	ADC sampling time when reading the V _{BAT} 1mV accuracy	2.2	-	-	μs

^{1.} Guaranteed by design, not tested in production.

^{2.} Shortest sampling time can be determined in the application by multiple iterations.

^{2.} Shortest sampling time can be determined in the application by multiple iterations.

7 Package characteristics

7.1 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.



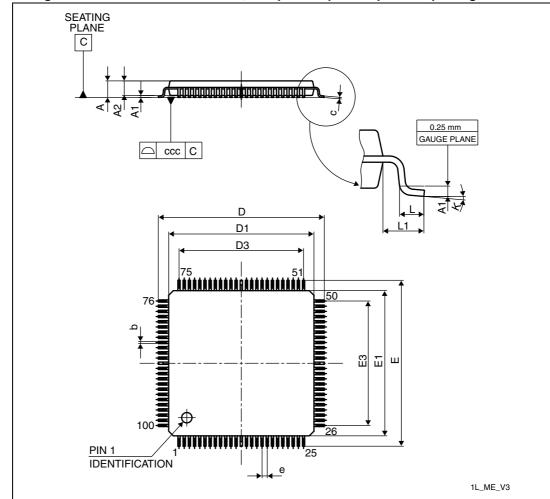


Figure 35. LQFP100 - 14 x 14 mm, 100-pin low-profile quad flat package outline

1. Drawing is not to scale.

Table 79. LQPF100 – 14 x 14 mm, low-profile quad flat package mechanical data

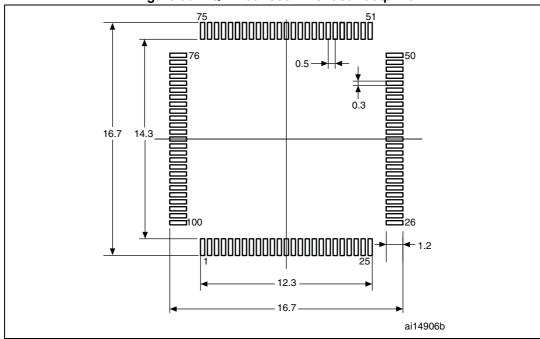
Cumah al	millimeters					
Symbol	Min	Тур	Max	Min	Тур	Max
А	-	-	1.60	-	-	0.063
A1	0.05	-	0.15	0.002	-	0.0059
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
С	0.09	-	0.2	0.0035	-	0.0079
D	15.80	16.00	16.2	0.622	0.6299	0.6378
D1	13.80	14.00	14.2	0.5433	0.5512	0.5591
D3	-	12.00	-	-	0.4724	-
Е	15.80	16.00	16.2	0.622	0.6299	0.6378

Table 79. LQPF100 – 14 x 14 mm, low-profile quad flat package mechanical data (continued)

Symbol		millimeters				
Symbol	Min	Тур	Max	Min	Тур	Max
E1	13.80	14.00	14.2	0.5433	0.5512	0.5591
E3	-	12.00	-	-	0.4724	-
е	-	0.50	-	-	0.0197	-
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1	-	1.00	-	-	0.0394	-
K	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.08	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 36. LQFP100 recommended footprint



1. Dimensions are in millimeters.

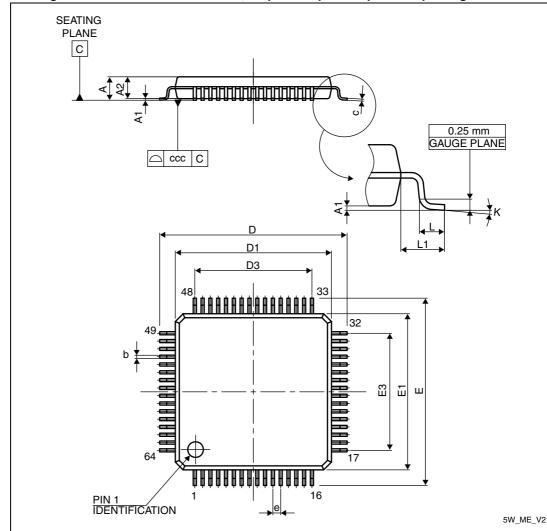


Figure 37. LQFP64 – 10 x 10 mm, 64 pin low-profile quad flat package outline

1. Drawing is not to scale.

Table 80. LQFP64 - 10 x 10 mm low-profile quad flat package mechanical data

Cumbal	Complete		millimeters		inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.60	-	-	0.0630
A1	0.05	-	0.15	0.0020	-	0.0059
A2	1.350	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106

Table 80. LQFP64 – 10 x 10 mm low-profile quad flat package mechanical data (continued)

Currelle e l	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
С	0.09	-	0.20	0.0035		0.0079
D	11.80	12.00	12.20	0.4646	0.4724	0.4803
D1	9.80	10.00	10.20	0.3858	0.3937	0.4016
D3	-	7.50	-	-	0.2953	-
E	11.80	12.00	12.20	0.4646	0.4724	0.4803
E1	9.80	10.00	10.20	0.3858	0.3937	0.4016
E3	-	7.50	-	-	0.2953	-
е	-	0.50	-	-	0.0197	-
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1	-	1.00	-	-	0.0394	-
K	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.08	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

1. Dimensions are in millimeters.

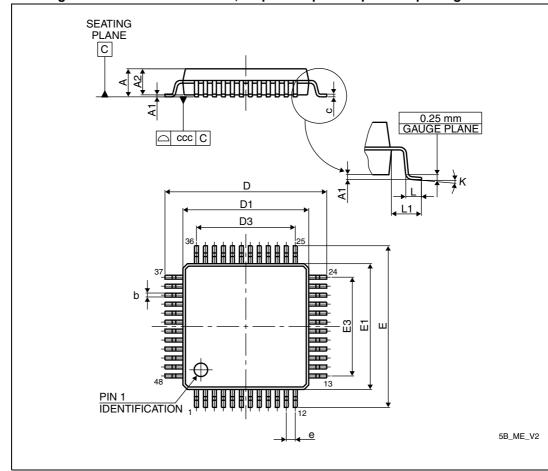


Figure 39. LQFP48 - 7 x 7 mm, 48-pin low-profile quad flat package outline

1. Drawing is not to scale.

Table 81. LQFP48 - 7 x 7 mm, 48-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.60	-	-	0.0630
A1	0.05	-	0.15	0.0020	-	0.0059
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
С	0.09	-	0.20	0.0035	-	0.0079
D	8.80	9.00	9.20	0.3465	0.3543	0.3622
D1	6.80	7.00	7.20	0.2677	0.2756	0.2835
D3	-	5.50	-	-	0.2165	-
Е	8.80	9.00	9.20	0.3465	0.3543	0.3622
E1	6.80	7.00	7.20	0.2677	0.2756	0.2835
E3	-	5.50	-	-	0.2165	-
е	-	0.50	-	-	0.0197	-

Table 81. LQFP48 – 7 x 7 mm, 48-pin low-profile quad flat package mechanical data (continued)

Complete		millimeters				
Symbol	Min	Тур	Max	Min	Тур	Max
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1	-	1.00	-	-	0.0394	-
K	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.08	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

1. Dimensions are in millimeters.

7.2 Thermal characteristics

The maximum chip junction temperature (T_Jmax) must never exceed the values given in *Table 22: General operating conditions on page 57*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \max = T_A \max + (P_D \max x \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{IA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and P_{I/O} max (P_D max = P_{INT} max + P_{I/O}max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

P_{I/O} max represents the maximum power dissipation on output pins where:

$$P_{I/O} \max = \sum (V_{OL} \times I_{OL}) + \sum ((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

· · · · · · · · · · · · · · · · · · ·								
Symbol	Parameter	Value	Unit					
	Thermal resistance junction-ambient LQFP64 - 10 × 10 mm / 0.5 mm pitch	45						
$\Theta_{\sf JA}$	Thermal resistance junction-ambient LQFP48 - 7 × 7 mm	55	°C/W					
	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	41						

Table 82. Package thermal characteristics

7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org



7.2.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Section 8: Part numbering*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F303xB/STM32F303xC at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 3 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL} = 0.4 V and maximum 2 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL} = 1.3 V

 P_{INTmax} = 50 mA × 3.5 V= 175 mW

 $P_{IOmax} = 3 \times 8 \text{ mA} \times 0.4 \text{ V} + 2 \times 20 \text{ mA} \times 1.3 \text{ V} = 61.6 \text{ mW}$

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 61.6 mW:

 $P_{Dmax} = 175 + 61.6 = 236.6 \text{ mW}$

Thus: $P_{Dmax} = 236.6 \text{ mW}$

Using the values obtained in *Table 82* T_{Jmax} is calculated as follows:

For LQFP64, 45°C/W

 T_{Jmax} = 82 °C + (45°C/W × 236.6 mW) = 82 °C + 10.65 °C = 92.65 °C

This is within the range of the suffix 6 version parts ($-40 < T_{.l} < 105$ °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Section 8: Part numbering*).



Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 115 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 9 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL} = 0.4 V

 P_{INTmax} = 20 mA × 3.5 V= 70 mW

 $P_{IOmax} = 9 \times 8 \text{ mA} \times 0.4 \text{ V} = 28.8 \text{ mW}$

This gives: $P_{INTmax} = 70 \text{ mW}$ and $P_{IOmax} = 28.8 \text{ mW}$:

 $P_{Dmax} = 70 + 28.8 = 98.8 \text{ mW}$

Thus: P_{Dmax} = 98.8 mW

Using the values obtained in $\textit{Table 82}\ T_{\textit{Jmax}}$ is calculated as follows:

For LQFP100, 41°C/W

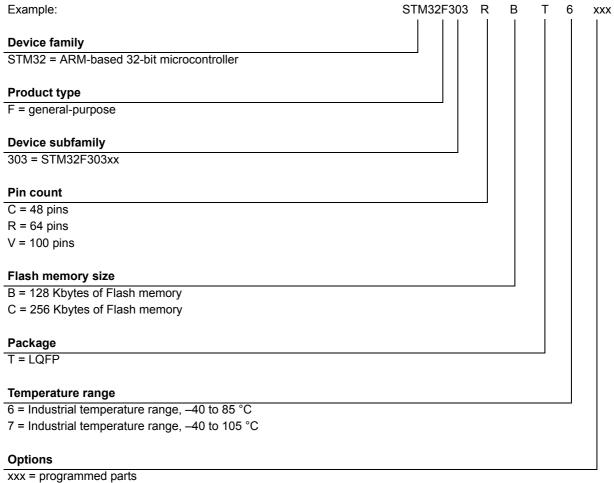
 T_{Jmax} = 115 °C + (41°C/W × 98.8 mW) = 115 °C + 4.05 °C = 119.05 °C

This is within the range of the suffix 7 version parts ($-40 < T_J < 125$ °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see Section 8: Part numbering).

Part numbering 8

Table 83. Ordering information scheme



TR = tape and reel

9 Revision history

Table 84. Document revision history

Date	Revision	Changes
22-Jun-2012	1	Initial release
07-Sep-2012	2	Modified Features on cover page. Modified Table 2: STM32F301xx family device features and peripheral counts Added clock tree to Section 3.8: Clocks and startup Added Table 5: STM32F303xB/STM32F303xC I2C implementation Added Table 6: USART features Added Table 7: STM32F303xB/STM32F303xC SPI/I2S implementation Modified Table 8: Capacitive sensing GPIOs available on STM32F303xB/STM32F303xC devices Modified Figure 4, Figure 5 and Figure 6: STM32F303xB/STM32F303xC LQFP100 pinout Modified Table 11: STM32F303xB/STM32F303xC pin definitions Modified Table 11: STM32F303xB/STM32F303xC pin definitions Modified Table 19: Voltage characteristics Modified Table 20: Current characteristics Modified Table 20: Current characteristics Modified Table 23: Operating conditions at power-up / power-down Added footnote to Table 29: Typical and maximum current consumption from the VDDA supply Added footnote to Table 33 and Table 34: Typical current consumption in Sleep mode, code running from Flash or RAM Removed table "Switching output I/O current consumption" and table "Peripheral current consumption" Added note under Figure 16: Typical application with a 32.768 kHz crystal Updated Table 42: HSI oscillator characteristics Updated Table 45: Flash memory characteristics Updated Table 45: Flash memory characteristics Updated Table 50: Electrical sensitivities Updated Table 51: I/O current injection susceptibility Updated Table 55: NRST pin characteristics Updated Table 55: NRST pin characteristics Updated Table 60: IS PI characteristics Updated Table 61: SPI characteristics Updated Table 62: I/S characteristics Updated Table 62: I/S characteristics Updated Table 63: SPI characteristics Updated Table 65: SPI characteristics Updated Table 66: IS PI characteristics Updated Table 67: SPI characteristics Updated Table 68: SPI characteristics Updated Table 69: IS Characteristics Updated Table 69:
21-Sep-2012	3	Updated Table 61: SPI characteristics

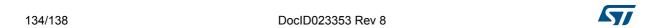


Table 84. Document revision history

Dete	Dovision	Table 84. Document revision history
Date	Revision	Changes
05-Dec-2012	4	Updated first page Removed references to VDDSDx and VSSSD Added reference to PM0214 in Section 1 Moved Temp. sensor calibartion values to Table 77 and VREF calibration values to Table 27 Updated Table 3: STM32F303xx family device features and peripheral counts Updated Section 3.4: Embedded SRAM Updated Section 3.2: Memory protection unit (MPU) Updated Section 3.2: Memory protection unit (MPU) Updated Section 3.2: Iniversal serial bus (USB) Modified Section 3.2: Touch sensing controller (TSC) Updated heading of Table 6: USART features Updated Table 11: STM32F303xB/STM32F303xC pin definitions Added notes to PC13, PC14 and PC15 in Table 11: STM32F303xB/STM32F303xC pin definitions Updated Figure 10: Power supply scheme Modified Table 19: Voltage characteristics Modified Table 19: Voltage characteristics Modified Table 19: Voltage characteristics Modified Table 20: Current characteristics Modified Table 20: Current characteristics Updated Table 20: Typical VBAT current consumption (LSE and RTC ONLSEDRY[1:0] = '00') Updated Section 6.3.14: I/O port characteristics Updated Table 28: Typical and maximum current consumption from VDD supply at VDD = 3.6V and Table 29: Typical and maximum current consumption from the VDDA supply Updated Table 30: Typical and maximum VDD consumption in Stop and Standby modes and Table 31: Typical and maximum VDDA consumption in Stop and Standby modes Updated Table 32: Typical VBAT current consumption (LSE and RTC ONLSEDRY[1:0] = '00') Updated Table 33: Typical ourrent consumption in Run mode, code with data processing running from Flash and Table 34: Typical current consumption in Stop mode, code running from Flash and RAM Added Table 36: Peripheral current consumption Updated Section 6.3.6: Wakeup time from low-power mode Modified Table 53: Output voltage characteristics Updated EBD absolute maximum ratings Modified Table 56: TilMx characteristics Updated Table 57: Upcarent injection susceptibility Updated Table 56: Tilmx characteristics Updated Table 57: Depraitonal amplifier characteris



Table 84. Document revision history

Date	Revision	Changes
08-Jan-2013	5	Updated V _{hys} and I _{lkg} in <i>Table 52: I/O static characteristics</i> . Updated V _{IL(NRST)} , V _{IH(NRST)} , and V _{NF(NRST)} in <i>Table 55: NRST pin characteristics</i> . Updated <i>Table 68: ADC accuracy - limited test conditions, 100-pin packages</i> and <i>Table 64: ADC accuracy - limited test conditions 2</i>).
24-Jun-2013	6	Replaced Cortex-M4F with Cortex M4 with FPU Updated Core, Memories and SPI bullet points in Features Removed 8KB CCM SRAM from STM32F302xx devices, updated Figure 1: STM32F303xB/STM32F303xC block diagram and Table 3: STM32F303xx family device features and peripheral counts Updated Section 3.4: Embedded SRAM Added VREF+ in Section 3.13: Digital-to-analog converter (DAC) Removed DMA support for UART5 in Table 6: USART features Added 'reference clock detection' bullet in Section 3.17: Real-time clock (RTC) and backup registers Added paragraph 'The touch sensing controller is fully' in Section 3.25: Touch sensing controller (TSC) Updated Comparison of I2C analog and digital filters Updated Section 3.9: General-purpose input/outputs (GPIOs) Added 'EVENTOUT' in Table 11: STM32F303xB/STM32F303xC pin definitions and added note to 'VREF+' pin Updated Σl _{VDD} in Table 20: Current characteristics and Output driving current Updated Table 59: I2C timings specification (see I2C specification, rev.03, June 2007) and Figure 24: I2C bus AC waveforms and measurement circuit Added VREF+ row to Table 66: ADC characteristics, replaced VDDA with VREF+, updated t _{conv} and added note to 'conversion voltage range Added VREF+ row to Table 73: DAC characteristics and replaced VDDA with VREF+ Added 'PGA BW' and 'en' in Table 75: Operational amplifier characteristics

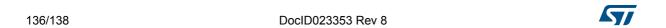


Table 84. Document revision history

Date	Revision	Changes
13-Nov-2013	7	Removed STM32F302xB/STM32F302xC products (now in a separate datasheet). Added I2S feature for SPI2 and SPI3 Added t _{SP} to <i>Table 59: I2C timings specification (see I2C specification, rev.03, June 2007).</i> Renamed t _{SP} to t _{AN} in <i>Table 60: I2C analog filter characteristics.</i> Added t _{STAB} in <i>Table 66: ADC characteristics</i> Renamed V _{OPAMPx} to _{VREFOPAMPx} Updated <i>Table 69: ADC accuracy, 100-pin packages.</i> Updated ADC channel names in <i>Section 3.12.1, Section 3.12.2</i> and <i>Section 3.12.3.</i>
18-Apr-2014	8	Updated <i>Table 48: EMI characteristics</i> conditions :3.3v replaced by 3.6V. Updated <i>Section 6.3.17: Communications interfaces</i> I ² C interface. Updated <i>Table 75: Operational amplifier characteristics</i> adding TS_OPAMP_VOUT row. Updated <i>Section 3.12: Fast analog-to-digital converter (ADC)</i> . updated ARM and Cortex trademark. Updated <i>Table 30: Typical and maximum VDD consumption in Stop and Standby modes</i> with Max value at 85°C and 105°C. Updated <i>Table 68: ADC accuracy - limited test conditions, 100-pin packages</i> and <i>Table 69: ADC accuracy, 100-pin packages</i> for 100-pin package. Added <i>Table 70: ADC accuracy - limited test conditions, 64-pin packages</i> and <i>Table 71: ADC accuracy, 64-pin packages</i> for 64-pin package. Added <i>Table 72: ADC accuracy at 1MSPS</i> for 1MSPS sampling frequency. Updated <i>Table 61: SPI characteristics</i> . Updated <i>Table 73: DAC characteristics</i> .



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